



Hands-on Workshop on Electronic-Structure Theory and Artificial Intelligence for Materials Science

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Shanghai, China



Introduction to electron and phonon transport

--from computational science perspective

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2025/11/06

Overview



Background



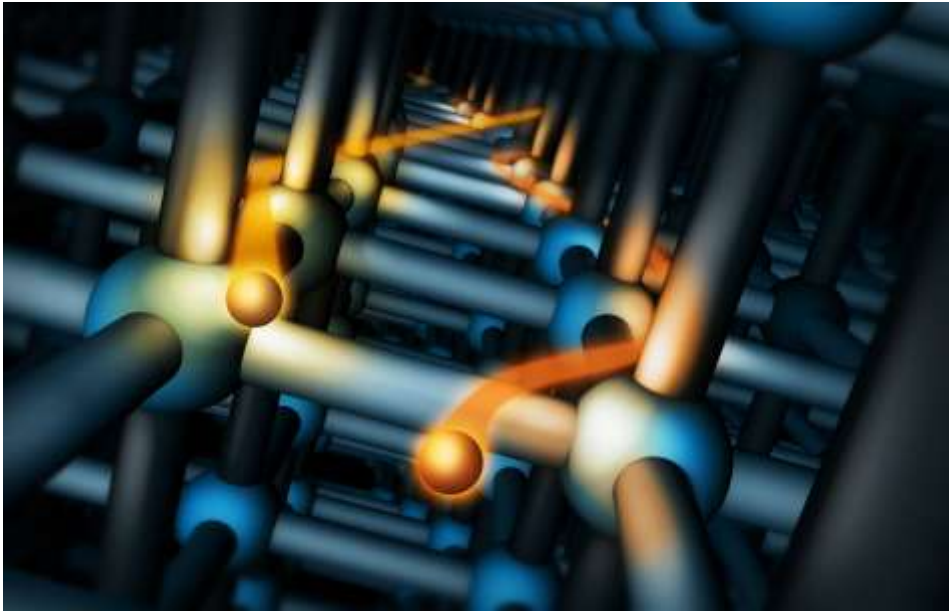
Electrical transport



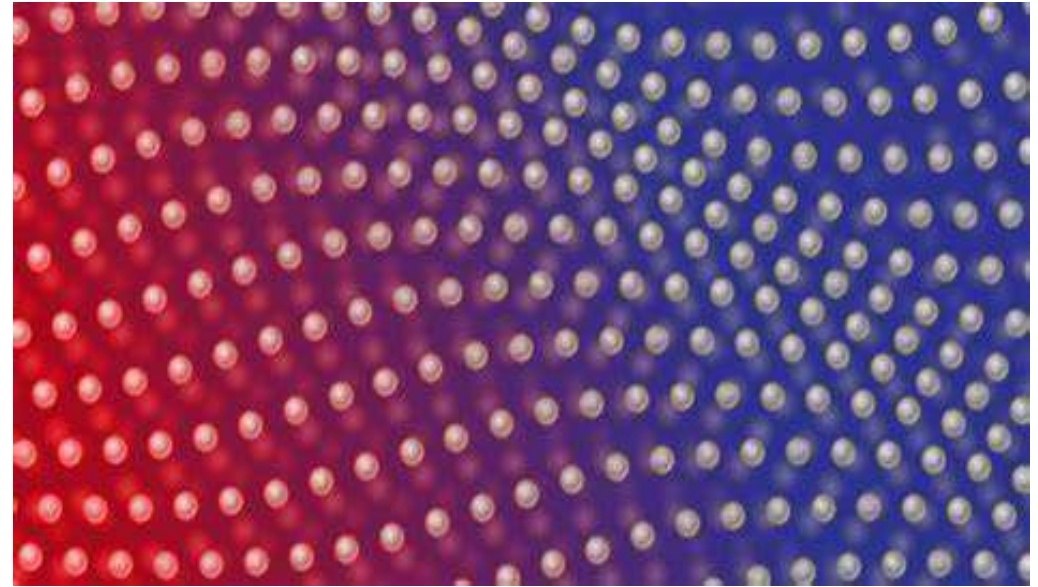
Lattice thermal conductivity

1. Background

Electron and phonon transport



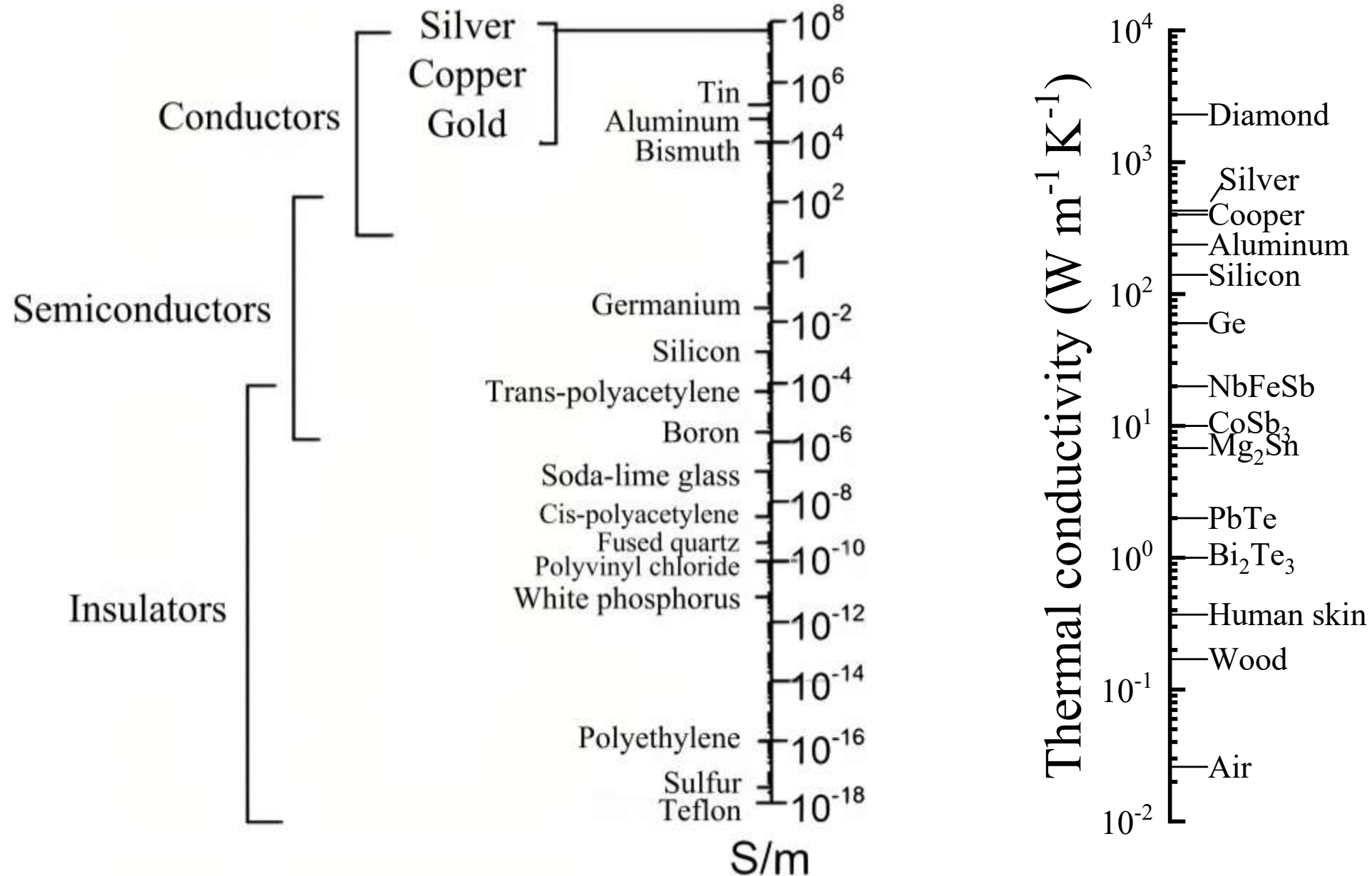
$$\mathbf{J} = \sigma \mathbf{E}$$



$$\mathbf{J} = \kappa dT/dx$$

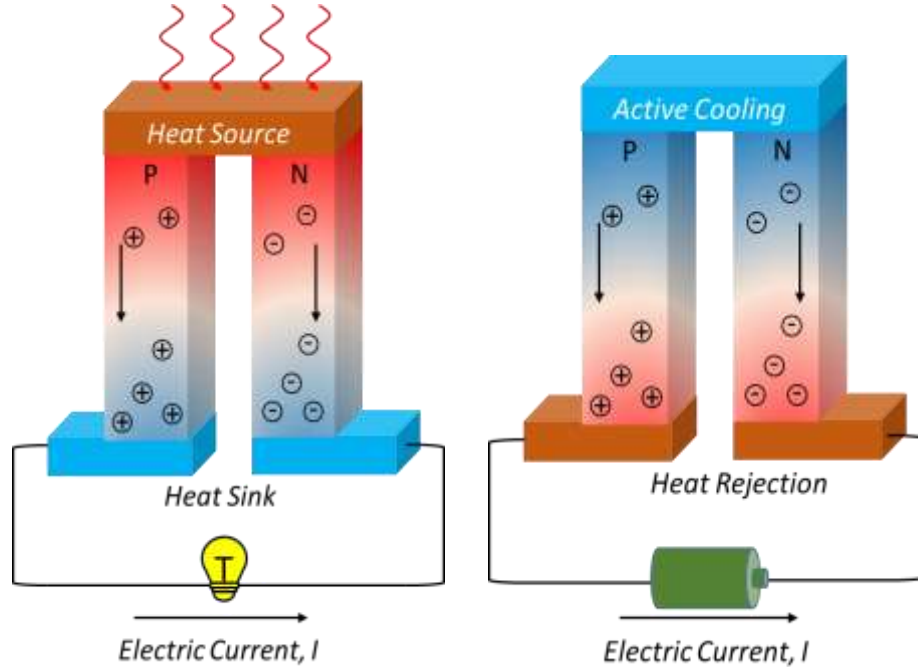
1. Background

Dimensions of electrical and thermal conductivities



1. Background

Thermoelectric Effect



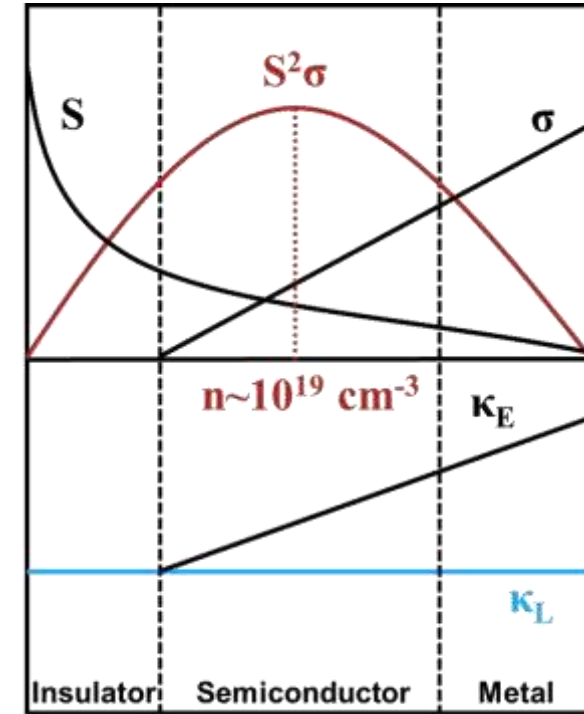
$$ZT = \frac{S^2 \sigma T}{\kappa_E + \kappa_L}$$

Electrical transport

σ : electrical conductivity
 S : Seebeck coefficient

Thermal transport

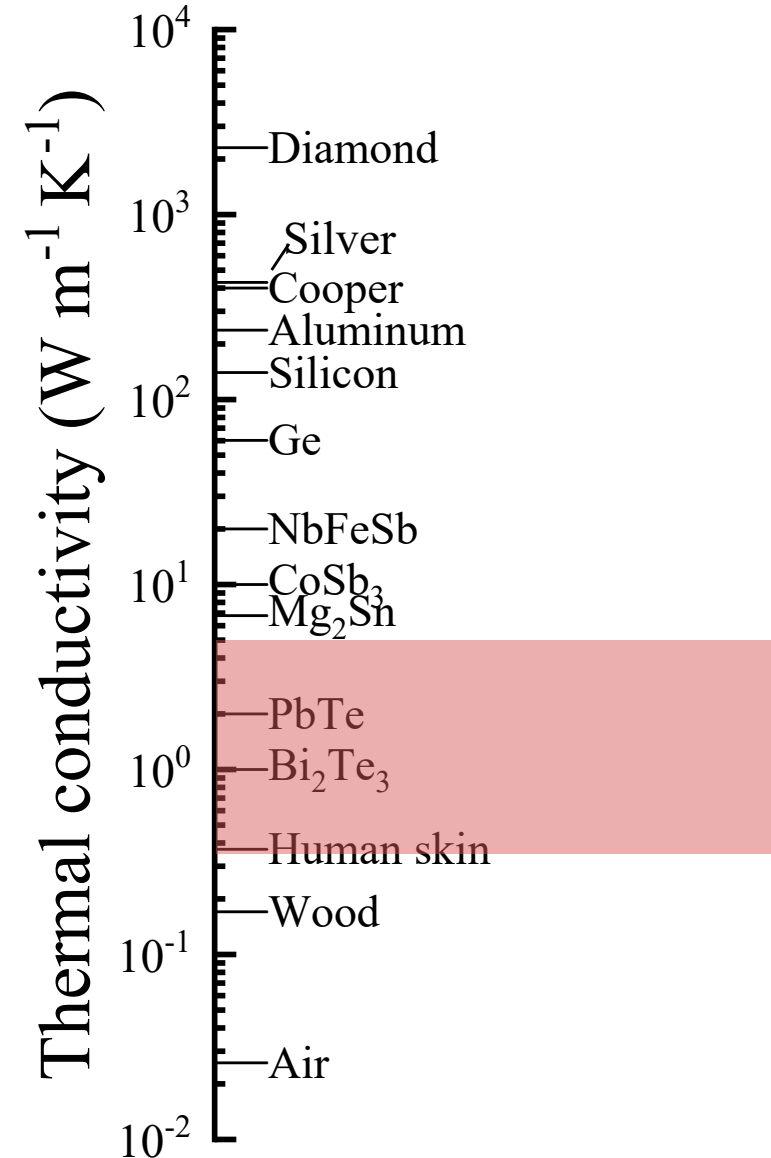
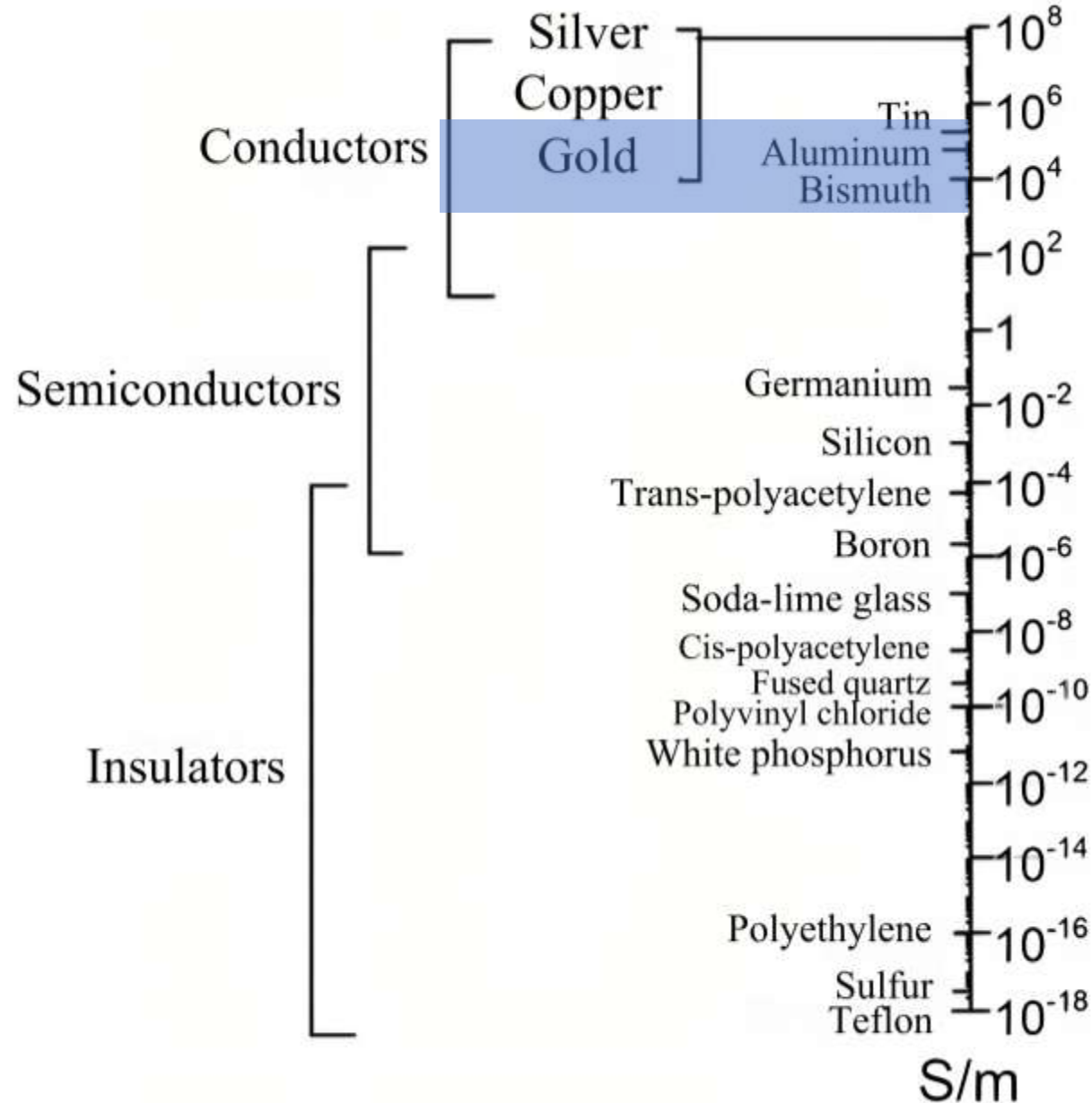
κ_L : lattice thermal conductivity
 κ_E : electronic thermal conductivity



- Adjusting the optimal carrier concentration to reach the peak power factor.
- Reducing the lattice thermal conductivity.

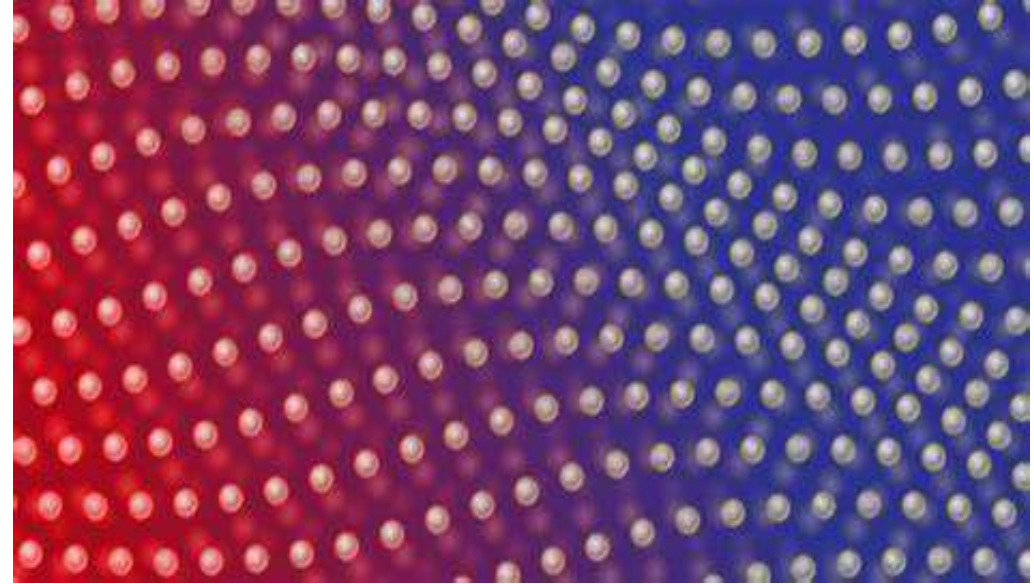
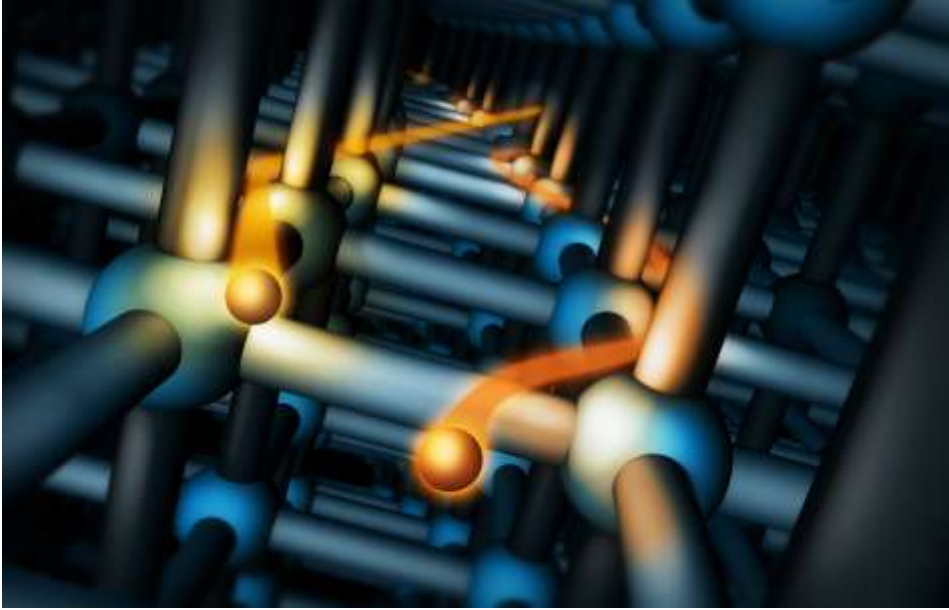
1. Background

Dimensions of electrical and thermal conductivities

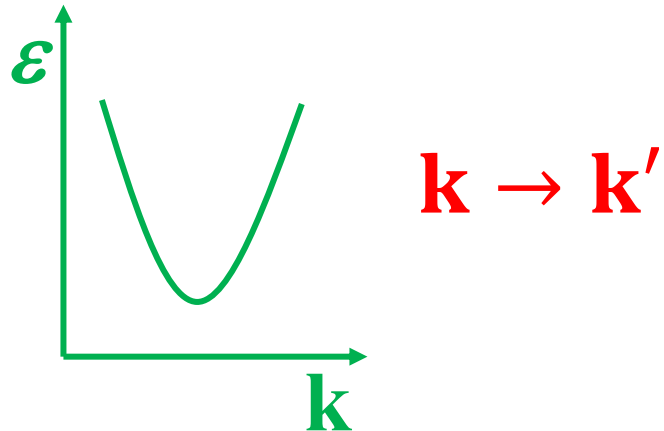


1. Background

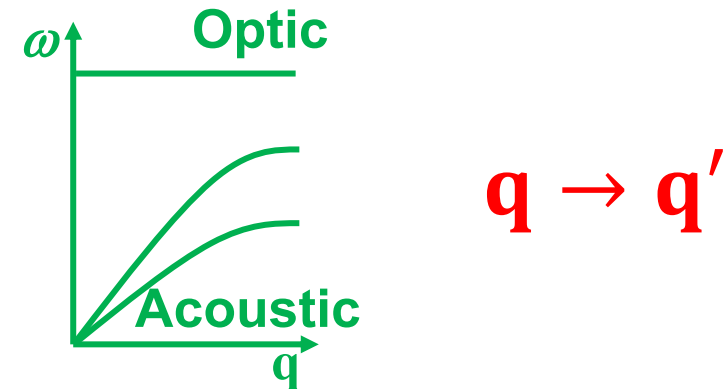
Electron and phonon transport



$$\sigma = \frac{1}{\Omega} \int N(\varepsilon) \mathbf{v}_e^2 \tau_e \left[-\frac{\partial f_0(T, \varepsilon)}{\partial \varepsilon} \right] d\varepsilon$$



$$\kappa_L = \frac{1}{3} \sum_{\mathbf{q}} \hbar \omega_{\mathbf{q}} \mathbf{v}_{\mathbf{q}}^2 \tau_{\mathbf{q}} \frac{\partial N_{\mathbf{q}}^0}{\partial T}$$



1. Background

Classical electron transport model

$$F_i = \int_0^\infty \frac{\epsilon^i d\epsilon}{1 + \exp[\epsilon - \eta]} \quad \eta = \frac{E_F}{k_B T}$$

$$n = 4\pi \left(\frac{2m_D^* k_B T}{h^2} \right)^{1.5} F_{\frac{1}{2}}(\eta) \quad m_D^* = N_v^{2/3} m_b^* \quad \bullet \text{ Effective mass}$$

• Degeneracy

$$S = \pm \frac{k_B}{e} \left(\frac{2F_1(\eta)}{F_0(\eta)} - \eta \right) \quad \sigma = en\mu$$

Acoustic phonon

$$\mu_{H,AP} = \frac{F_{-0.5}}{2F_0} \frac{e\pi\hbar^4}{\sqrt{2}(kT)^{1.5}} \frac{C_l}{E_{\text{def}}^2(m_I)(m_b^*)^{1.5}}$$

Scattering by optical modes: polar crystals

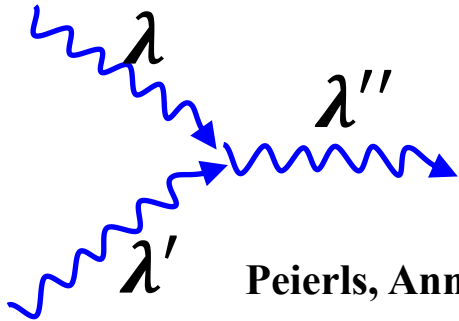
$$\mu = \frac{\gamma(\hbar\omega)^{\frac{3}{2}}}{\pi 2^{\frac{5}{2}} e m^{*\frac{3}{2}}} (e^{\hbar\omega/kT} - 1).$$

Scattering by impurities and imperfections

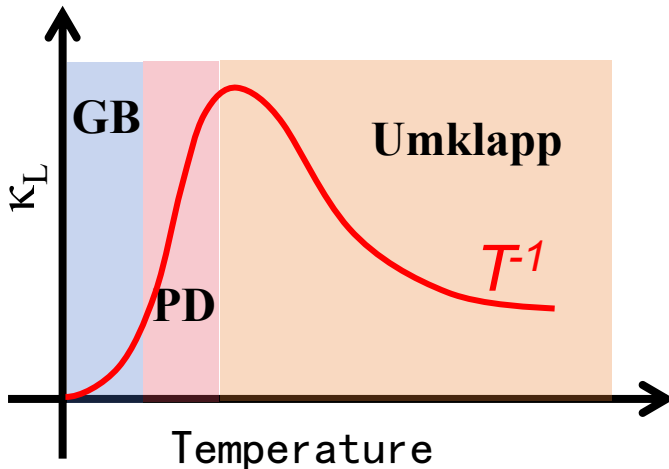
$$\mu_i = \frac{2^{\frac{1}{2}}}{\pi^{\frac{3}{2}}} \frac{\epsilon^2}{Z^2 e^3 m^{*\frac{1}{2}}} \frac{(kT)^{\frac{3}{2}}}{N_i} F(3kT). \quad F(\mathcal{E}) \equiv \ln\left(1 + \frac{8m^*\mathcal{E}}{\varphi^2\hbar^2}\right) - \left(1 + \frac{\varphi^2\hbar^2}{8m^*\mathcal{E}}\right)^{-1}$$

● Phonon Gas Model :

$$\kappa_L = \frac{1}{3} \sum C_V \mathbf{v}_q^2 \tau_q$$



Peierls, Ann. Phys. 3, 1055 (1929)



Matthiessen's rule :

$$\frac{1}{\tau_q} = \frac{1}{\tau_U} + \frac{1}{\tau_{e-p}} + \frac{1}{\tau_{PD}} + \frac{1}{\tau_B} + \dots$$

Phonon- Electron Point Grain
phonon -phonon defect boundary

Slack model for Umklapp
process under Debye phonon
in the high-temperature limit

$$\kappa_L = A \cdot \frac{\bar{M} \theta^3 \delta}{\gamma^2 n^{2/3}} T^{-1}$$

1. Background

Debye-Callaway Model

- Based on the linear phonon dispersion and independent scattering approximations

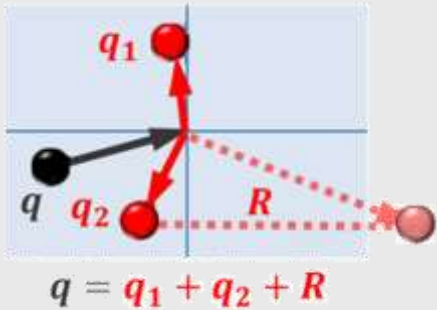
$$\kappa_L = \frac{k_B}{2\pi^2 v_s} \left(\frac{k_B}{\hbar} \right)^3 T^3 \int_0^{\theta_D/T} \tau \frac{x^4 e^x}{(e^x - 1)^2} dx$$



$$\tau^{-1} = A\omega^2 + B\omega^2 + C\omega^4 + \frac{v}{L}$$

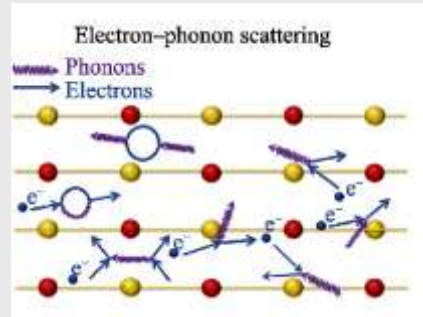
Other scattering mechanisms

Umklapp phonon scattering



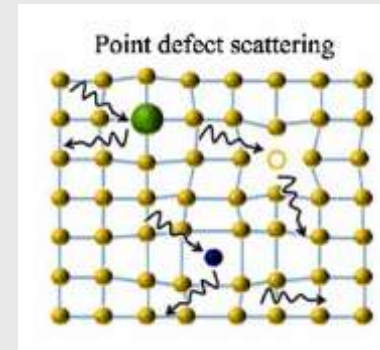
$$\frac{1}{\tau_U} = \frac{\hbar \gamma^2 \omega^2 T}{\bar{M} v^2 \theta_D} \exp\left(-\frac{\theta_D}{3T}\right)$$

Electron-phonon scattering



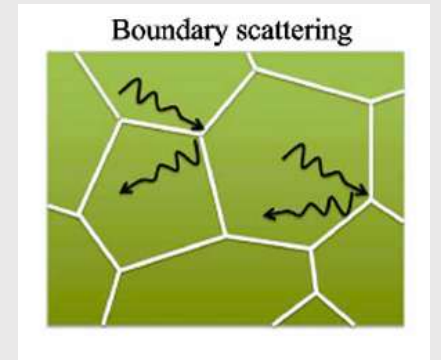
$$\frac{1}{\tau_{EP}} = \frac{E_{def}^2 m^* \omega^2}{2\pi \hbar^3 \rho v_L}$$

Point defect scattering



$$\frac{1}{\tau_{PD}} = \frac{\bar{V} \omega^4}{4\pi v^3} \Gamma$$

Grain boundary scattering

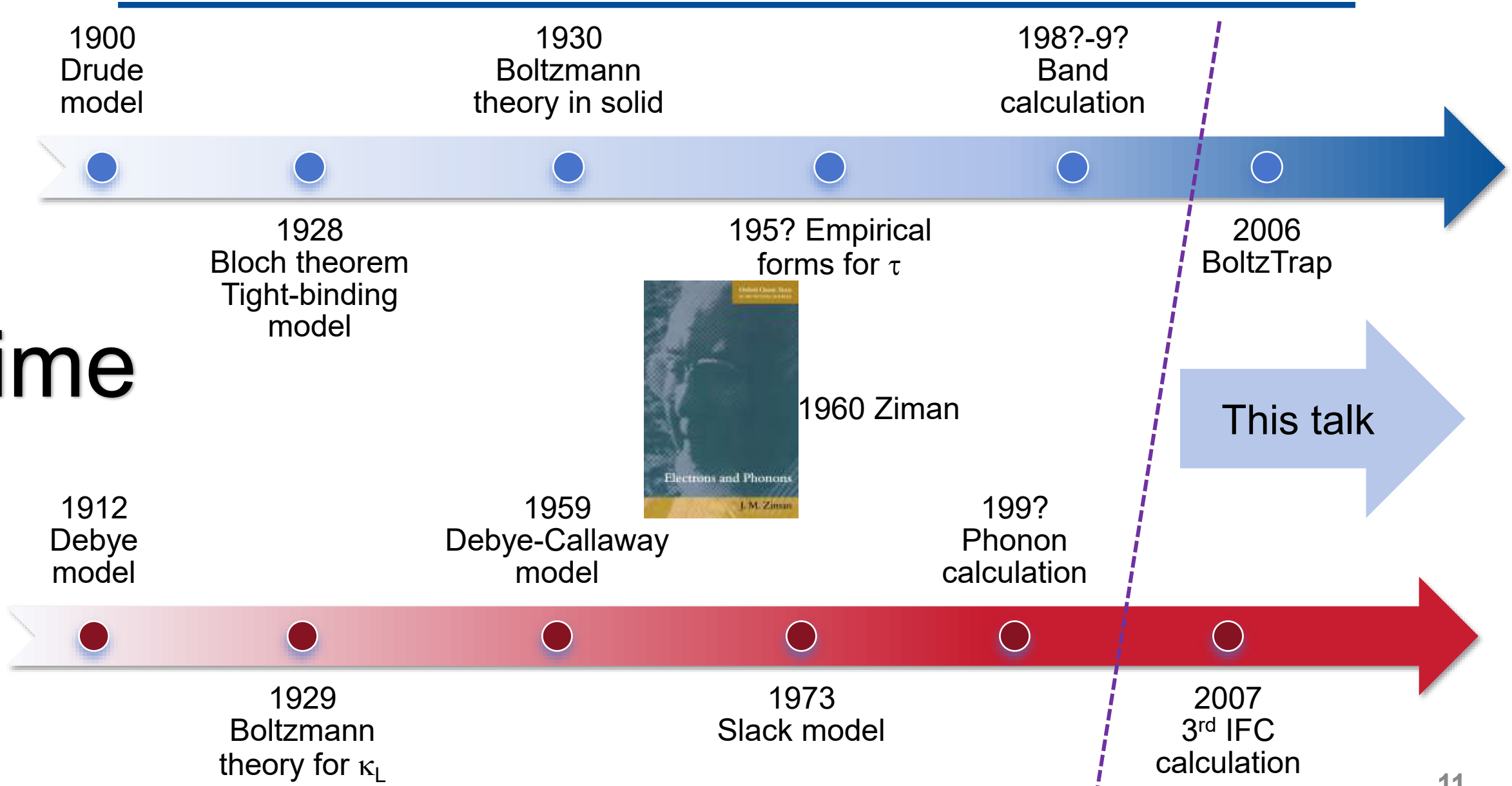


$$\frac{1}{\tau_B} = \frac{v}{L}$$

1. Background

Timeline for the electrical and thermal transport

Time



Overview



Background



Electrical transport



Lattice thermal conductivity

2.1 BTE in Electrical Transport

□ Boltzmann transport equation within the relaxation time approximation

$$\sigma_{\alpha\beta}(\mu, T) = \frac{1}{V} \sum_{n\mathbf{k}} v_{n\mathbf{k}\alpha} v_{n\mathbf{k}\beta} \tau_{n\mathbf{k}} \left[-\frac{\partial f_{\mu}(\varepsilon_{n\mathbf{k}}, T)}{\partial \varepsilon_{n\mathbf{k}}} \right]$$

$$S_{\alpha\beta}(\mu, T) = \frac{1}{eTV} \sigma_{\alpha\beta}(\mu, T)^{-1} \sum_{n\mathbf{k}} v_{n\mathbf{k}\alpha} v_{n\mathbf{k}\beta} \tau_{n\mathbf{k}} (\mu - \varepsilon_{n\mathbf{k}}) \left[-\frac{\partial f_{\mu}(\varepsilon_{n\mathbf{k}}, T)}{\partial \varepsilon_{n\mathbf{k}}} \right]$$

$$f_{\mu} = \frac{1}{\exp(\varepsilon_{n\mathbf{k}} - \mu) + 1}$$

Fermi-Dirac Distribution
 μ Fermi level $\varepsilon_{n\mathbf{k}}$ band energy

$\mathbf{v}_{n\mathbf{k}}$

Group velocity

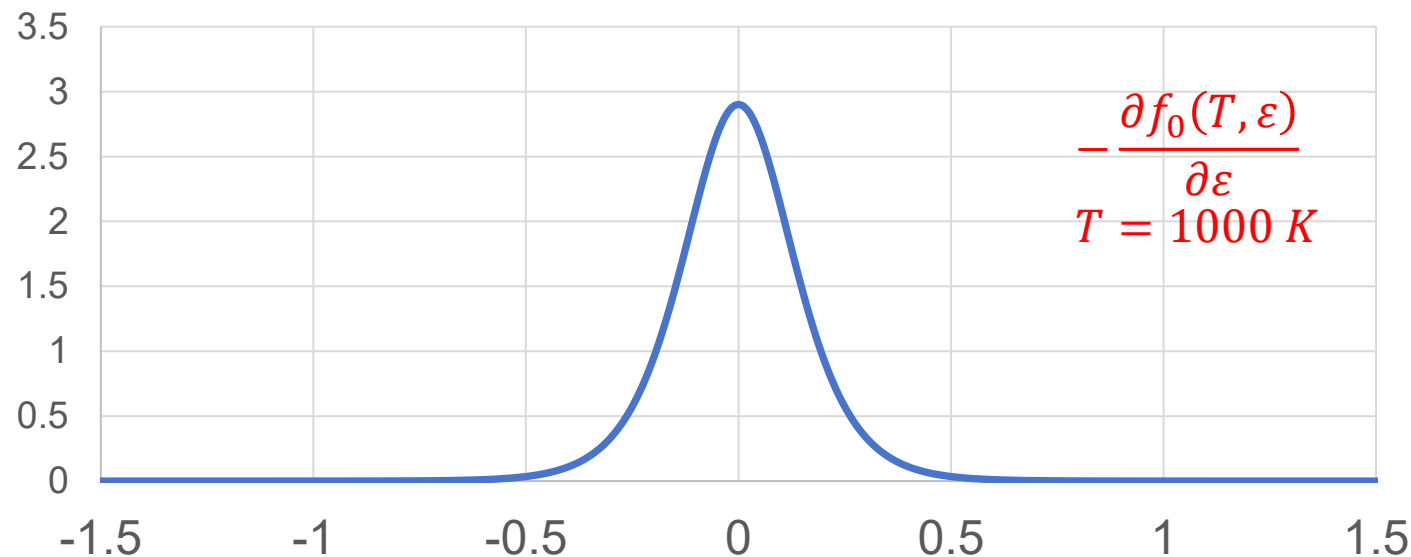
$\tau_{n\mathbf{k}}$

Relaxation time

2.1 BTE in Electrical Transport

Effective Range of Electronic States

$$\sigma_{\alpha\beta}(\mu, T) = \frac{1}{V} \sum_{n\mathbf{k}} v_{n\mathbf{k}\alpha} v_{n\mathbf{k}\beta} \tau_{n\mathbf{k}} \left[- \frac{\partial f_{\mu}(\varepsilon_{n\mathbf{k}}, T)}{\partial \varepsilon_{n\mathbf{k}}} \right]$$

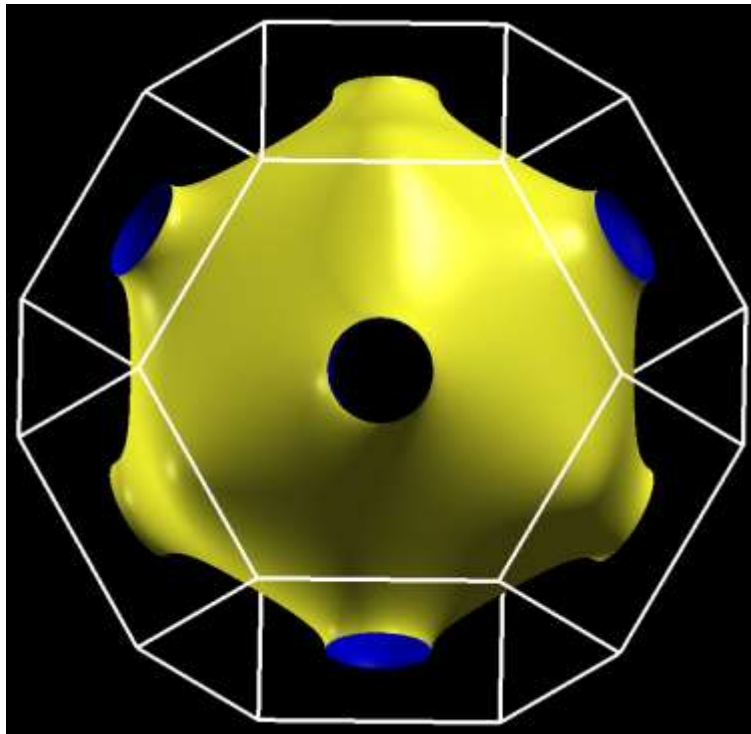


- Only electronic states within a few $k_B T$ around E_F contribute significantly to transport
- The importance of electronic states far from E_F decreases exponentially
- The effective energy range expands with increasing temperature

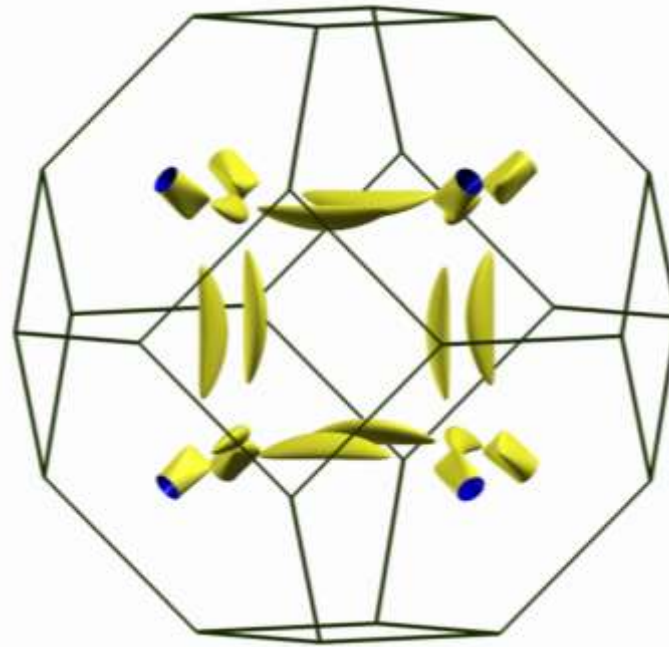
2.1 BTE in Electrical Transport

- Fermi surface at the Fermi level: the origin of electrical conductivity in metals and heavily-doped semiconductors

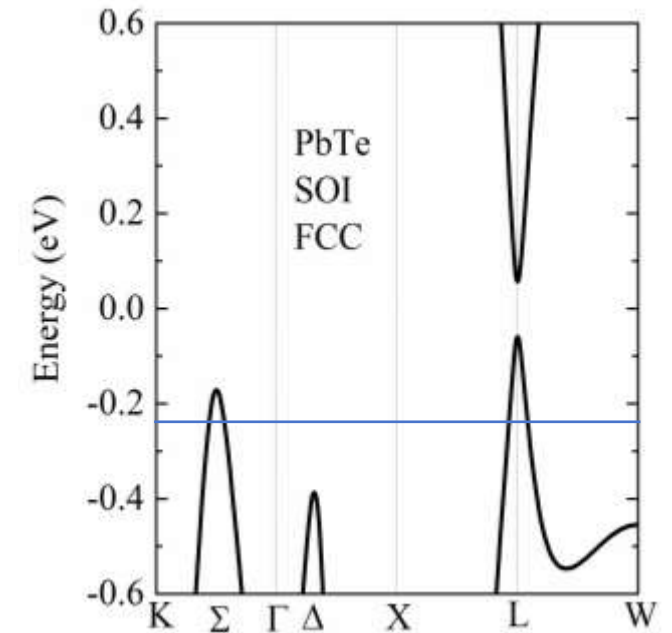
$$\sigma_{\alpha\beta}(\mu, T) = \frac{1}{V} \sum_{n\mathbf{k}} v_{n\mathbf{k}\alpha} v_{n\mathbf{k}\beta} \tau_{n\mathbf{k}} \left[- \frac{\partial f_{\mu}(\varepsilon_{n\mathbf{k}}, T)}{\partial \varepsilon_{n\mathbf{k}}} \right]$$



Fermi Surface at E_F in Metal Cu

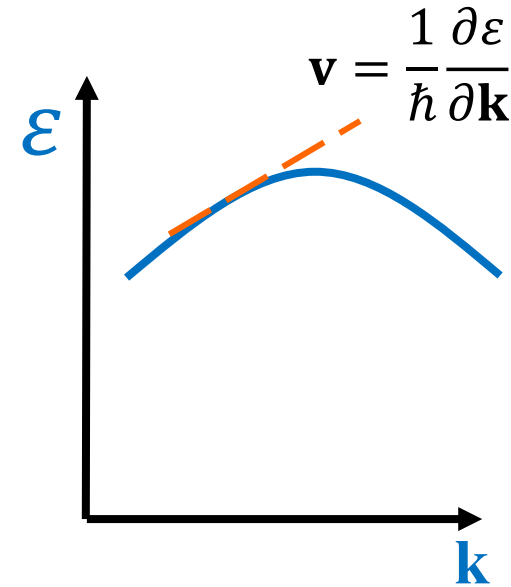
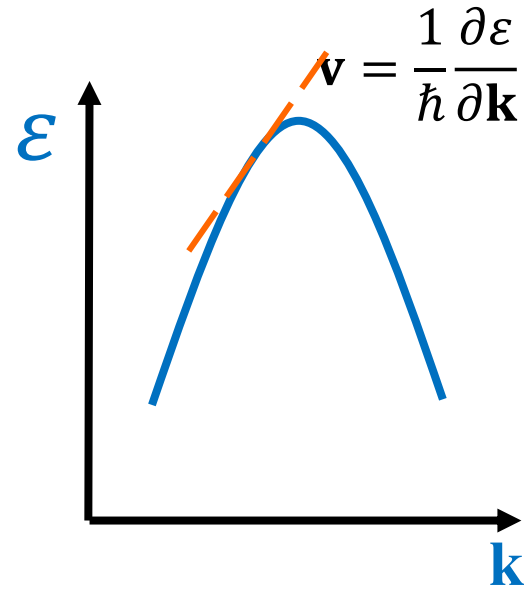


Fermi surface in heavily doped semiconductors reflects the band degeneracy.



2.1 BTE in Electrical Transport

$$\sigma_{\alpha\beta}(\mu, T) = \frac{1}{V} \sum_{n\mathbf{k}} \mathbf{v}_{n\mathbf{k}\alpha} \mathbf{v}_{n\mathbf{k}\beta} \tau_{n\mathbf{k}} \left[- \frac{\partial f_{\mu}(\varepsilon_{n\mathbf{k}}, T)}{\partial \varepsilon_{n\mathbf{k}}} \right]$$



The average electron group velocity lies within the range of 10^4 - 10^5 m/s

2.1 BTE in Electrical Transport

$$\sigma_{\alpha\beta}(\mu, T) = \frac{1}{V} \sum_{n\mathbf{k}} v_{n\mathbf{k}\alpha} v_{n\mathbf{k}\beta} \tau_{n\mathbf{k}} \left[-\frac{\partial f_{\mu}(\varepsilon_{n\mathbf{k}}, T)}{\partial \varepsilon_{n\mathbf{k}}} \right]$$

$$\tau: 10^{-15} \sim 10^{-14} \text{ s}$$

Matthiessen's Rule

$$\frac{1}{\tau_{n\mathbf{k}}} = \frac{1}{\tau_{\text{e-ph}}} + \frac{1}{\tau_{\text{IMP}}} \dots$$

The mobility is determined by the integral of group velocity and relaxation time.

2.1 BTE in Electrical Transport

Relaxation time under full electron-phonon interaction (FEPI)

$$\frac{1}{\tau_{\mathbf{k}}} = \frac{2\pi}{\hbar} \sum_{\mathbf{k}'} |\langle \mathbf{k}' | \partial_{\mathbf{q}} V | \mathbf{k} \rangle|^2 [(f_{\mathbf{k}'} + n_{\mathbf{q}}) \delta(\varepsilon_{\mathbf{k}} - \varepsilon_{\mathbf{k}'} + \hbar\omega_{\mathbf{q}}) \delta_{\mathbf{k}+\mathbf{q}, \mathbf{k}'+\mathbf{G}} \\ + (1 - f_{\mathbf{k}'} + n_{\mathbf{q}}) \delta(\varepsilon_{\mathbf{k}} - \varepsilon_{\mathbf{k}'} - \hbar\omega_{\mathbf{q}}) \delta_{\mathbf{k}-\mathbf{q}, \mathbf{k}'+\mathbf{G}}] \left(1 - \frac{\mathbf{v}_{\mathbf{k}'} \cdot \mathbf{v}_{\mathbf{k}}}{|\mathbf{v}_{\mathbf{k}'}| |\mathbf{v}_{\mathbf{k}}|}\right) .$$

Relaxation time under constant values of EPI matrix

acoustic deformation potential
(ADP) short range

$$\frac{1}{\tau_{\text{ADP}, n\mathbf{k}}} = \frac{2\pi k_{\text{B}} E_{\text{def}}^2 T}{\hbar G V} \sum_{m\mathbf{k}'} \delta(\varepsilon_{n\mathbf{k}} - \varepsilon_{m\mathbf{k}'})$$

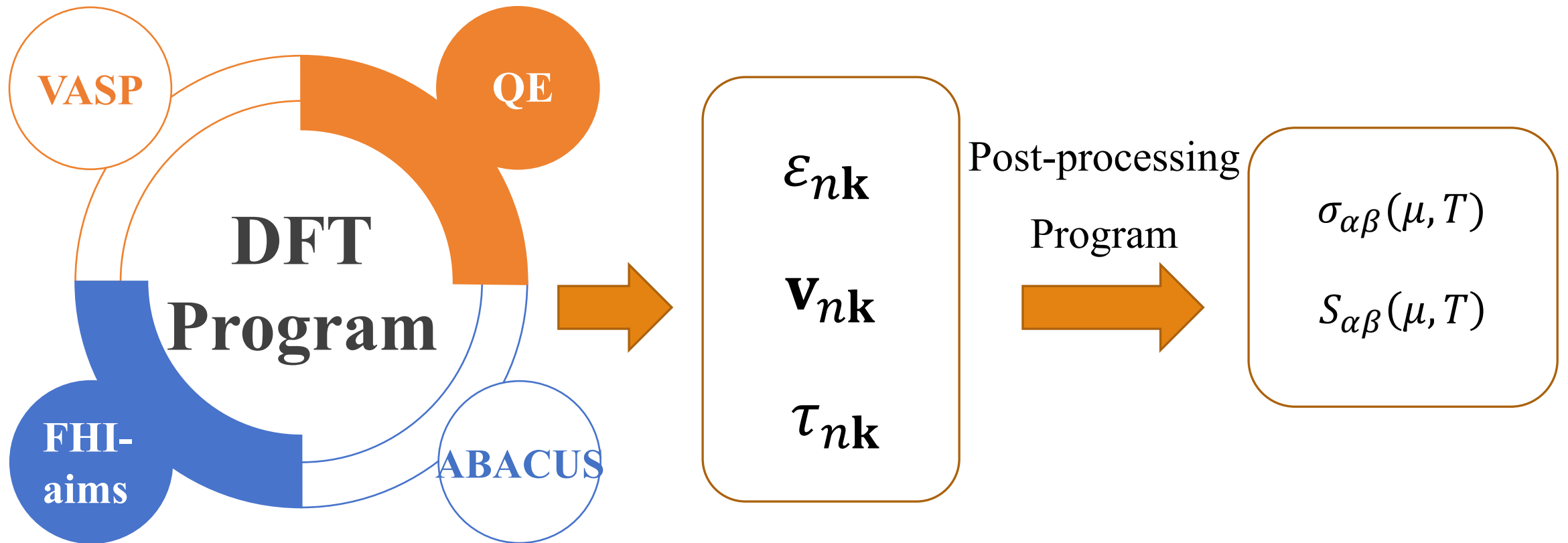
Bardeen-Shockley

polar optical phonon
(POP) long range

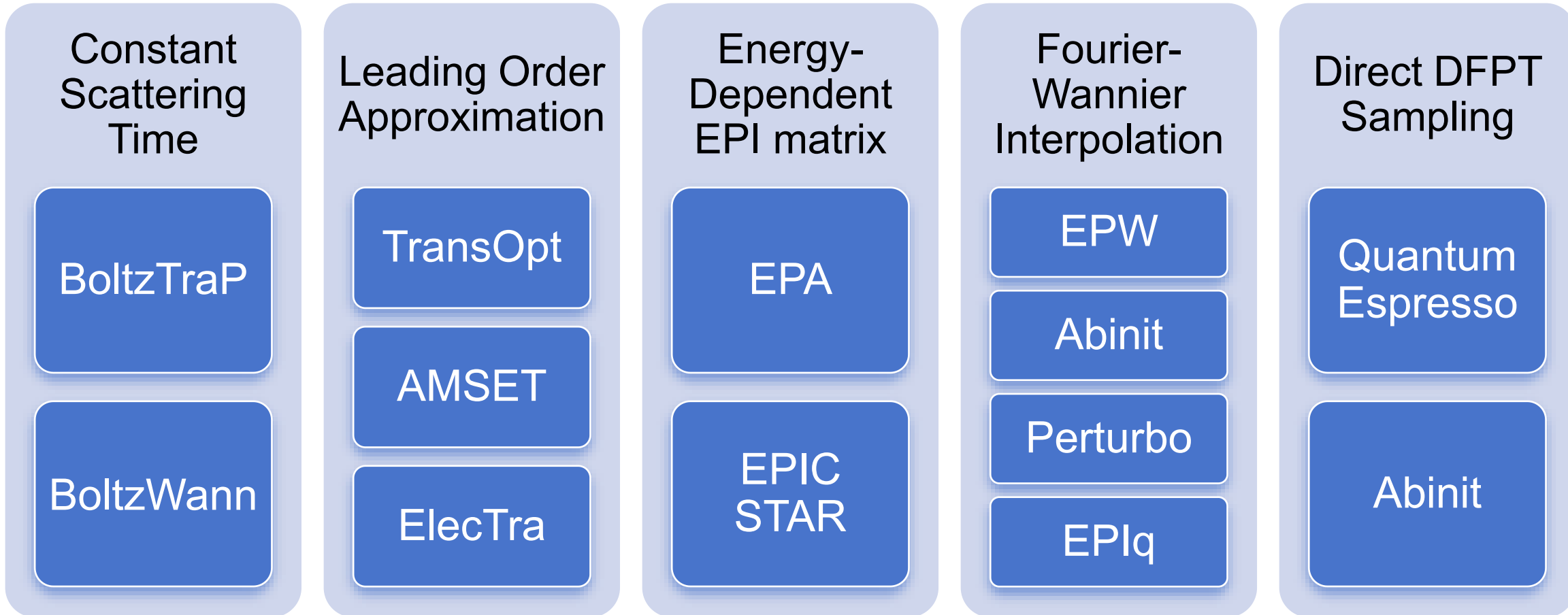
$$\frac{1}{\tau_{\text{POP}, n\mathbf{k}}} = \sum_{m\mathbf{k}'} \frac{\pi \omega_{\text{po}} e^2}{V |\mathbf{k}' - \mathbf{k}|^2 \kappa_0} \left(\frac{1}{\varepsilon_{\infty}} - \frac{1}{\varepsilon_s} \right) (2N_{\omega} + 1) \delta(\varepsilon_{n\mathbf{k}} - \varepsilon_{m\mathbf{k}'})$$

Frölich

2.2 Softwares for Electrical Transport



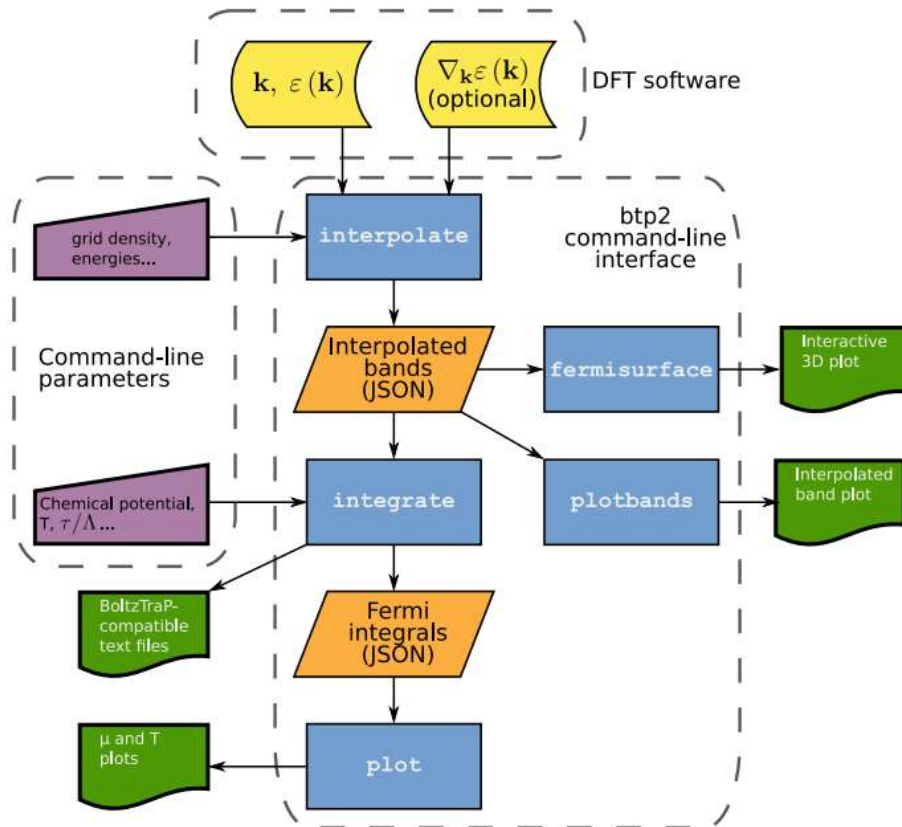
2.2 Softwares for Electrical Transport



Complexity, Cost, Completeness

Acknowledgement to Prof. Tianqi Deng
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Computer Physics Communications 175 (2006) 67–71

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BoltzTraP. A code for calculating band-structure dependent quantities [☆]

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BoltzTraP2, a program for interpolating band structures and calculating semi-classical transport coefficients [☆]

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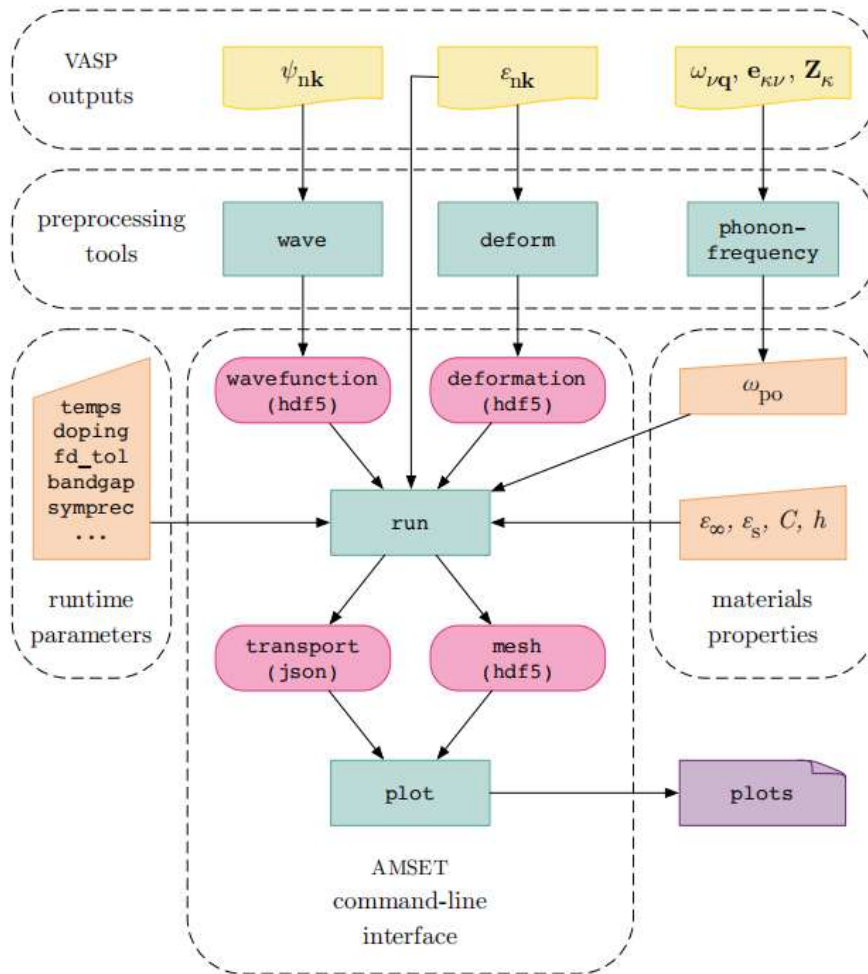
^b nanomat/QMAT/CESAM and Department of Physics, Université de Liège, allée du 6 août, 19, B-4000 Liège, Belgium

^c European Theoretical Spectroscopy Facility, Belgium



- Early Release & Broad Application: including Seebeck coefficient and other properties under the constant relaxation time approximation (CRTA).
- High-Throughput Suitable: ideal for high-throughput computational workflows.
- Star function method for band interpolation

2.2 Softwares for Electrical Transport Amset



Supplementary Figure 3. Schematic of the AMSET program indicating the typical inputs and outputs, command-line tools, and program flow.

NATURE COMMUNICATIONS | 12:2222 (2021)

- Eliminates the computationally expensive DFPT matrix element calculations.
- Anisotropy models and scattering mechanisms: ADP, POP, PI, and IMP
- Utilize BoltzTraP2 for band structure interpolation

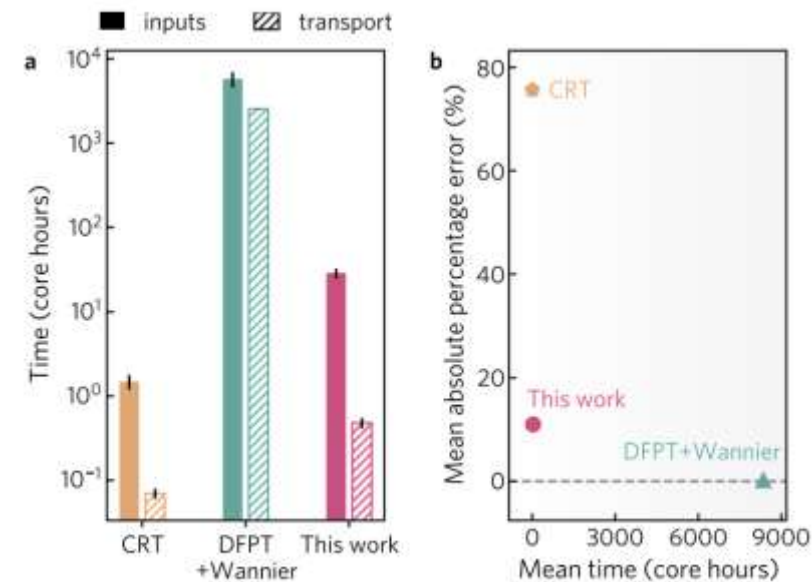


Fig. 2 Comparison of speed against accuracy for transport calculations.

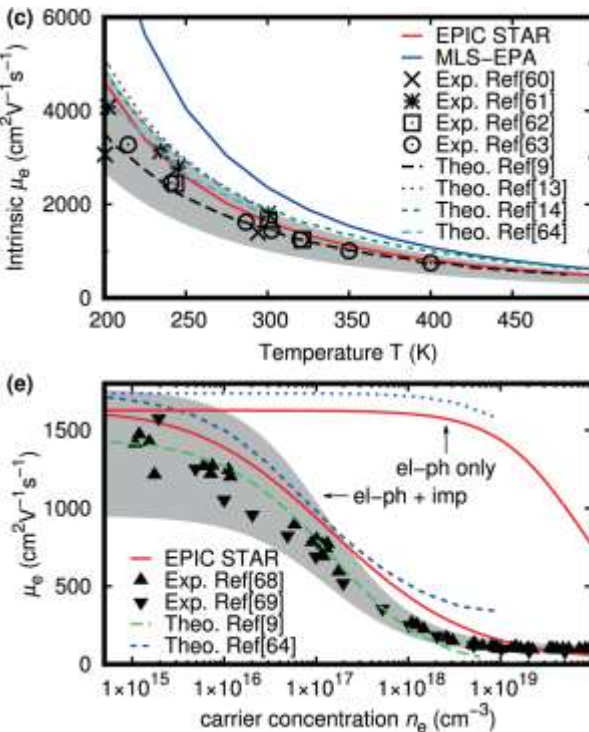
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EPIC STAR: a reliable and efficient approach for phonon- and impurity-limited charge transport calculations

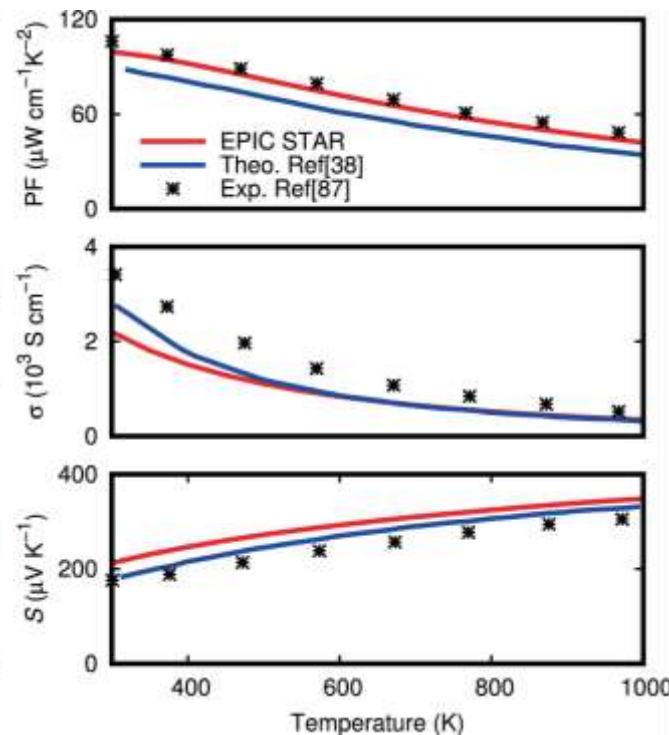
Tianqi Deng, Gang Wu , Michael B. Sullivan, Zicong Marvin Wong, Kedar Hippalgaonkar, Jian-Sheng Wang & Shuo-Wang Yang 

npj Computational Materials 6, Article number: 46 (2020) | [Cite this article](#)

Silicon



NbFeSb



EPIC STAR

- Generalized Eliashberg function for short-range electron-phonon scattering
- Analytical expressions for long-range electron-phonon and electron-impurity scattering

Utilize BoltzTraP2 for band interpolation

$$\alpha_l^2 F(E, \omega) = \frac{\omega}{\rho(E)} \sum_{mn} \int_{BZ} \frac{d\mathbf{k}}{\Omega_{BZ}} \frac{d\mathbf{q}}{\Omega_{BZ}} \frac{|g_{nml}^S(\mathbf{k}, \mathbf{q})|^2}{\omega_{l\mathbf{q}}} \delta(E - \varepsilon_{n\mathbf{k}}) \times \delta(\hbar\omega + E - \varepsilon_{m\mathbf{k}+\mathbf{q}}) [\delta(\omega - \omega_{l\mathbf{q}}) + \delta(\omega + \omega_{l\mathbf{q}})]$$

$$\tau_l^{-1}(E, \mu, T) = 2\pi \left\{ \int_0^{+\infty} \alpha_l^2 F(E, \omega) [f(E + \hbar\omega - \mu, T) + n(\hbar\omega, T)] d\omega + \int_{-\infty}^0 \alpha_l^2 F(E, \omega) [1 - f(E + \hbar\omega - \mu, T) + n(\hbar\omega, T)] d\omega \right\}$$

$$\tau_{\text{POP},l}^{-1}(E) = C_{\text{POP},l}^2 \frac{\Omega}{\pi \hbar^2} \sqrt{\frac{m_b(E)}{2E}} \left\{ \sinh^{-1} \sqrt{\frac{E}{\hbar\omega_l}} [n(\hbar\omega_l, T) + f(E + \hbar\omega_l - \mu, T)] + \sinh^{-1} \sqrt{\frac{E}{\hbar\omega_l} - 1} [n(\hbar\omega_l, T) + 1 - f(E - \hbar\omega_l - \mu, T)] \right\}$$

$$\tau_{\text{imp}}^{-1}(E) \approx \frac{n_{\text{imp}} e^4}{16 \sqrt{2m_b(E)} \pi \epsilon^2 \epsilon_0^2} \frac{1}{\sqrt{E^3}} \left[\ln \left(1 + \frac{8m_b(E)EL^2}{\hbar^2} \right) - \frac{8m_b(E)EL^2}{\hbar^2 + 8m_b(E)EL^2} \right]$$



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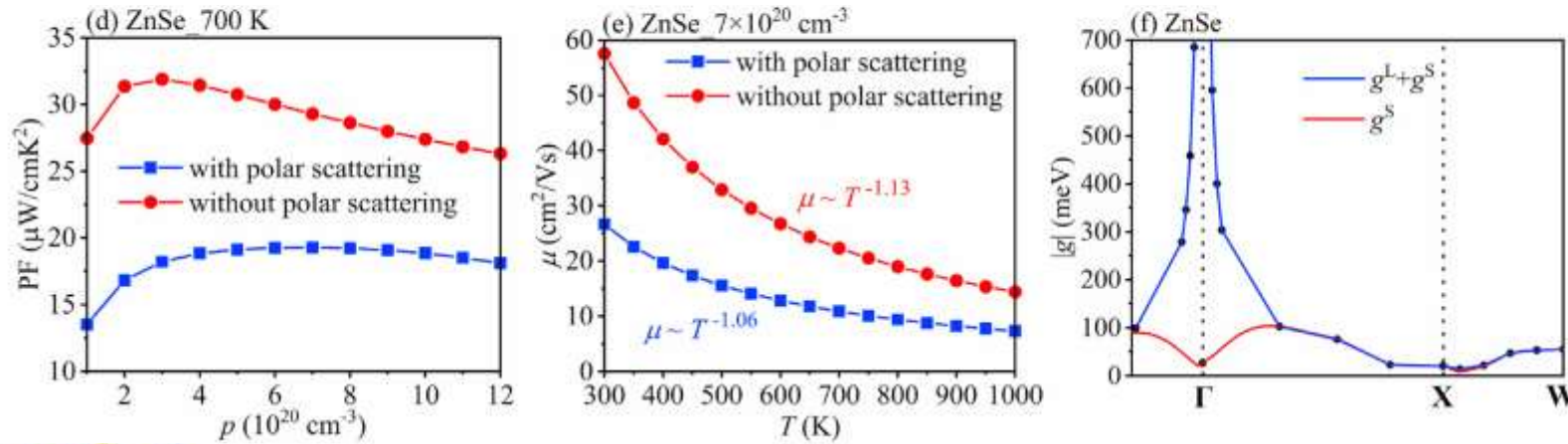
Electrical transport limited by electron-phonon coupling from Boltzmann transport equation: An *ab initio* study of Si, Al, and MoS₂

Wu Li*

Scientific Computing & Modelling NV, De Boelelaan 1083, 1081 HV Amsterdam, The Netherlands

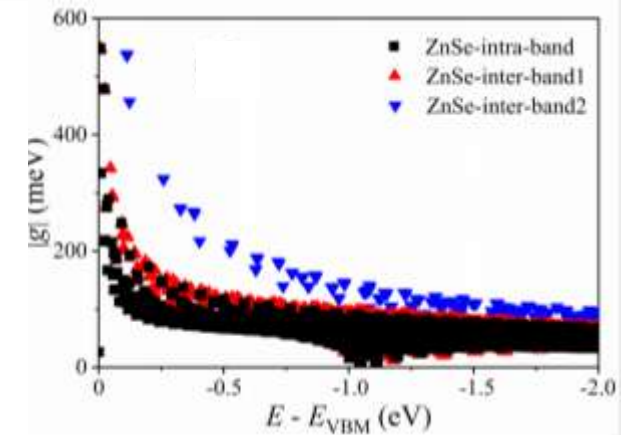
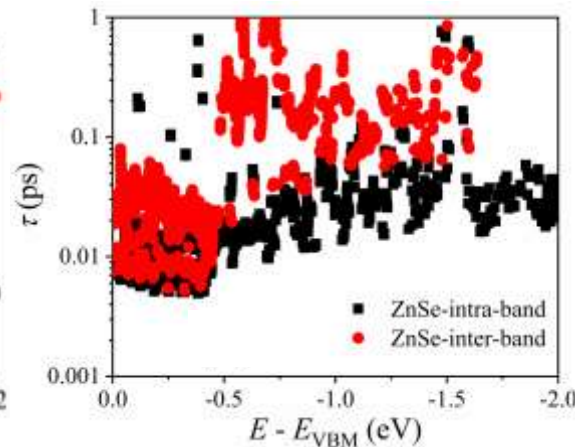
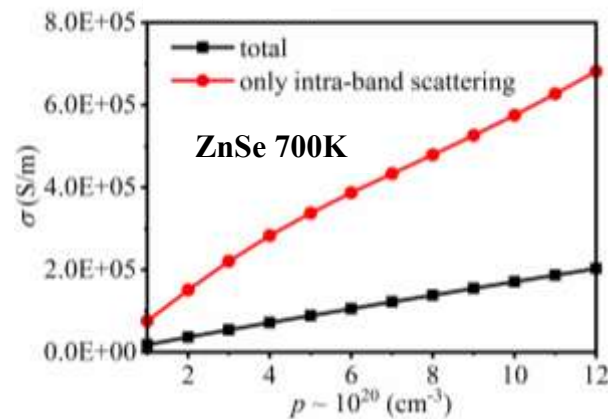
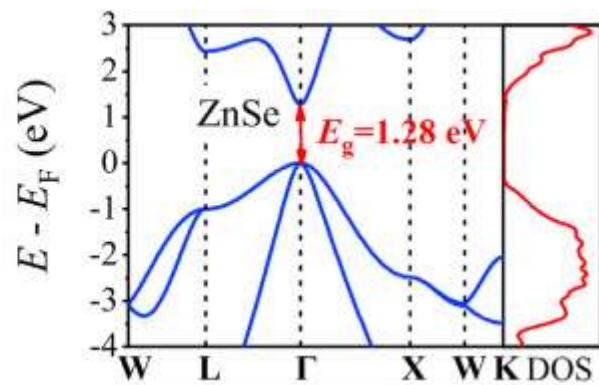
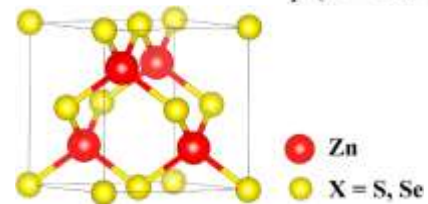
(Received 24 March 2015; published 4 August 2015)

- Relaxation times based on *ab initio* electron-phonon interaction. $g_{mn\nu}(\mathbf{k}, \mathbf{q}) = \langle m\mathbf{k} + \mathbf{q} | \partial_{\nu\mathbf{q}} \hat{V}_{DFT} | n\mathbf{k} \rangle$
- Only can calculate the mobility.
- Requires third-party post-processing tools (e.g., TransOpt) to obtain the full electrical transport results (Seebeck coefficient, electrical conductivity, electrical thermal conductivity, *etc*).



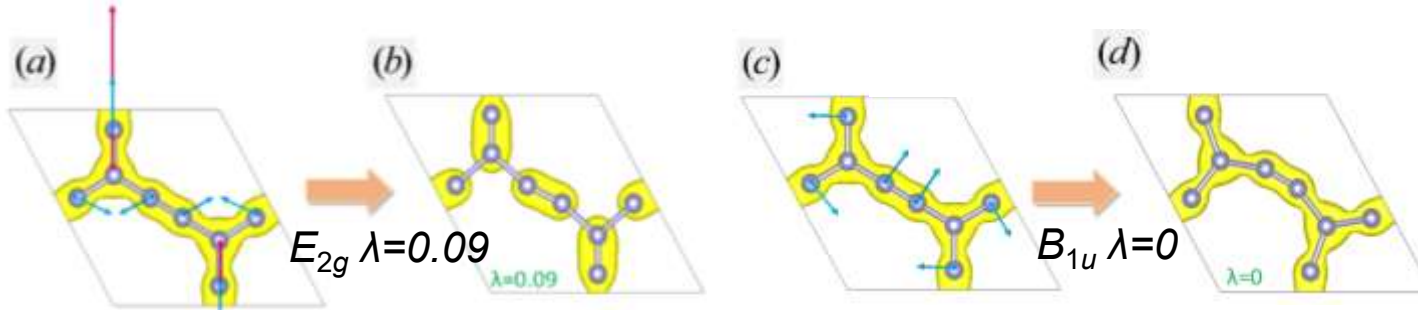
$$g_{mn\lambda}^L(\mathbf{k}, \mathbf{q}) = i \frac{4\pi}{\Omega} \frac{e^2}{4\pi\epsilon_0} \sum_{\kappa} \left(\frac{\hbar}{2NM_{\kappa}\omega_{\mathbf{q}\lambda}} \right)^{1/2} \times \sum_{\mathbf{G} \neq \mathbf{q}} \frac{(\mathbf{q} + \mathbf{G}) \cdot \mathbf{Z}_{\kappa}^* \cdot \mathbf{e}_{\kappa\lambda}(\mathbf{q})}{(\mathbf{q} + \mathbf{G}) \cdot \epsilon^{\infty} \cdot (\mathbf{q} + \mathbf{G})} \times \langle \psi_{m\mathbf{k}+\mathbf{q}} | e^{i(\mathbf{q}+\mathbf{G}) \cdot \mathbf{r}} | \psi_{n\mathbf{k}} \rangle$$

Due to the strong polarity, the polar optical phonon (POP) scattering is the dominant mechanism for the electrical transport in ZnX.



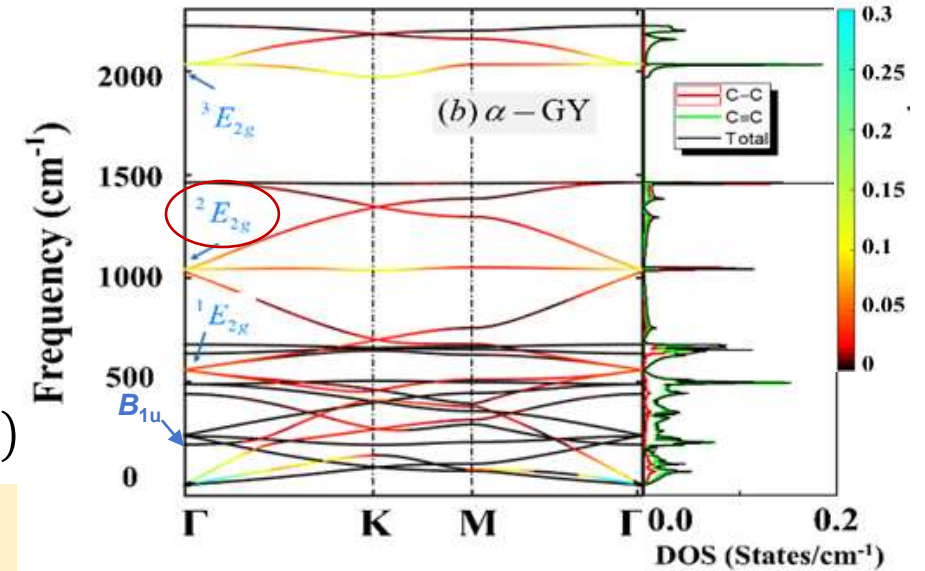
Due to the triple degeneracy near the VBM, the inter-band scattering also has detrimental contributions to the electrical conductivities.

□ Origin of the strong E_{2g} - optical phonon coupling in α -graphyne



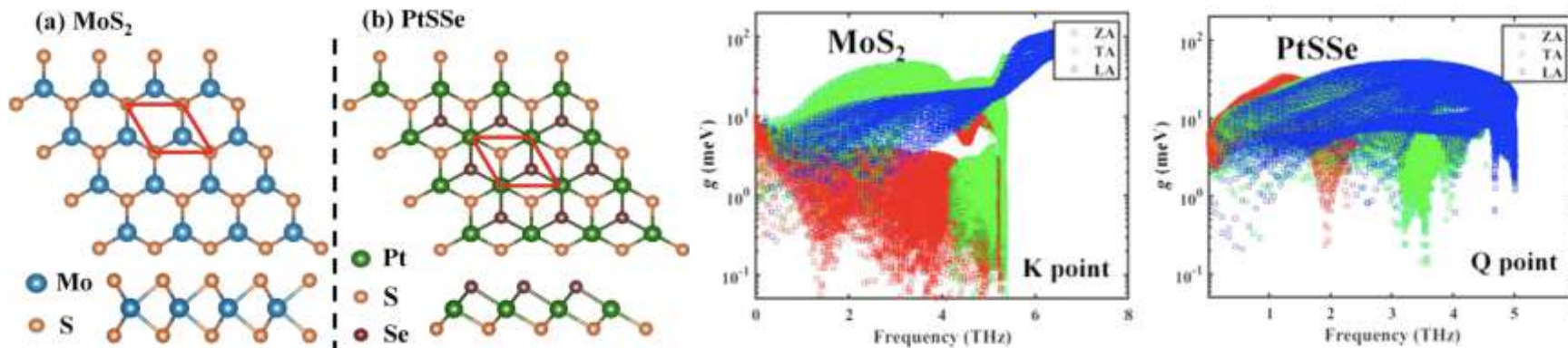
El-ph coupling strength: $\lambda_{\mathbf{qv}} = \frac{2}{\hbar\omega_{\mathbf{qv}}N(\epsilon_f)} \sum_{\mathbf{k}mn} |g_{m,n,\mathbf{k}}^{\mathbf{qv}}|^2 \times \delta(\epsilon_{n\mathbf{k}} - \epsilon_f) \delta(\epsilon_{m\mathbf{k}+\mathbf{q}} - \epsilon_f)$

➤ a larger $\lambda_{\mathbf{qv}}$ of E_{2g} phonon can be understandable from the group theory. In real space, E_{2g} phonon greatly disrupts electronic state.



Nanoscale, 11, 10828 (2019)

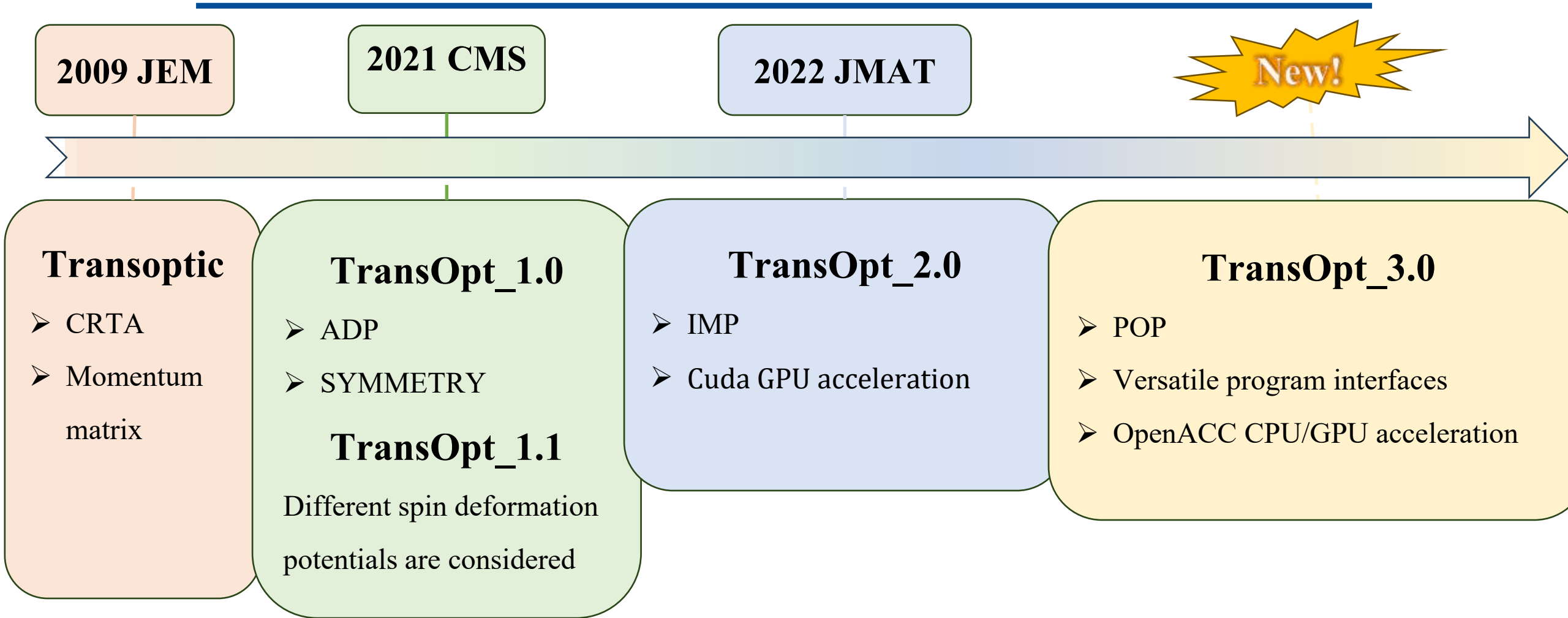
□ ZA (out-of-plane acoustic) phonon in TMD monolayers



Lack of horizontal mirror symmetry in PtSSe enables a strong el-ZA ph coupling

Mater. Today Phys., 15, 100277 (2020)

2.3 TransOpt



J. Electron. Mater., 38, 1397 (2009)
Comput. Mater. Sci., 186, 110074 (2021)
npj Comput. Mater., 9, 190 (2023)
J. Materiomics, 8, 1222-1229 (2022)

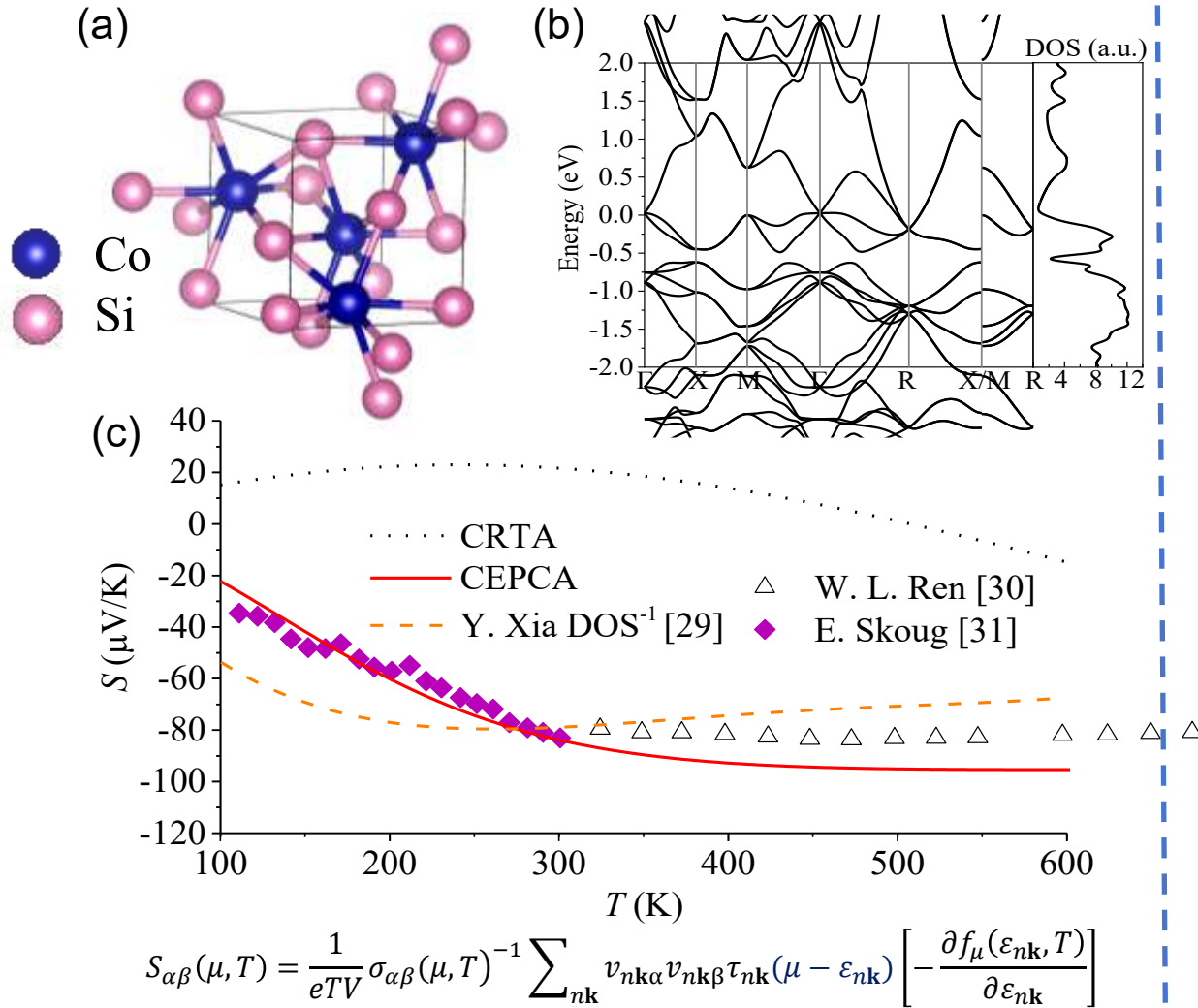
2.3 Formulas in TransOpt

$\frac{1}{\tau_{\text{e-ph}}}$		acoustical phonon (ADP)	$\frac{1}{\tau_{\text{ADP},n\mathbf{k}}} = \frac{2\pi k_{\text{B}} E_{\text{def}}^2 T}{\hbar G V} \sum_{m\mathbf{k}'} \delta(\varepsilon_{n\mathbf{k}} - \varepsilon_{m\mathbf{k}'})$	Bardeen-Shockley
		polar optical phonon (POP)	$\frac{1}{\tau_{\text{POP},n\mathbf{k}}} = \sum_{m\mathbf{k}'} \frac{\pi \omega_{\text{po}} e^2}{V \mathbf{k}' - \mathbf{k} ^2 \kappa_0} \left(\frac{1}{\varepsilon_{\infty}} - \frac{1}{\varepsilon_{\text{s}}} \right) (2N_{\omega} + 1) \delta(\varepsilon_{n\mathbf{k}} - \varepsilon_{m\mathbf{k}'})$	Frölich
		...		
$\frac{1}{\tau_{\text{IMP}}}$		ionized impurity (IMP)	$\frac{1}{\tau_{\text{IMP},n\mathbf{k}}} = \sum_{m\mathbf{k}'} \frac{2\pi n_{\text{imp}} Z_{\text{imp}}^2 e^4}{V \hbar (\varepsilon_{\text{s}} \kappa_0)^2 (L_{\text{D}}^{-2} + \mathbf{k}' - \mathbf{k} ^2)^2} \delta(\varepsilon_{n\mathbf{k}} - \varepsilon_{m\mathbf{k}'})$	Brooks-Herring

$$L_{\text{D}} = \sqrt{\frac{\varepsilon_{\text{s}} \kappa_0 k_{\text{B}} T}{e^2 n_0}}$$

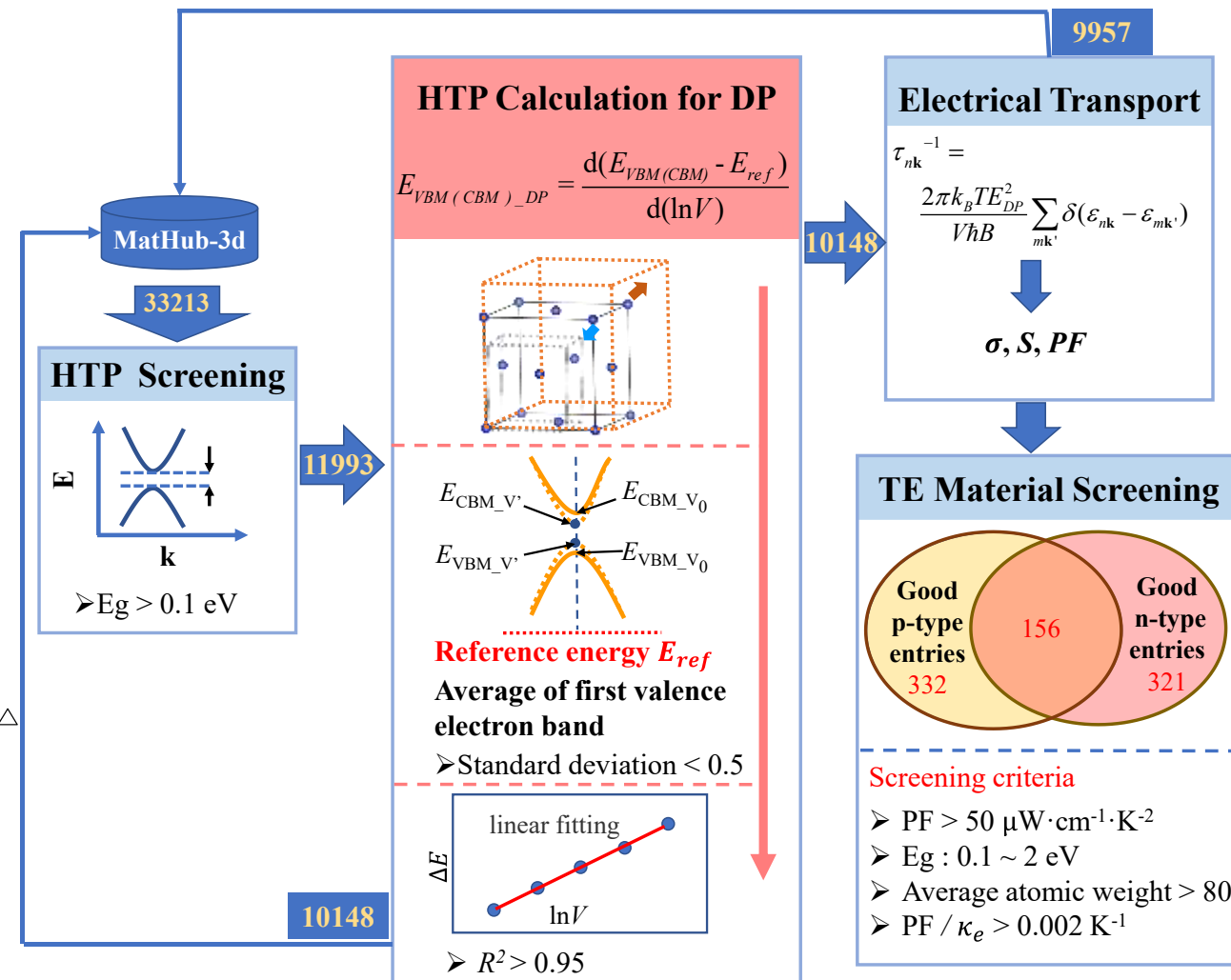
E_{def} Deformation potential; G Modulus; n_{imp} Impurity concentration; Z_{imp} Impurity charge; ε_{s} Static dielectric; ε_{∞} high frequency dielectric; κ_0 vacuum dielectric constant; L_{D} Debye screening length; n_0 carrier concentration; ω_{po} Effective polar phonon frequency

$$\frac{1}{\tau_{\text{ADP},nk}} = \frac{2\pi k_B E_{\text{def}}^2 T}{\hbar G V} \sum_{m\mathbf{k}'} \delta(\varepsilon_{n\mathbf{k}} - \varepsilon_{m\mathbf{k}'})$$



- Higher accuracy for Seebeck coefficient than CRTA, due to explicit treatment of relaxation time.

Comp. Mater. Sci., 186, 110074 (2021)

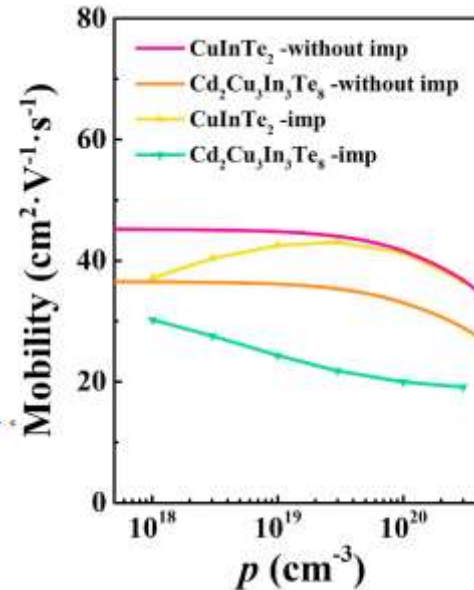
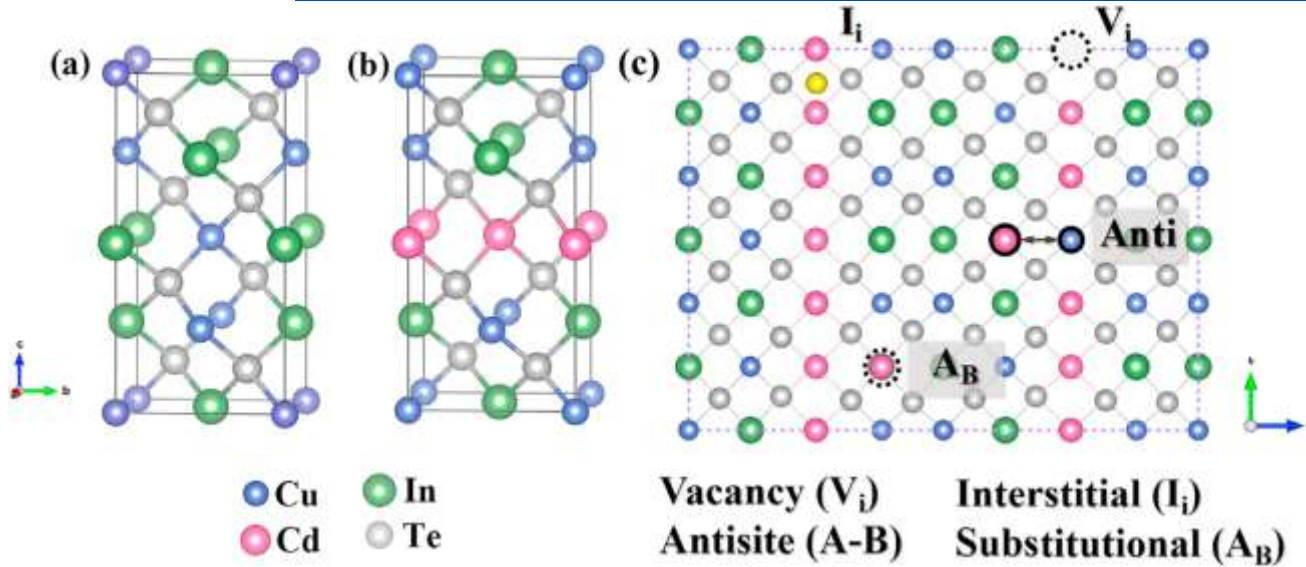


- A high-throughput screening workflow based on MatHub-3d and the deformation potential method.

npj Comput. Mater., 9, 190 (2023) www.mathub3d.net

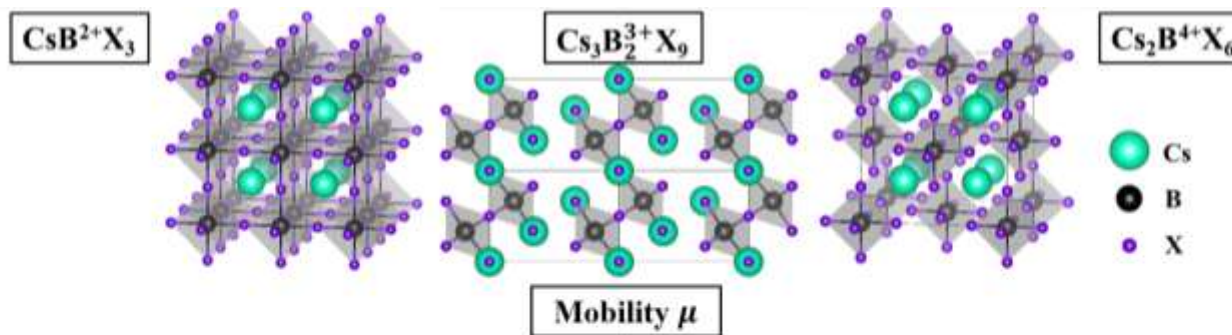
2.3 TransOpt Recent works by TransOpt 2.0

$$\frac{1}{\tau_{\text{IMP},n\mathbf{k}}} = \sum_{m\mathbf{k}'} \frac{2\pi n_{\text{imp}} Z_{\text{imp}}^2 e^4}{V \hbar (\epsilon_s \kappa_0)^2 (L_D^{-2} + |\mathbf{k}' - \mathbf{k}|^2)^2} \delta(\epsilon_{n\mathbf{k}} - \epsilon_{m\mathbf{k}'})$$



- Low formation energies of the defects in Cd₂Cu₃In₃Te₈ cause high defect density ($4.80 \times 10^{20} \text{ cm}^{-3}$) and severely reduced mobility.

J. Materiomics, 8 1222 (2022)



Mobility μ

group velocity v

relaxation time τ $\tau^{-1} = \tau_{\text{acoustic}}^{-1} + \tau_{\text{impurity}}^{-1}$

$v_{113} > v_{329} > v_{216}$

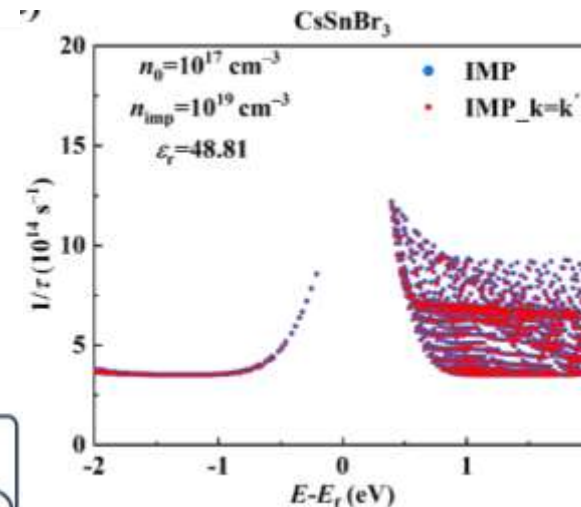
3D delocalized BX₆ conductive network

2D delocalized BX₆ conductive network

isolated BX₆

high impurity & low carrier concentration
 $\tau_{\text{impurity}}^{-1}$ dominates

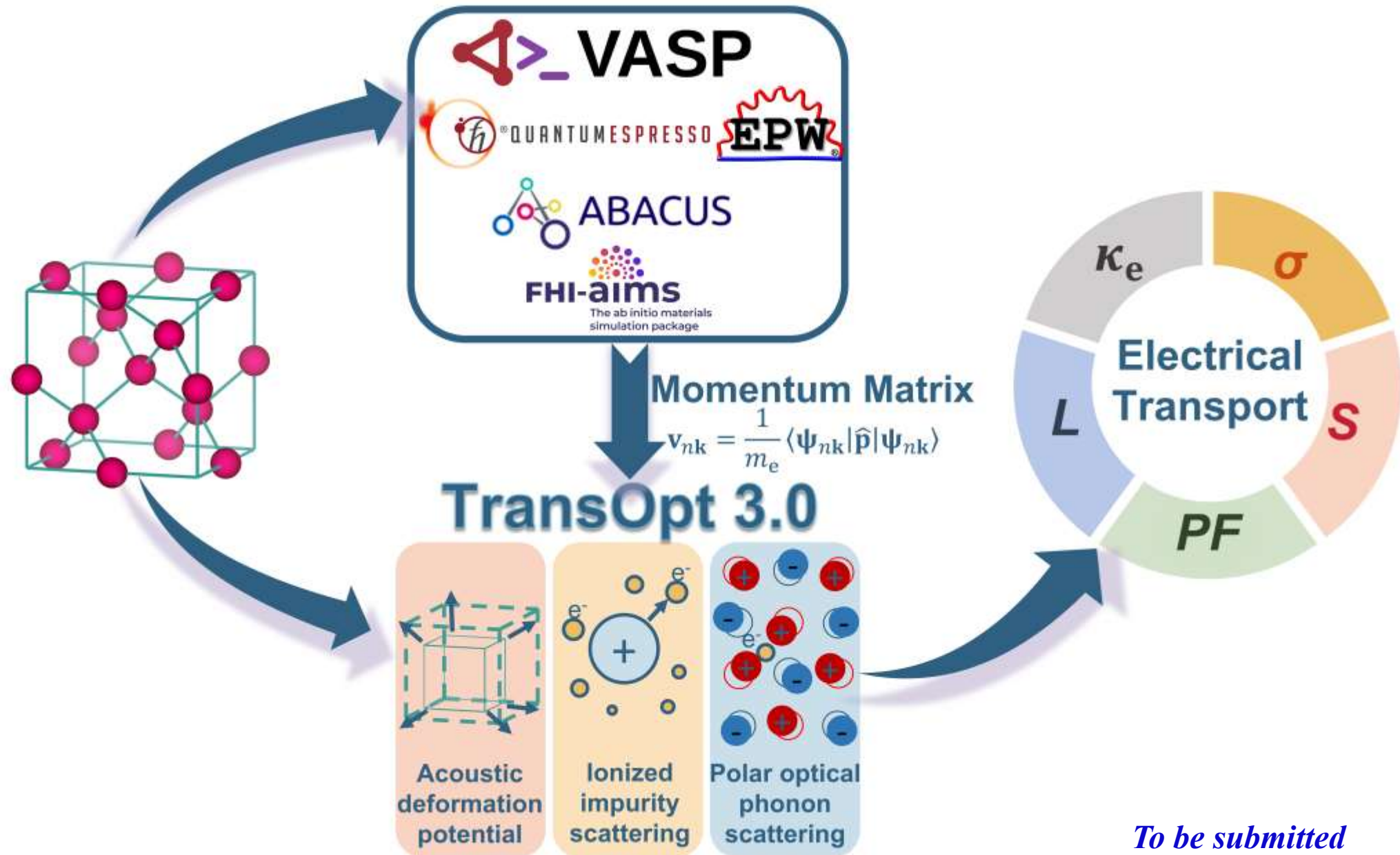
ionized impurity scattering rate is related to the band degeneracy.



Direct transition process ($\mathbf{k}' = \mathbf{k}$) dominates IMP

J. Mater. Sci. Technol., 204, 245–254 (2025)

2.3 TransOpt 3.0

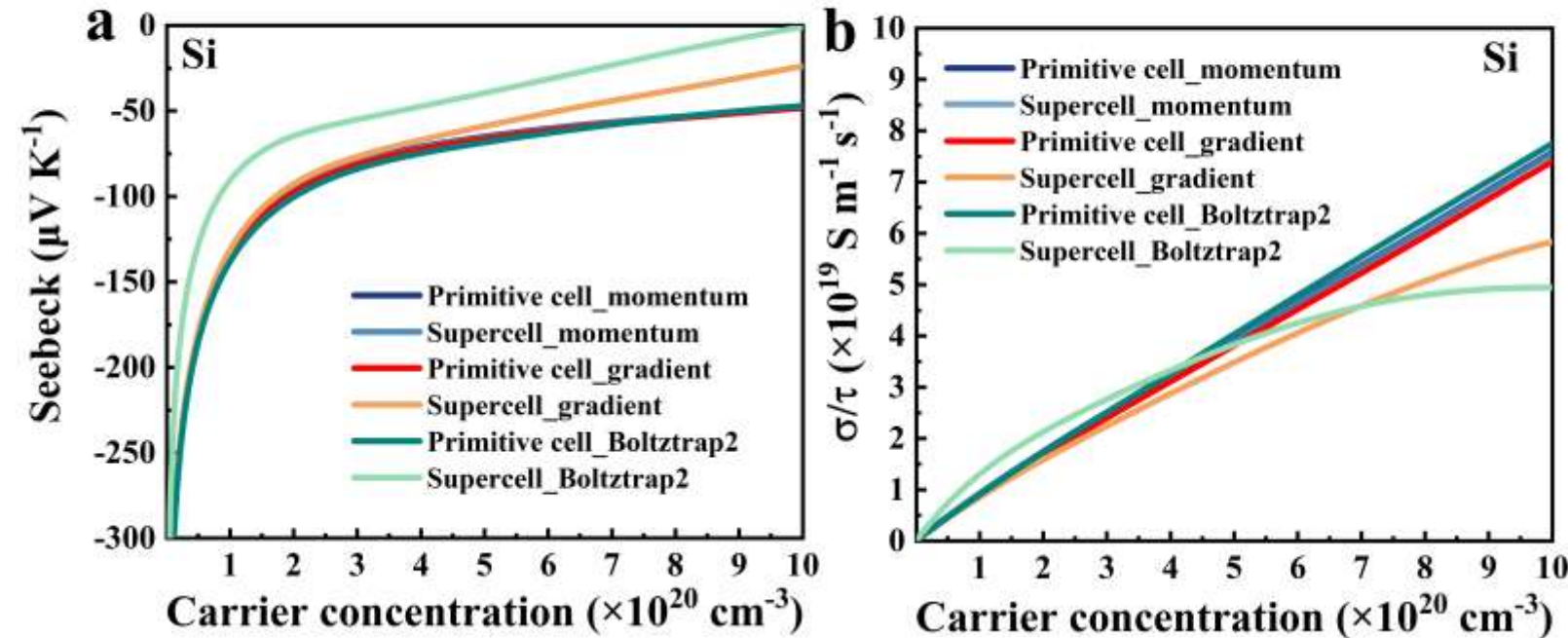


$$\mathbf{v}_{nk} = \frac{1}{m_e} \langle \psi_{nk} | \hat{\mathbf{p}} | \psi_{nk} \rangle \quad \text{vs} \quad \mathbf{v}_{nk} = \frac{1}{\hbar} \nabla_{\mathbf{k}} \epsilon_{nk}$$

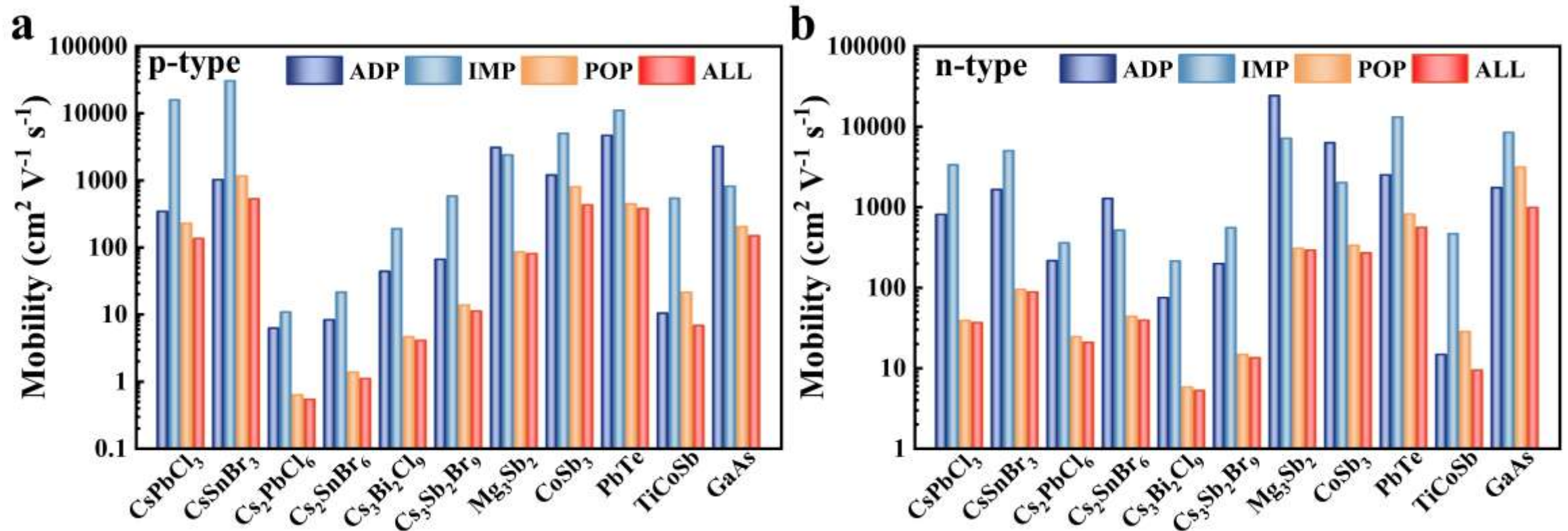
- Momentum matrix method provides better agreement between supercell and primitive cell results compared to gradient method or BoltzTraP2 interpolation.
- This scheme offers distinct advantages for systems involving doping or those with large primitive cells.
- Momentum matrix method for group velocity has been achieved in all the DFT codes compatible with TransOpt 3.0.

TransOpt 3.0: momentum/gradient
 Primitive cell: Si₂ k mesh 80×80×80
 Supercell: Si₁₂₈ k mesh 20×20×20

Boltztrap2:
 Interpolation factor: 64
 Primitive cell: Si₂ k mesh 20×20×20
 Supercell: Si₁₂₈ k mesh 5×5×5



Calculated Results for Typical Thermoelectric Materials and Perovskites

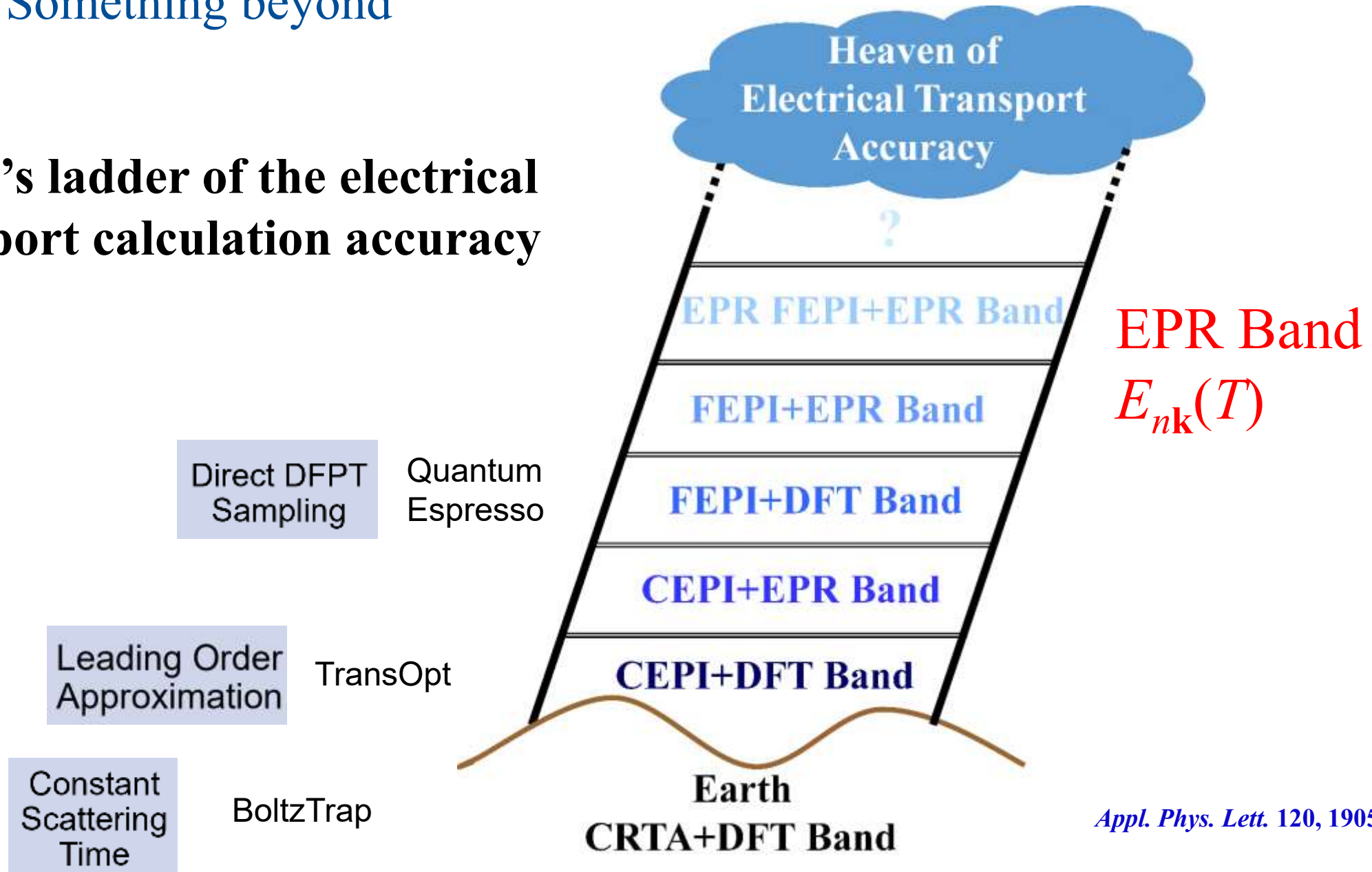


$$n_0 = n_{\text{imp}} = 10^{18} \text{ cm}^{-3}$$

- POP scattering dominates the total carrier mobility in majority of the investigated cases.

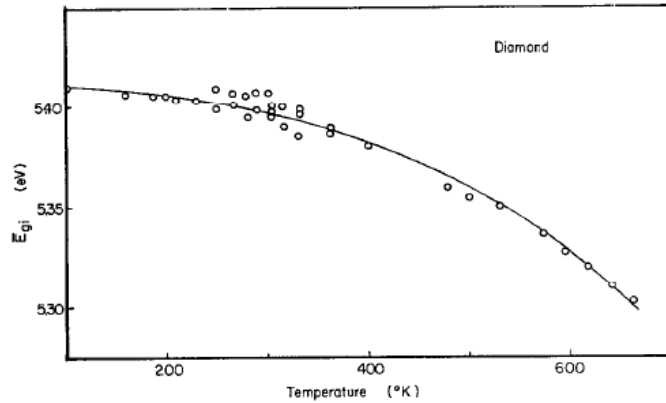
2.4 Something beyond

Jacob's ladder of the electrical transport calculation accuracy

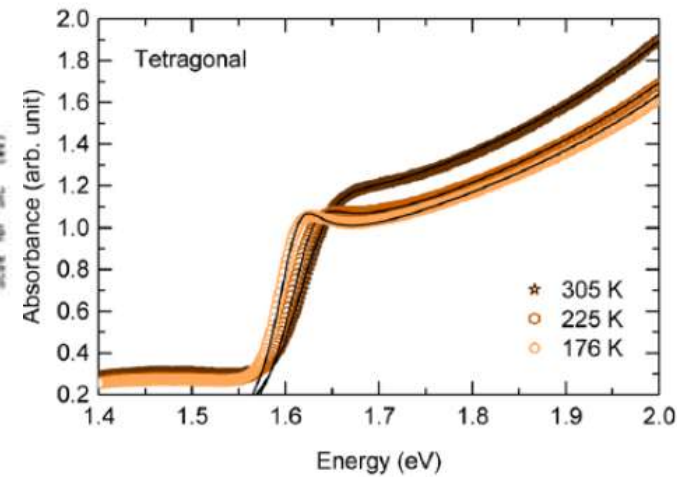
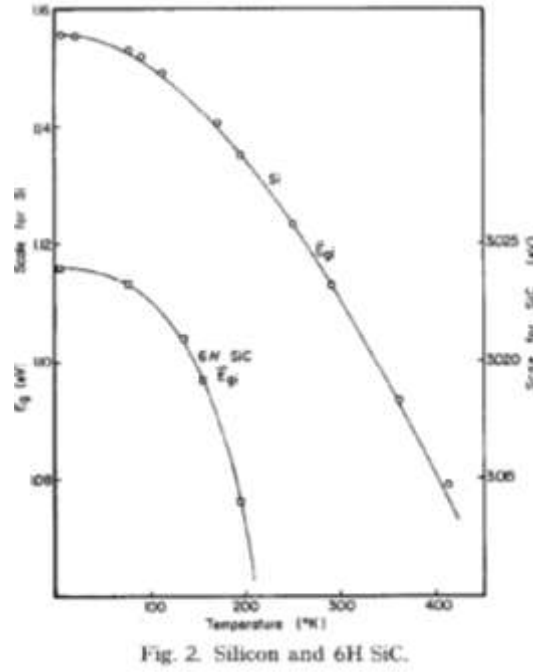


2.4 Something beyond Temperature-induced band renormalization

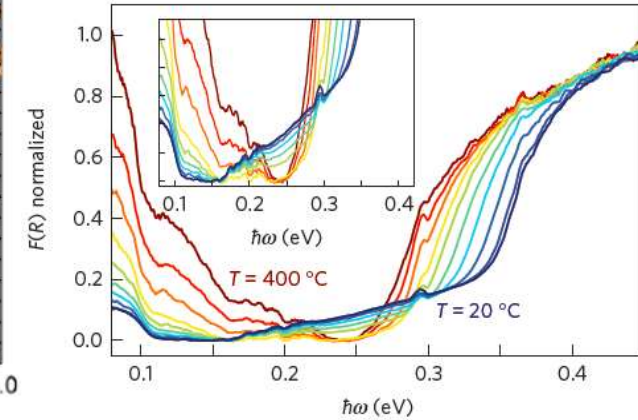
Experiment



Diamond, Si, SiC, *Physica*, 34, 149 (1967);
J. Phys. Chem. Solids, 40, 791(1979)



MAPbI₃, *J. Phys. Chem. Lett.*, 7, 3014 (2016) **CoSb₃**, *Nat. Mater.*, 14, 1223 (2015)



Theory

Electron-Phonon Renormalization (EPR)

$$\Delta E_{n\mathbf{k}}(T) = \Delta E_{n\mathbf{k}}^{VIB}(0) + \Delta E_{n\mathbf{k}}^{VIB}(T) + \Delta E_{n\mathbf{k}}^{LE}(T)$$

Zero-point vibration at 0 K

Thermal vibration at T

Lattice expansion at T

2.4 Something beyond Temperature-induced band renormalization

□ Electron energy at finite T :

◆ Step1: Lattice expansion effect

Method1: QHA by VASP and Phonopy

Method2: NPT AIMD by VASP

◆ Step2: Vibration effect

Method1: AHC theory in VASP6.5.1 or Abinit

- Electron self-energy: $\Sigma_{nk}^{ep}(T) = \Sigma_{nk}^{FM}(T) + \Sigma_{nk}^{DW}(T)$
- Electron energy at T : $\tilde{\epsilon}_{nk} = \epsilon_{nk} + \text{Re}\Sigma_{nk}^{ep}(T)$

◆ Step2: Vibration effect

Method 2: “one-shot” method by VASP and Phonopy

- Atomic displacement at T :

$$\Delta\tau_{k\alpha} = (M_p/M_\kappa)^{1/2} \sum_v (-1)^{v-1} e_{k\alpha,v} s_{v,T}$$

$$s_{v,T}^2 = (\hbar/2M_p \omega_v)(2n_{v,T} + 1)$$

- Electron energy at T by using the effective structure under lattice expansion and thermal vibrations at T

◆ Step2: Vibration effect

Method 3: NVT AIMD by VASP

- Electron energy at T : time average of MD snapshots

□ Electrical transport at finite T :

Method: Boltzmann transport theory by TransOpt

- Electrical conductivity:

$$\sigma_{\alpha\beta}(\epsilon_F, T) = \sum_n \int \frac{d\mathbf{k}}{\Omega_{BZ}} \tilde{v}_{n\mathbf{k}\alpha} \tilde{v}_{n\mathbf{k}\beta} \tilde{\tau}_{n\mathbf{k}} \left[-\frac{\partial \tilde{f}_{n\mathbf{k}}(\epsilon_F, T)}{\partial \tilde{\epsilon}_{n\mathbf{k}}} \right]$$

- Seebeck coefficient:

$$S_{\alpha\beta}(\epsilon_F, T) = \frac{1}{eT} \sigma_{\alpha\beta}(\epsilon_F, T)^{-1}$$

$$\sum_n \int \frac{d\mathbf{k}}{\Omega_{BZ}} \tilde{v}_{n\mathbf{k}\alpha} \tilde{v}_{n\mathbf{k}\beta} \tilde{\tau}_{n\mathbf{k}} (\epsilon_F - \tilde{\epsilon}_{n\mathbf{k}}) \left[-\frac{\partial \tilde{f}_{n\mathbf{k}}(\epsilon_F, T)}{\partial \tilde{\epsilon}_{n\mathbf{k}}} \right]$$

- Scattering rate:

$$1) \frac{1}{\tilde{\tau}_{n\mathbf{k}}} = \frac{2\pi k_B T D_{def}^2}{\hbar c} \sum_m \int \frac{d\mathbf{k}'}{\Omega_{BZ}} \delta(\tilde{\epsilon}_{n\mathbf{k}} - \tilde{\epsilon}_{m\mathbf{k}'})$$

$$2) \frac{1}{\tau_{n\mathbf{k}}} = 2 \cdot \text{Im}\Sigma_{n\mathbf{k}}^{ep}(T)$$

Rev. Mod. Phys., 89, 015003 (2017)

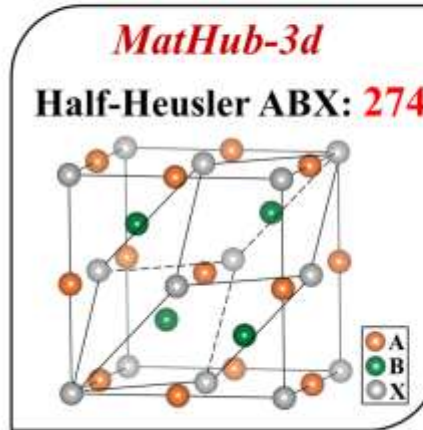
J. Phys.: Condens. Matter, 32, 475503 (2020)

2.4 Something beyond Temperature-induced band renormalization

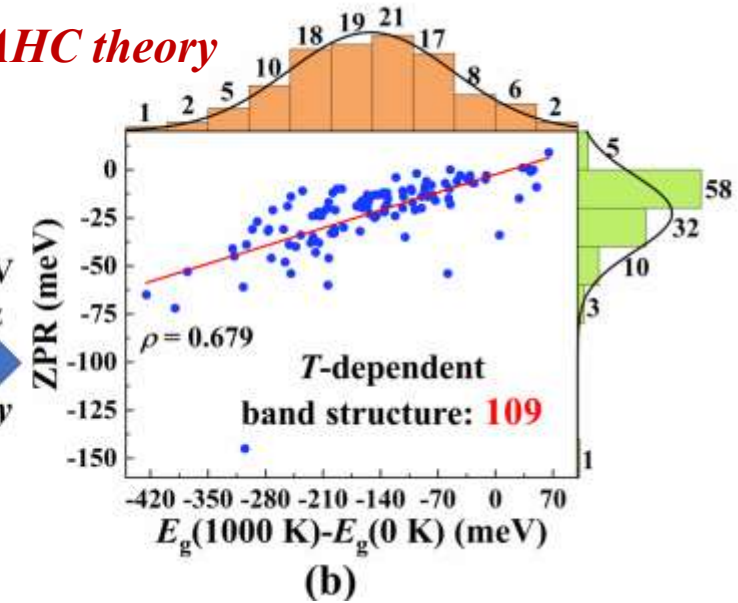
Thermoelectric Half-Heusler compounds

- E_g of most systems gradually decreases with T . Median E_g change from 0 K to 1000 K is ~ -200 meV. Even at 0 K, the ZPR has some influences.

Method1: AHC theory

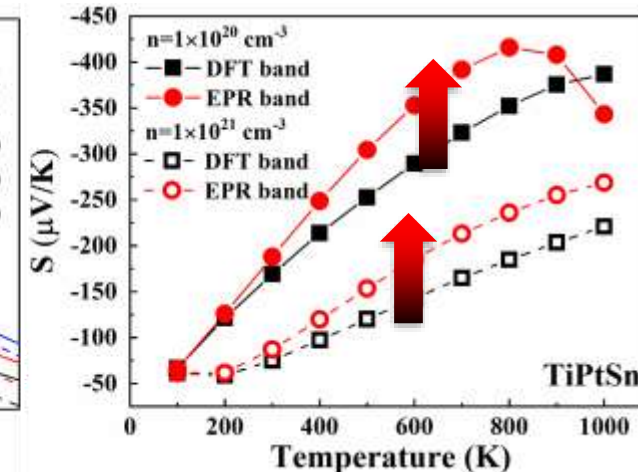
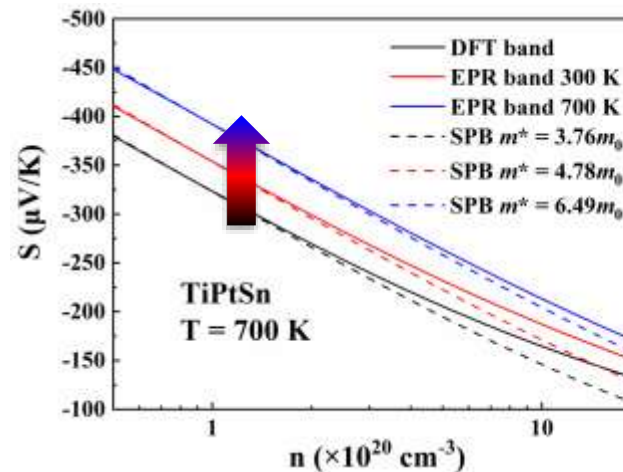


- $E_g > 0.1$ eV
 - $\omega > 0$ THz
- AHC theory**



(a)

(b)

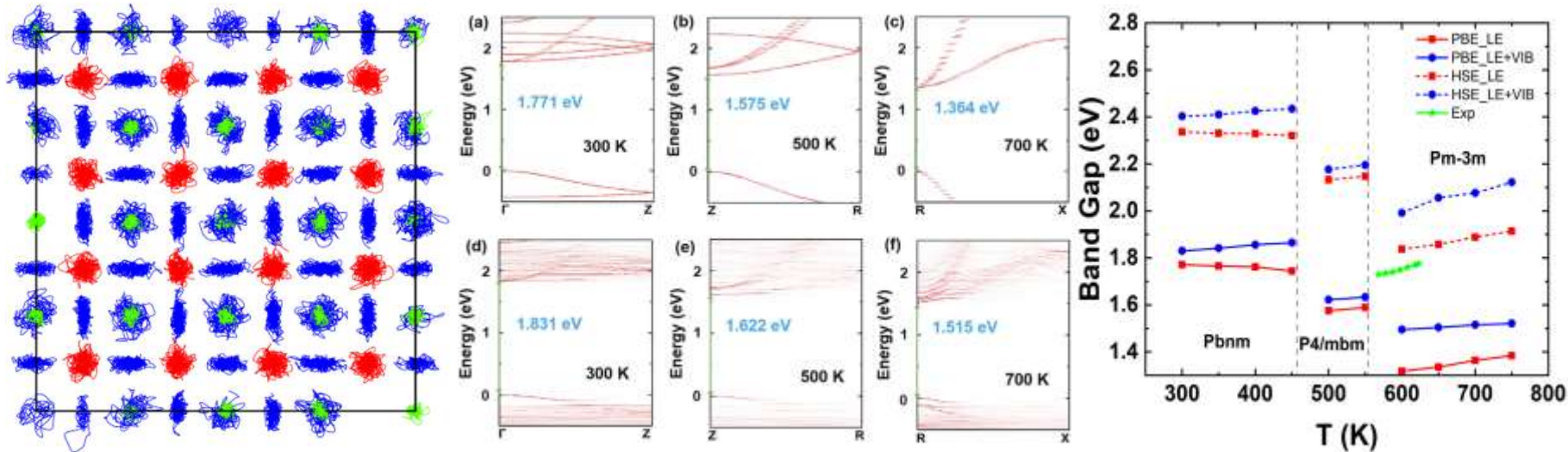


- The EPR band has been used in the calculations of Seebeck coefficients, for the first time.

[arXiv:2407.00433](https://arxiv.org/abs/2407.00433)

2.4 Something beyond Temperature-induced band renormalization

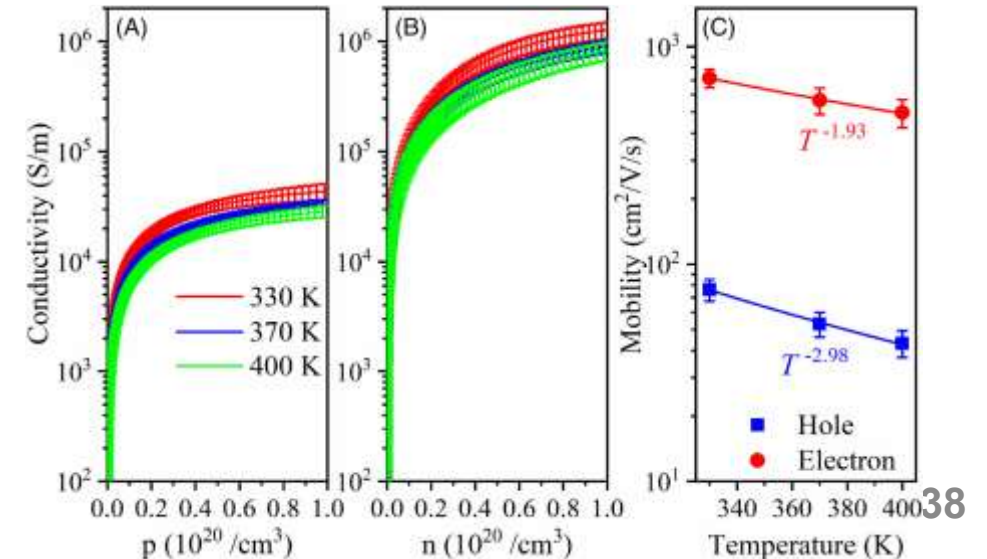
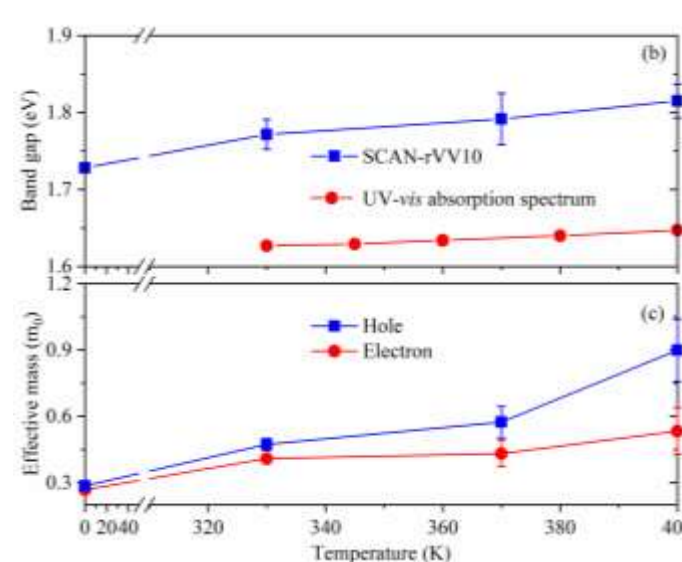
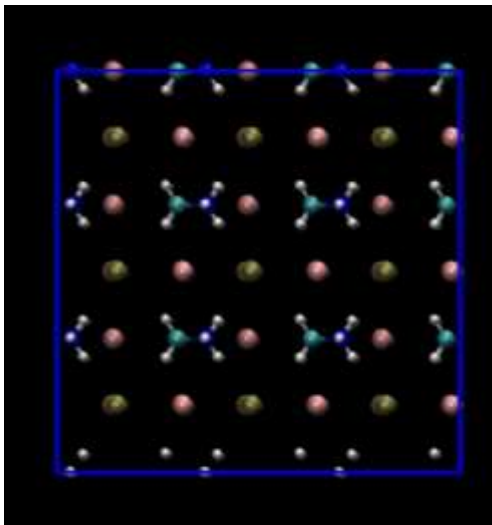
Orthorhombic, tetragonal, and cubic CsPbI_3 (Method 2: “one-shot”)



Strong structural fluctuation
Strong band gap renormalization
Strong suppression on transport

J. Comput. Chem., 42, 2213 (2021)
Phys. Chem. Chem. Phys., 24, 16003 (2022)

Optoelectronic Perovskites: Cubic MAPbI_3 (Method 3: AIMD)



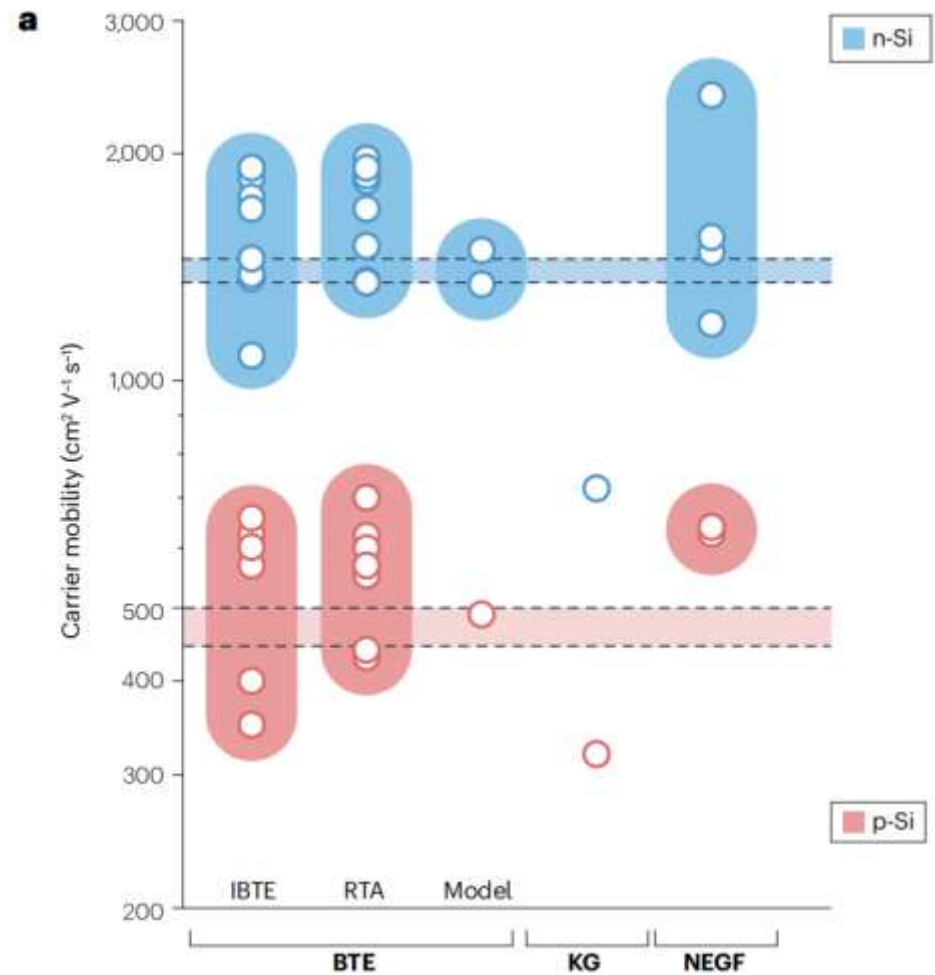
- Electrical transport properties within the framework of linear response theory

$$\sigma(\omega) = \frac{2\pi q^2 \hbar^2}{m^2 V \omega} \sum_{m,n,\mathbf{k}} (\langle \psi_{n\mathbf{k}} | \nabla_\alpha | \psi_{m\mathbf{k}} \rangle \langle \psi_{m\mathbf{k}} | \nabla_\alpha | \psi_{n\mathbf{k}} \rangle) (f_{n\mathbf{k}}^0 - f_{m\mathbf{k}}^0) \delta(\varepsilon_{m\mathbf{k}} - \varepsilon_{n\mathbf{k}} - \hbar\omega)$$

- ✓ **Liquids & amorphous:** amorphous Cu-doped Ta₂O₅; liquid aluminum; liquid Zr; liquid and supercooled silicon...
- ✓ **Dense metals:** warm dense aluminum; dense silver plasma; warm dense helium-hydrogen mixtures...
- ✓ **Semiconductors:** monolayer and bilayer phosphorene; semiconducting fematinite-like structure (Cu₃SbS₄); perovskites...

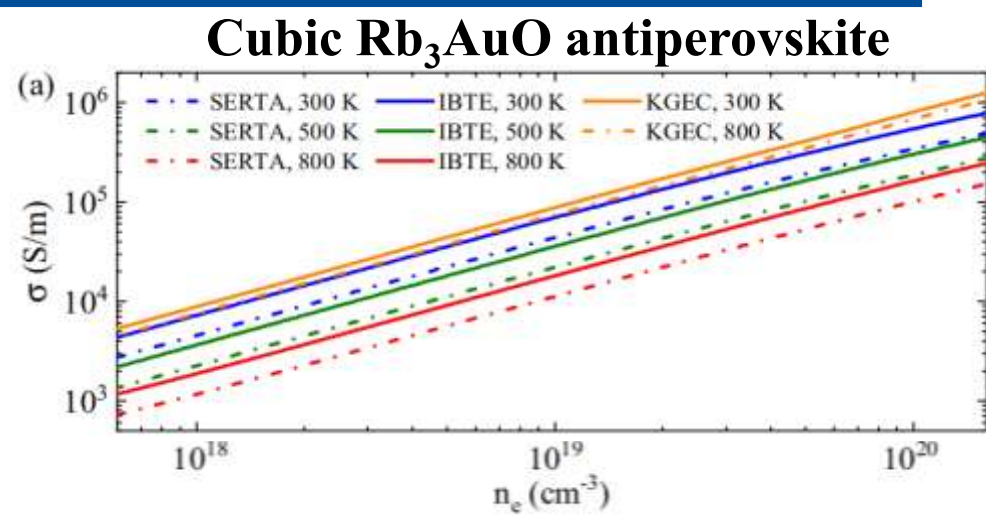
3. Kubo framework

Kubo-Greenwood

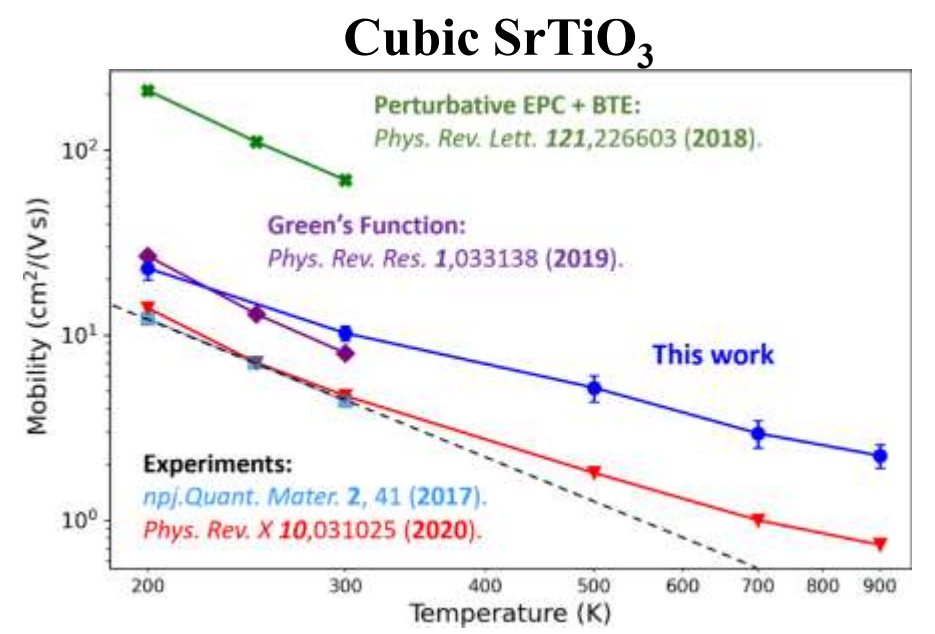


Calculated values of carrier mobility at room temperature using different frameworks and methods.

Nat. Rev. Phys., 7, 73–90 (2025)



Phys. Rev. B, 102, 094314 (2020)



Phys. Rev. B, 110, 235202 (2024)

Summary on e-trans

□ BTE level:

- ✓ **The calculation of full electron-phonon interaction is still demanding.**
- ✓ **Different softwares with different approximations on multiple scattering mechanisms are available.**

□ Higher level:

- ✓ **Electron-phonon renormalization on band structures are considered in some materials.**
- ✓ **Kubo-Greenwood method is suitable for anharmonic materials.**

Overview

Background

Electrical transport

Lattice thermal conductivity

3.1 BTE in Lattice Thermal Transport

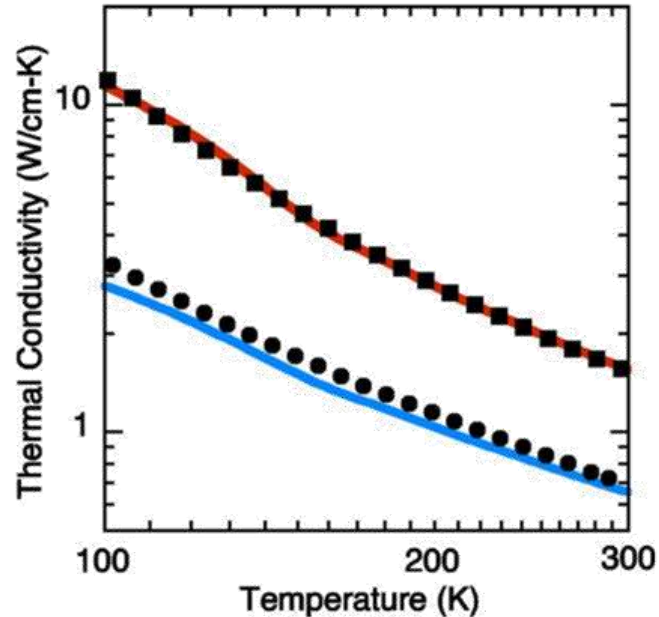


FIG. 1. (Color online) Lattice thermal conductivity $\kappa^{(i)}$ as a function of temperature. The red line and solid squares are the calculated and measured thermal conductivities of silicon, respectively, while the blue line and the solid circles are the corresponding quantities for germanium.

- Since **2007**, three-phonon calculations combined with **BTE** have become a standard approach for κ_L prediction, achieving high accuracy in conventional crystals.
- Phonon BTE is less demanding than full el-ph interaction.

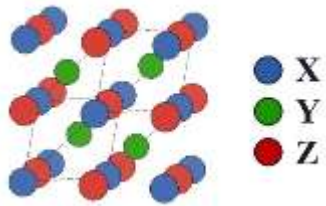
3.1 BTE in Lattice Thermal Transport Taylor Expansion of Potential Energy

□ The potential energy is expressed using a Taylor expansion

$$E = E_0 + \frac{1}{2} \sum_{ij\alpha\beta} \Phi_{ij}^{\alpha\beta} r_i^\alpha r_j^\beta + \frac{1}{3!} \sum_{ijk\alpha\beta\gamma} \Phi_{ijk}^{\alpha\beta\gamma} r_i^\alpha r_j^\beta r_k^\gamma + \frac{1}{4!} \sum_{ijkl\alpha\beta\gamma\theta} \Phi_{ijkl}^{\alpha\beta\gamma\theta} r_i^\alpha r_j^\beta r_k^\gamma r_l^\theta + \dots$$

First-order
Atomic force

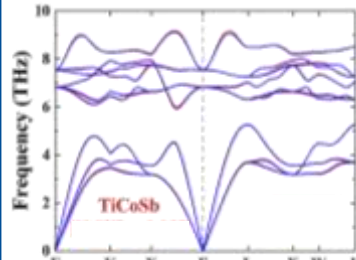
Structural properties



Second-order

Harmonic IFCs

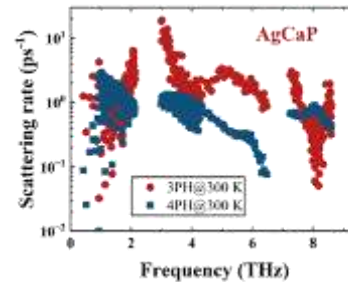
Phonon dispersion



Higher-order

Anharmonic IFCs

Phonon scattering rate



$$\kappa_L = \frac{1}{NV} \sum_{\lambda} C_V(\omega_{\lambda}) v_g^2(\omega_{\lambda}) \tau(\omega_{\lambda})$$

Software: phonopy

$$D_{ij}^{\alpha\beta}(\mathbf{q}) = \sum_l \frac{\Phi_{ijl}^{\alpha\beta}}{\sqrt{m_i m_j}} \exp[i\mathbf{q} \cdot (\mathbf{r}_i - \mathbf{r}_{jl})]$$

$$\sum D_{ij}^{\alpha\beta}(\mathbf{q}) \mathbf{e}(\omega_{\lambda}) = [\omega_{\lambda}]^2 \mathbf{e}(\omega_{\lambda})$$

$$\mathbf{v}(\omega_{\lambda}) = \frac{1}{2\omega_{\lambda}} \langle \mathbf{e}(\omega_{\lambda}) | \frac{\partial D(\mathbf{q})}{\partial \mathbf{q}} | \mathbf{e}(\omega_{\lambda}) \rangle = \frac{\partial \omega_{\mathbf{q}}}{\partial \mathbf{q}}$$

□ **Phonon heat capacity:** $C_V = \left(\frac{dU}{dT} \right) = \left(\frac{d \sum_{\mathbf{q}s} E_{\mathbf{q}s}}{dT} \right) = \sum_{\mathbf{q}s} c_{\mathbf{q}s}$

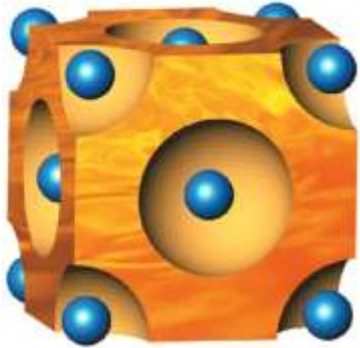
□ **Phonon energy:** $E_{\mathbf{q}s} = \left(n_{\mathbf{q}s} + \frac{1}{2} \right) \hbar \omega_{\mathbf{q}s}$

□ **Bose-Einstein distribution:** $n_{\mathbf{q}s} = \frac{1}{\exp\left(\frac{\hbar \omega_{\mathbf{q}s}}{k_B T}\right) - 1}$

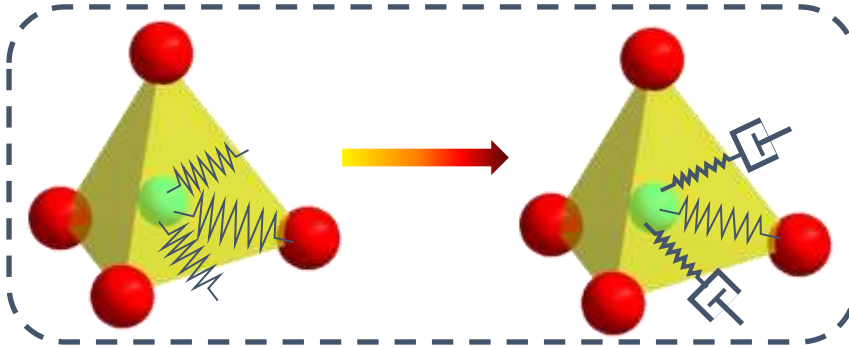
$$\kappa_L = \frac{1}{NV} \sum_{\lambda} C_V(\omega_{\lambda}) v_g^2(\omega_{\lambda}) \tau(\omega_{\lambda})$$

□ **Mode heat capacity:** $c_{\mathbf{q}s} = k_B \left(\frac{\hbar \omega_{\mathbf{q}s}}{k_B T} \right)^2 \frac{\exp(\hbar \omega_{\mathbf{q}s} / k_B T)}{[\exp(\hbar \omega_{\mathbf{q}s} / k_B T) - 1]^2}$

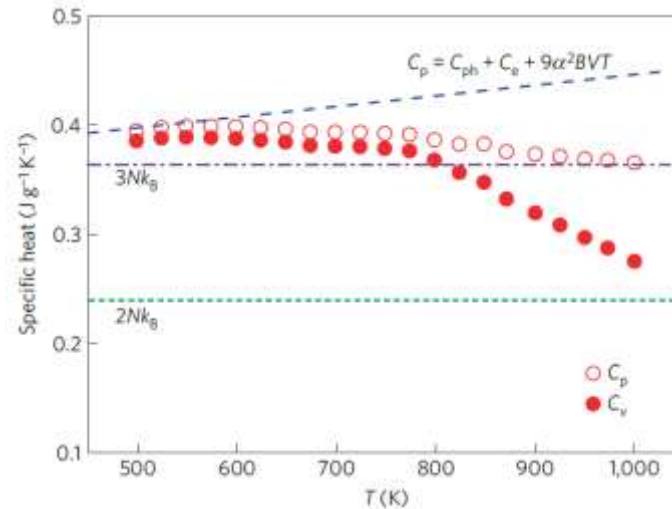
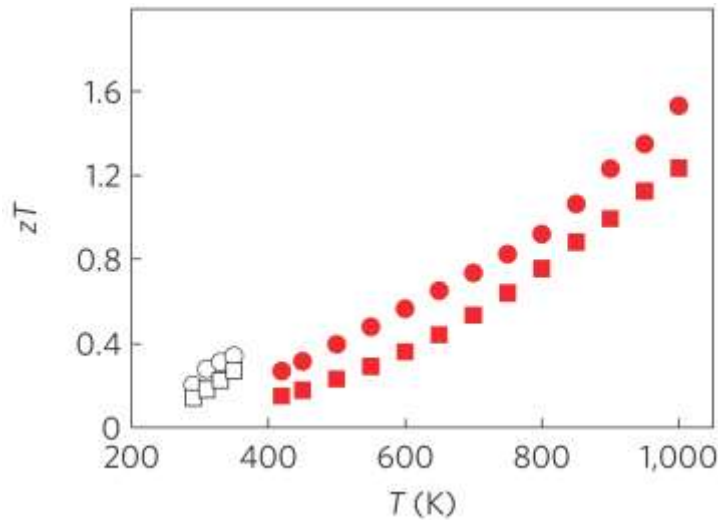
High-temperature limit $c_{\mathbf{q}s} \sim k_B$ $C_V \sim 3N_A k_B$



Crystal Structure of $\text{Cu}_2\text{S/Te}$ (High-Temperature Phase)



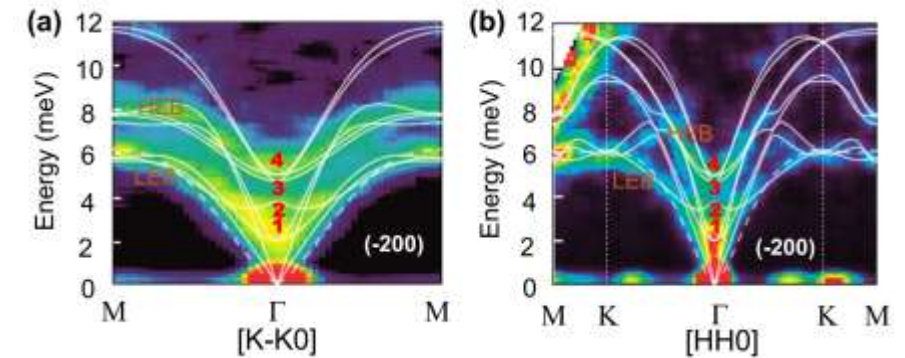
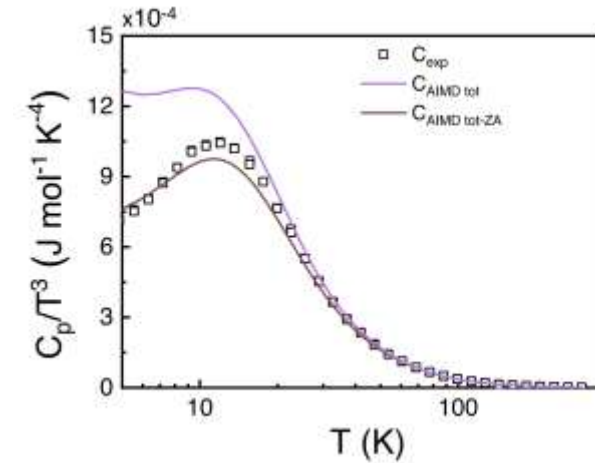
- The number of heat-carrying modes is reduced, accompanied by the loss of some transverse modes.



Nat. Mater., 11, 422 (2012)

□ Boson-peak-like feature

Debye model at low T limit: $C_V \propto T^3$



Nat. Commun., 15, 6248 (2024)

□ The potential energy is expressed using a Taylor expansion

$$E = E_0 + \frac{1}{2} \sum_{ij\alpha\beta} \Phi_{ij}^{\alpha\beta} r_i^\alpha r_j^\beta + \frac{1}{3!} \sum_{ijk\alpha\beta\gamma} \Phi_{ijk}^{\alpha\beta\gamma} r_i^\alpha r_j^\beta r_k^\gamma + \frac{1}{4!} \sum_{ijkl\alpha\beta\gamma\theta} \Phi_{ijkl}^{\alpha\beta\gamma\theta} r_i^\alpha r_j^\beta r_k^\gamma r_l^\theta + \dots$$

Scattering strength $\Phi_{\lambda\lambda'\lambda''} = \sum_{ijk} \sum_{\alpha\beta\gamma} \frac{e^\alpha(i, \lambda) e^\beta(j, \lambda') e^\gamma(k, \lambda'')}{\sqrt{m_i m_j m_k} \sqrt{\omega_\lambda \omega_{\lambda'} \omega_{\lambda''}}} \Phi_{ijk}^{\alpha\beta\gamma} e^{i(q \cdot r_i + q' \cdot r_j + q'' \cdot r_k)}$

$$\tau_\lambda^{-1}(\omega) = \frac{\hbar\pi}{8} \sum_{\lambda', \lambda''} |\Phi_{\lambda\lambda'\lambda''}|^2 [(n_{\lambda'} + n_{\lambda''} + 1) \delta(\omega - \omega_{\lambda'} - \omega_{\lambda''}) + 2(n_{\lambda'} - n_{\lambda''}) \delta(\omega - \omega_{\lambda'} + \omega_{\lambda''})] \Delta_{\mathbf{q}\mathbf{q}'\mathbf{q}''}$$

Scattering phase space

$$\kappa_L = \frac{1}{NV} \sum_{\lambda} C_V(\omega_\lambda) v_g^2(\omega_\lambda) \tau(\omega_\lambda)$$

$$\frac{1}{\tau_{\mathbf{q}}} = \frac{1}{\tau_{3ph}} + \frac{1}{\tau_{4ph}} + \dots$$

$$\frac{1}{\tau_{\mathbf{q}}} = \frac{1}{\tau_{3ph}} + \frac{1}{\tau_{e-p}} + \frac{1}{\tau_{4ph}} + \frac{1}{\tau_{GB}} + \frac{1}{\tau_{PD}} \dots$$

1.  Linearized BTE solved without any empirical parameters

Phys. Rev. B, 86, 174307 (2012)

2.  Applies the random displacement method to obtain higher-order IFCs.

J. Phys.: Condens. Matter, 26, 225402 (2014)

3. **phono3py**

Phys. Rev. B, 91, 094306 (2015)

.....

**Accurate
electron–phonon interaction**



$$g_{mn\lambda}(\mathbf{k}, \mathbf{q}) = \sqrt{\frac{\hbar}{2M\omega_{\mathbf{q}\lambda}}} \langle \Psi_{m\mathbf{k}+\mathbf{q}} | \Delta V_{\mathbf{q}\lambda} | \Psi_{n\mathbf{k}} \rangle$$

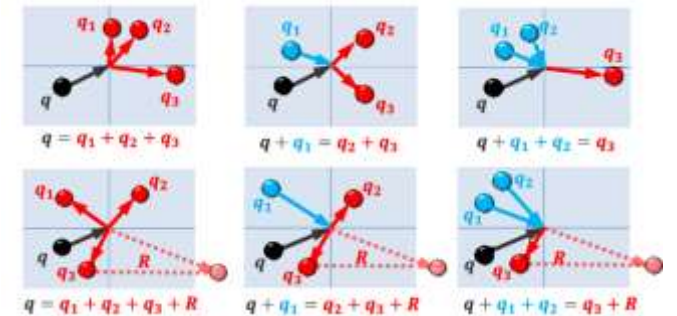
Comput. Phys. Commun., 181, 2140 (2010)

**Constant electron-phonon
coupling approximation**

$$|g_{mn}^{\lambda}(\mathbf{k}, \mathbf{q})|^2 = \frac{\hbar D_A^2 \omega_{\mathbf{q}\lambda}}{2VB}$$

Comput. Mater. Sci., 244, 113190 (2024)

Four-phonon Interactions

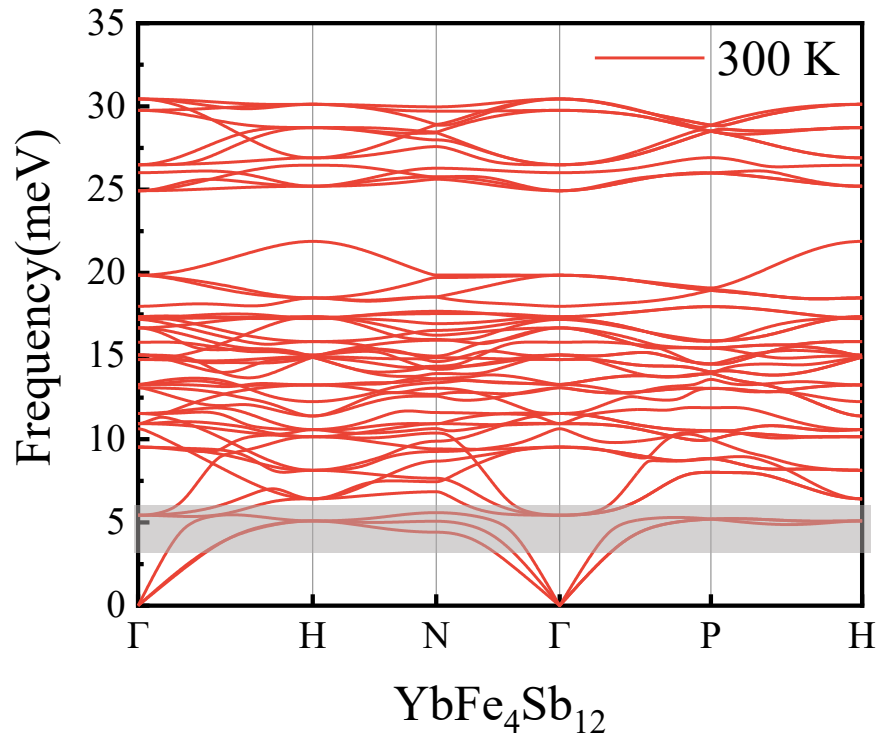


Phys. Rev. B, 96, 161201 (2017)

Also capable of treating
grain boundary scattering

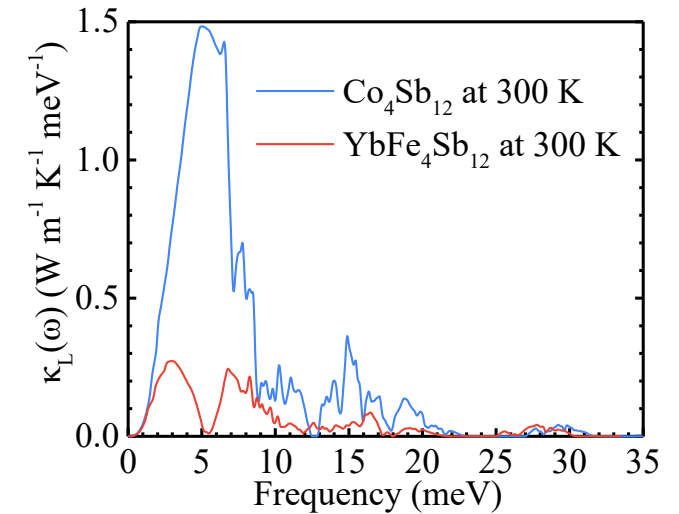
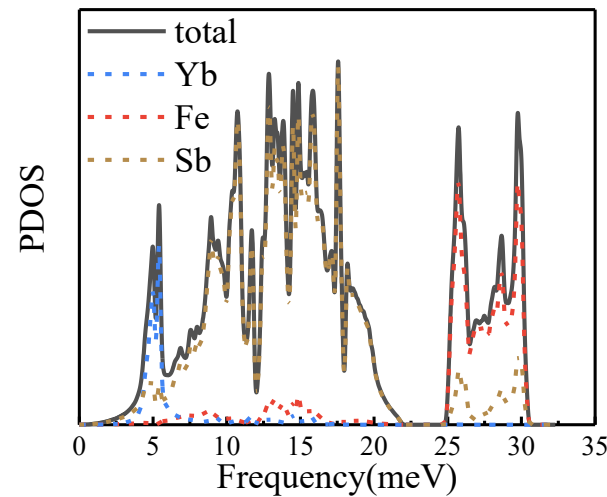
$$\frac{1}{\tau_B} = \frac{v}{L}$$

■ Filled skutterudites $\text{Yb}(\text{Ba})\text{Fe}_4\text{Sb}_{12}$



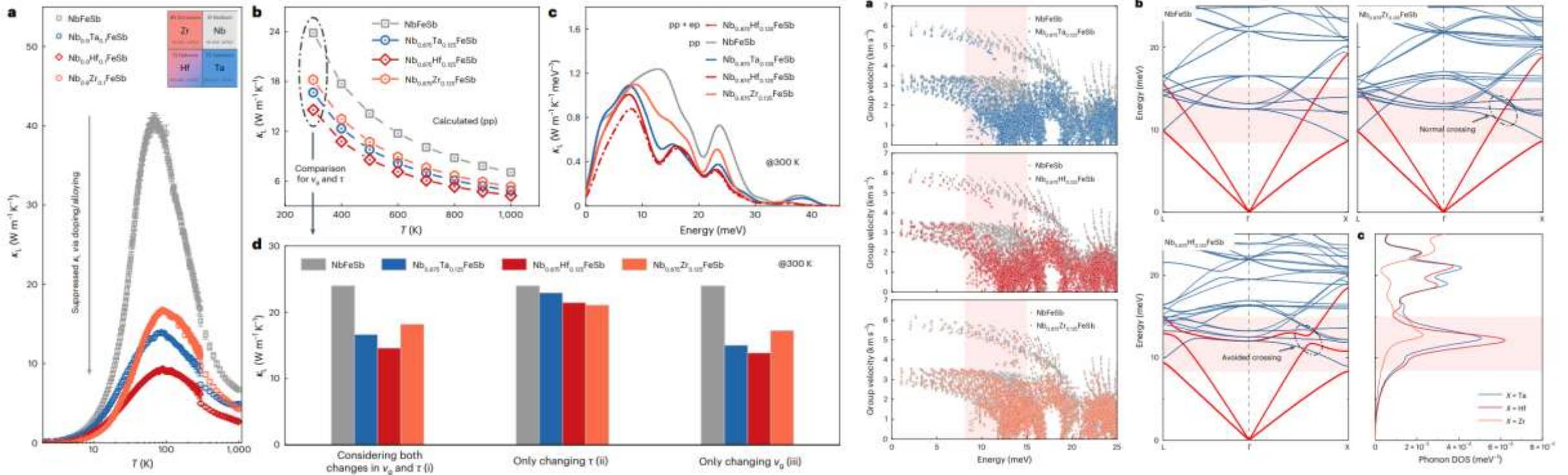
Weighted Scattering Phase Space (W)

$$W_{\lambda}^{\pm} = \frac{1}{2N} \sum_{\lambda' p''} \left\{ \frac{2(f_{\lambda'} - f_{\lambda''})}{f_{\lambda'} + f_{\lambda''} + 1} \right\} \frac{\delta(\omega_{\lambda} \pm \omega_{\lambda'} - \omega_{\lambda''})}{\omega_{\lambda} \omega_{\lambda'} \omega_{\lambda''}}$$



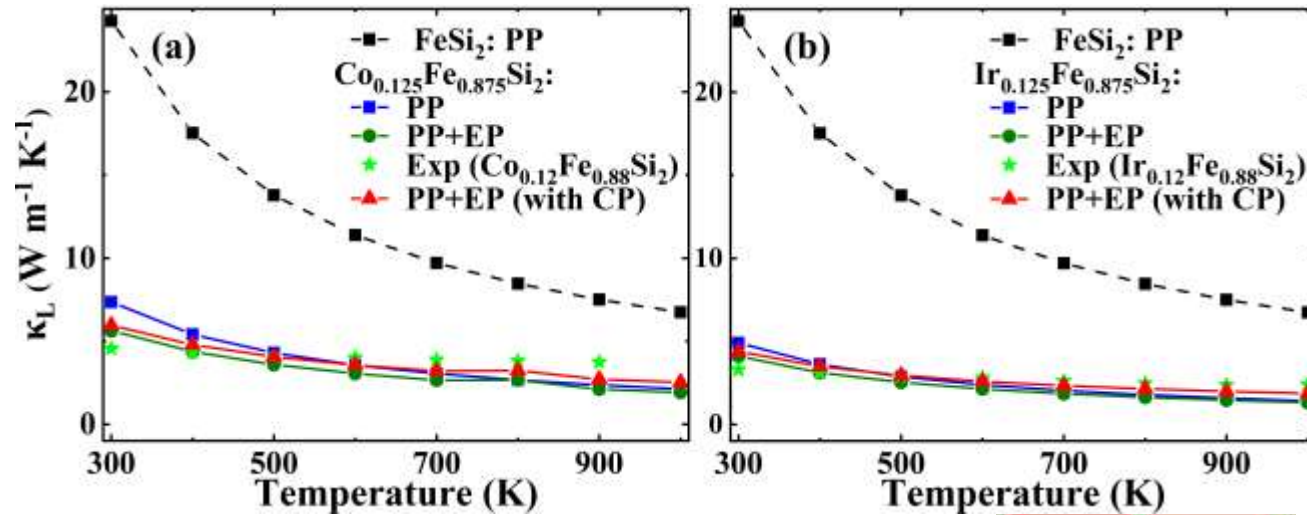
- The avoided-crossing filler modes greatly enhance the scattering phase space of $\text{YbFe}_4\text{Sb}_{12}$.
- The influence of low-frequency optical branches on phonon **scattering phase space** .vs. **Resonant scattering**.

- Pure *ab initio* force constant study.
- Dopants reduce the sound velocities and thus reduce the κ_L .
- Heavy-element doping induces **avoided-crossing behavior** in the phonon dispersion.



Nb_{0.875}X_{0.125}FeSb (X= Zr; Nb; Hf; Ta)

□ Effect of Ir/Co Doping on FeSi₂ κ_L



κ_L at 300 K(Experimental results):

Ir_{0.12}: 82%, Co_{0.12}: 76%, Co_{0.24}: 65%

$$\eta = \frac{\kappa_L^{\text{undoped}} - \kappa_L^{\text{doped}}}{\kappa_L^{\text{undoped}}}$$

26 Fe iron 55.845	27 Co cobalt 58.933
44 Ru ruthenium 101.07	45 Rh rhodium 102.91
76 Os osmium 190.23	77 Ir iridium 192.22

Calculated results

κ_L at 300 K(PP):

Ir_{0.125}: 80%, Co_{0.125}: 70%, Co_{0.25}: 52%

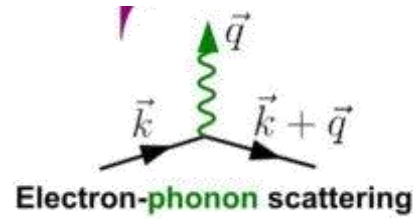
κ_L at 300 K(PP+EP):

Ir_{0.125}: 83%, Co_{0.125}: 77%, Co_{0.25}: 69%

- The modulation of force constants and EP coupling through adjacent-site doping can effectively reduce κ_L , not necessary to include the point defect scattering model.

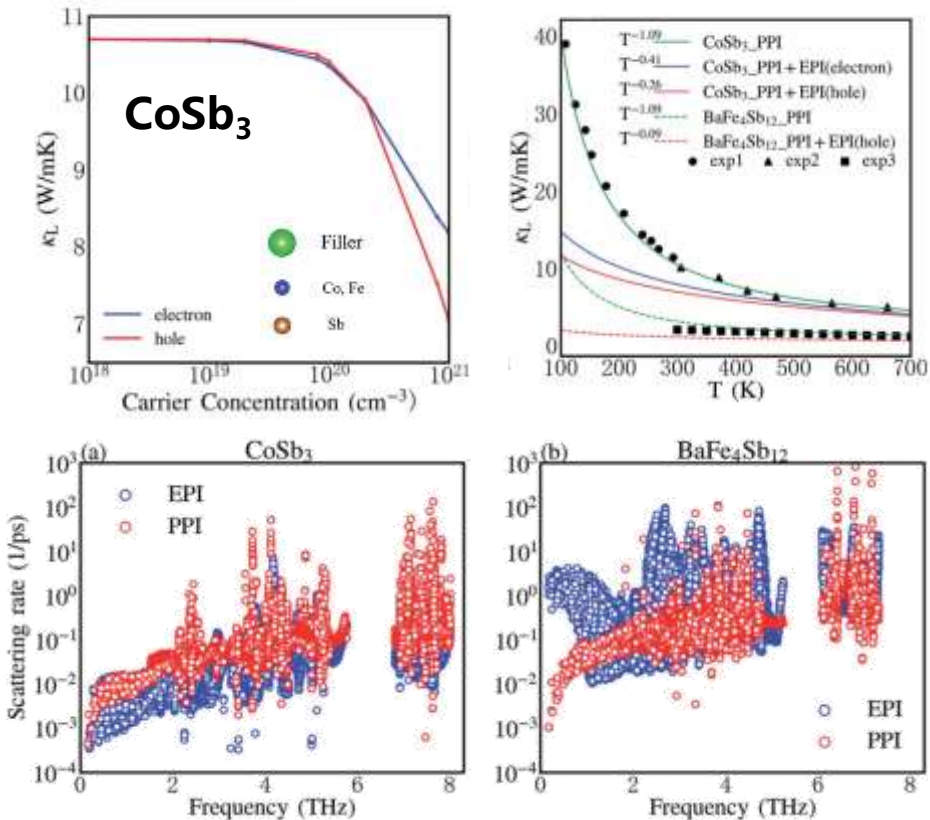
3.2 Case Studies Using Phonon BTE

Electron-Phonon Scattering



$$\frac{1}{\tau_{\mathbf{q}\lambda}^{\text{EP}}} = \frac{2\pi}{\hbar} \sum_{mn,\mathbf{k}} |g_{mn\lambda}(\mathbf{k}, \mathbf{q})|^2 (f_{n\mathbf{k}} - f_{m\mathbf{k}+\mathbf{q}}) \delta(\varepsilon_{n\mathbf{k}} - \varepsilon_{m\mathbf{k}+\mathbf{q}} - \hbar\omega_{\mathbf{q}\lambda})$$

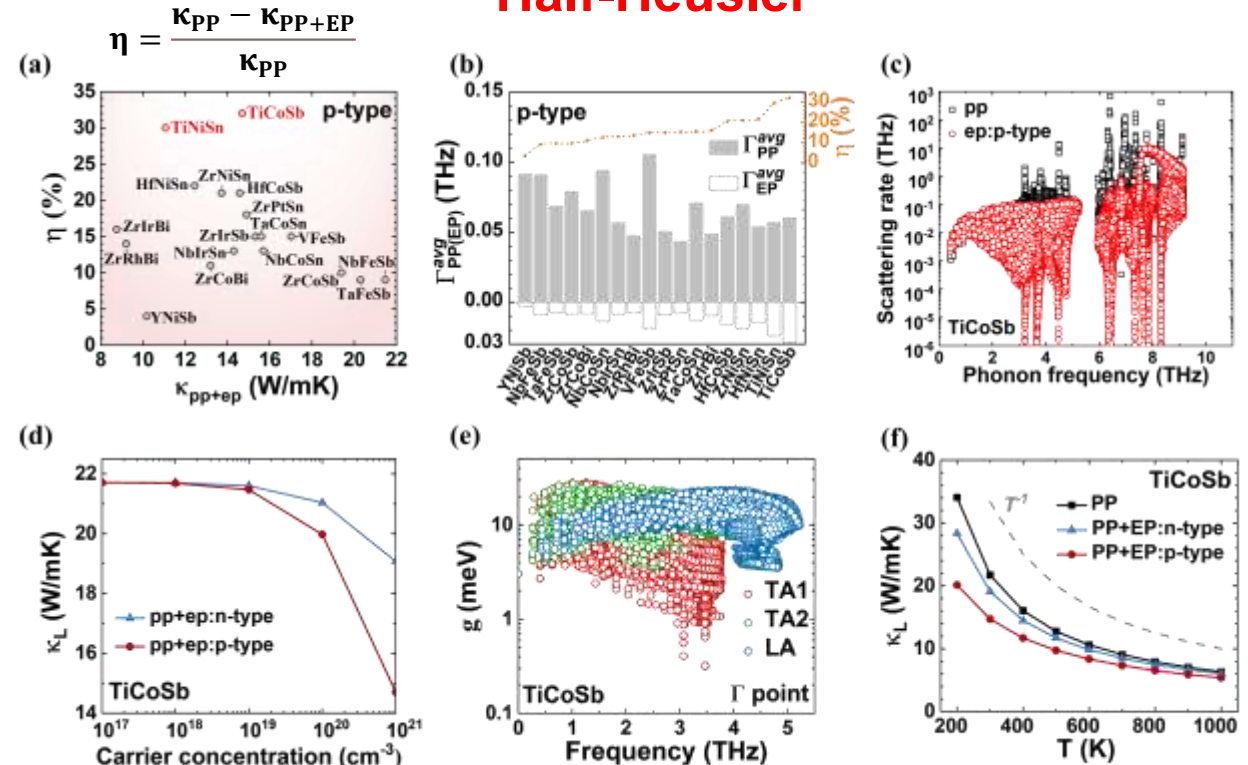
Skutterudite



@300K-BaFe₄Sb₁₂ ↓64.8%

J. Mater. Chem. A, 10, 13484 (2022)

Half-Heusler



- At 300 K with the carrier concentration of 10²¹ cm⁻³
- For the p-type doping, a more significant η for **TiCoSb (32%)**

Mater. Today Phys., 31, 100993 (2023)

3.2 Case Studies Using Phonon BTE Efficient electron-phonon code: TTEP

□ Replace the expensive electron-phonon coupling

$$g_{mn}^{\lambda}(\mathbf{k}, \mathbf{q}) = \sqrt{\frac{\hbar}{2M\omega_{\mathbf{q}\lambda}}} \langle \varphi_{m\mathbf{k}+\mathbf{q}} | \partial V_{\mathbf{q}\lambda} | \varphi_{n\mathbf{k}} \rangle \quad \text{-----} \quad \textcircled{1}$$

by the acoustic phonon long-wavelength limit($|\mathbf{q}| \rightarrow 0$):

$$\langle \varphi_{m\mathbf{k}+\mathbf{q}} | \partial V_{\mathbf{q}\lambda} | \varphi_{n\mathbf{k}} \rangle \approx D_A \cdot \mathbf{q} \quad \text{-----} \quad \textcircled{2}$$

Efficient electron-phonon scattering rate for phonon transport:

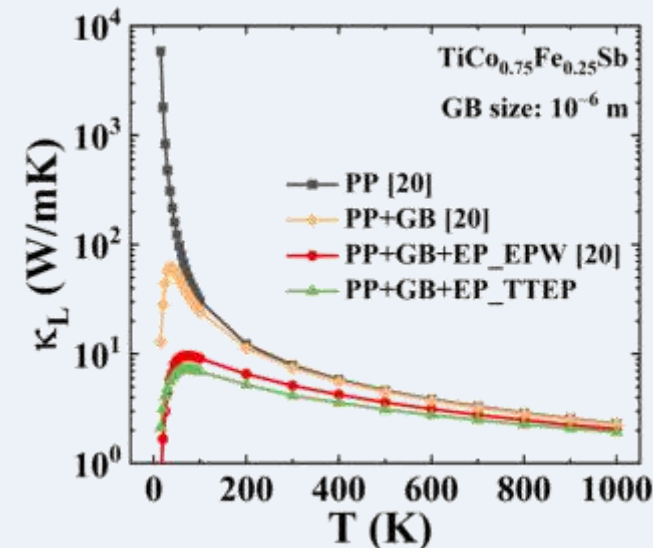
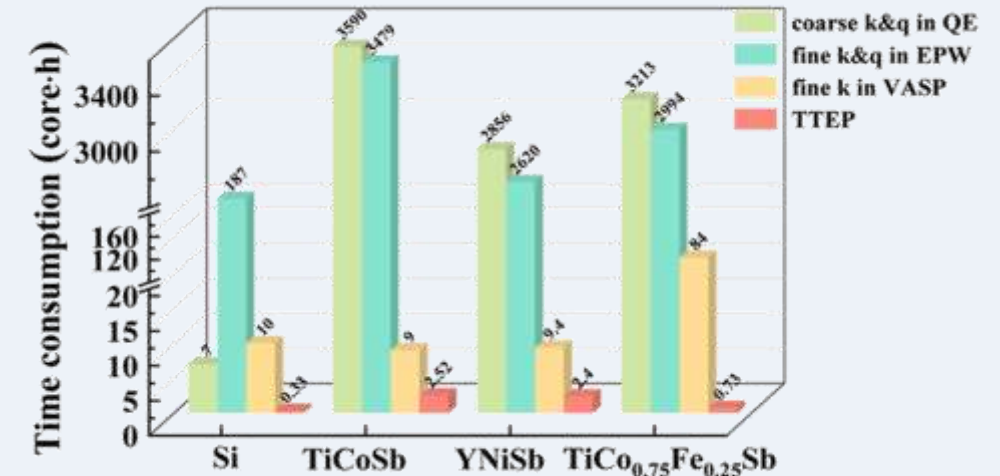
$$\frac{1}{\tau_{\mathbf{q}\lambda}^{\text{EP}}} = \frac{\pi D_A^2}{VB} \sum_{mn,\mathbf{k}} \omega_{\mathbf{q}\lambda} (f_{m\mathbf{k}+\mathbf{q}} - f_{n\mathbf{k}}) \delta(\varepsilon_{n\mathbf{k}} - \varepsilon_{m\mathbf{k}+\mathbf{q}} - \hbar\omega_{\mathbf{q}\lambda})$$

D_A : deformation potential $\omega_{\mathbf{q}\lambda}$: phonon frequency

V : Volume of unitcell B : Bulk modulus

Comput. Mater. Sci., 244, 113190 (2024)

Achieved a balance between accuracy and efficiency



- The TTEP code can also handle **grain boundary scattering**.

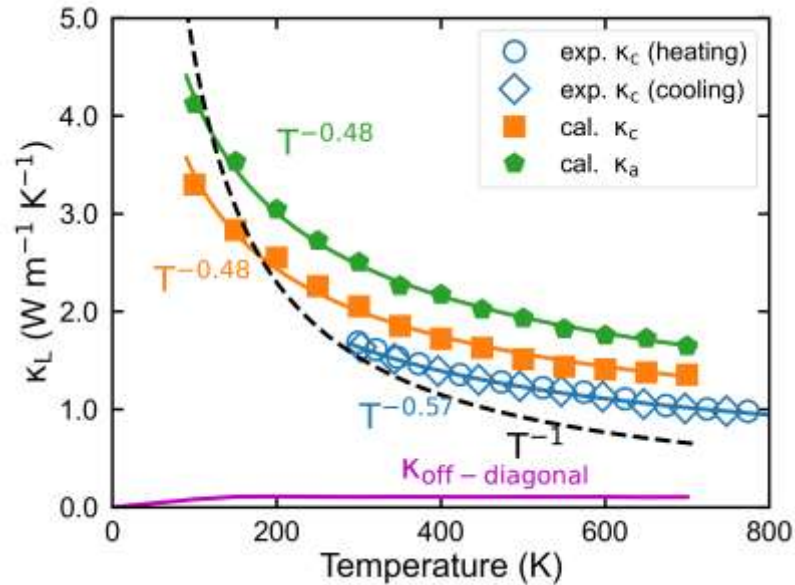
3.3 Something Beyond Temperature-dependent force constants

$$E = E_0 + \frac{1}{2} \sum_{ij\alpha\beta} \Phi_{ij}^{\alpha\beta} r_i^\alpha r_j^\beta + \frac{1}{3!} \sum_{ijk\alpha\beta\gamma} \Phi_{ijk}^{\alpha\beta\gamma} r_i^\alpha r_j^\beta r_k^\gamma + \frac{1}{4!} \sum_{ijkl\alpha\beta\gamma\theta} \Phi_{ijkl}^{\alpha\beta\gamma\theta} r_i^\alpha r_j^\beta r_k^\gamma r_l^\theta + \dots$$

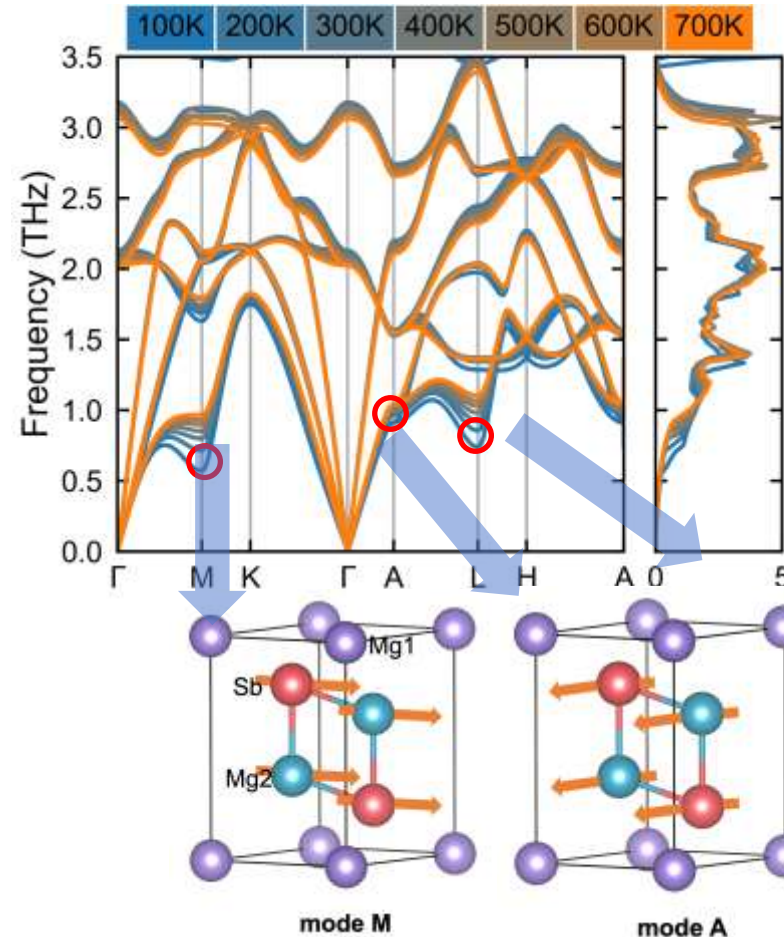
$\Phi^{\alpha\beta}(T)$

$\Phi^{\alpha\beta\gamma}(T)$

□ Temperature-Dependent κ_L of Mg_3Sb_2



- Weak κ_L T -dependence in Mg_3Sb_2 (theory: $T^{-0.48}$; experiment: $T^{-0.57}$), deviating from the classical T^{-1} law.



- Phonon dispersion is derived from the **effective 2nd IFCs**
- Noticeable changes are observed in the **TA branches**

- TA phonon hardening at high $T \rightarrow$ **weak κ_L - T dependence**, common in low κ_L materials.

3.3 Something Beyond

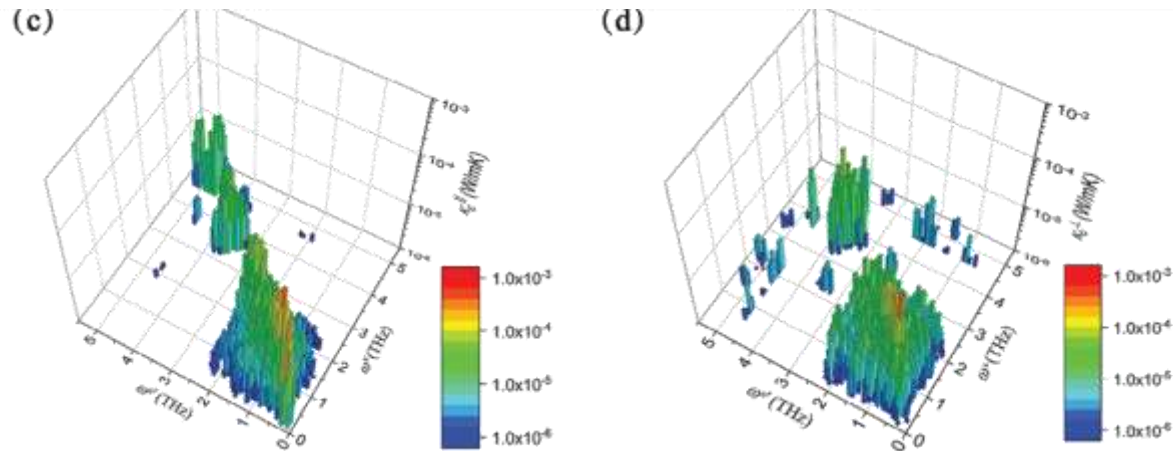
coherence κ_L

- $\kappa_L^{\alpha\beta} = \kappa_p^{\alpha\beta} + \kappa_c^{\alpha\beta}$

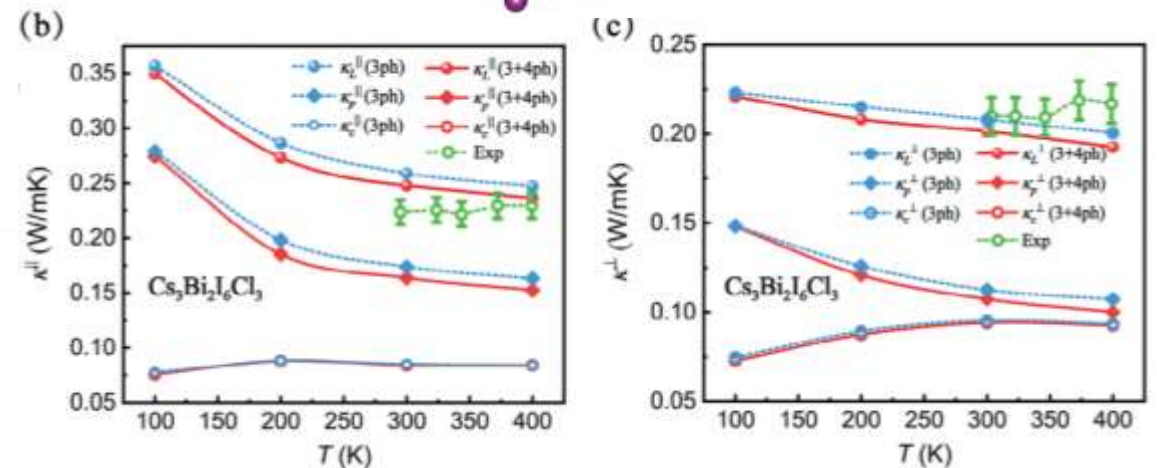
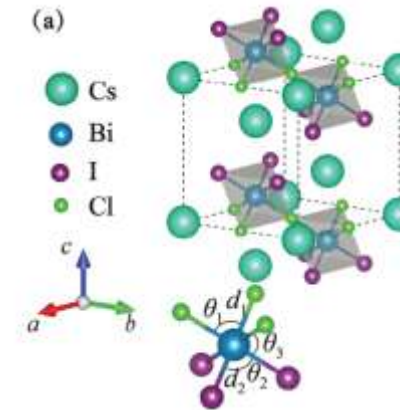
$$\kappa_C = \frac{\hbar^2}{k_B T^2 V N} \sum_{\mathbf{q}} \sum_{s \neq s'} \frac{\omega_{\mathbf{q}\lambda}^s + \omega_{\mathbf{q}\lambda}^{s'}}{2} v_{\mathbf{q}\lambda}^{s,s'}$$

- $\otimes v_{\mathbf{q}\lambda}^{s',s} \times \frac{\omega_{\mathbf{q}\lambda}^s n_{\mathbf{q}\lambda}^s (n_{\mathbf{q}\lambda}^s + 1) + \omega_{\mathbf{q}\lambda}^{s'} n_{\mathbf{q}\lambda}^{s'} (n_{\mathbf{q}\lambda}^{s'} + 1)}{4(\omega_{\mathbf{q}\lambda}^{s'} - \omega_{\mathbf{q}\lambda}^s)^2 + (\Gamma_{\mathbf{q}\lambda}^s + \Gamma_{\mathbf{q}\lambda}^{s'})^2} (\Gamma_{\mathbf{q}\lambda}^s + \Gamma_{\mathbf{q}\lambda}^{s'})$

- $v_{\mathbf{q}\lambda}^{s',s} = \frac{\langle e_{\mathbf{q}\lambda}^s | \frac{\partial D(\mathbf{q})}{\partial \mathbf{q}} | e_{\mathbf{q}\lambda}^{s'} \rangle}{\omega_{\mathbf{q}\lambda}^s + \omega_{\mathbf{q}\lambda}^{s'}}$



Adv. Sci., 11, 2406380 (2024)



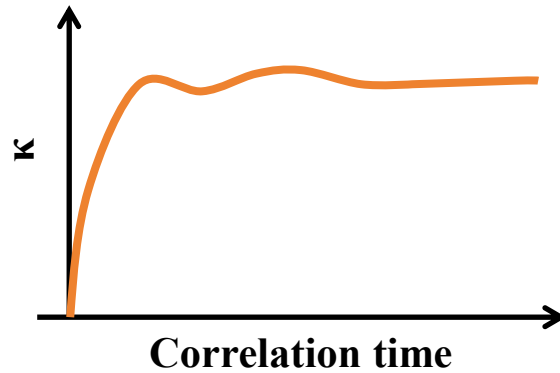
- Large coherence κ_L stems from large scattering rate (strong anharmonicity) and small frequency difference.
- The coherence κ_L is very common in ultralow κ_L materials.

3.3 Something Beyond

Green-Kubo vs NEMD

GK-EMD method

$$\kappa_{\alpha\beta} = \frac{1}{k_B T^2 V} \int_0^\infty \langle J_\alpha(0) J_\beta(t) \rangle dt$$

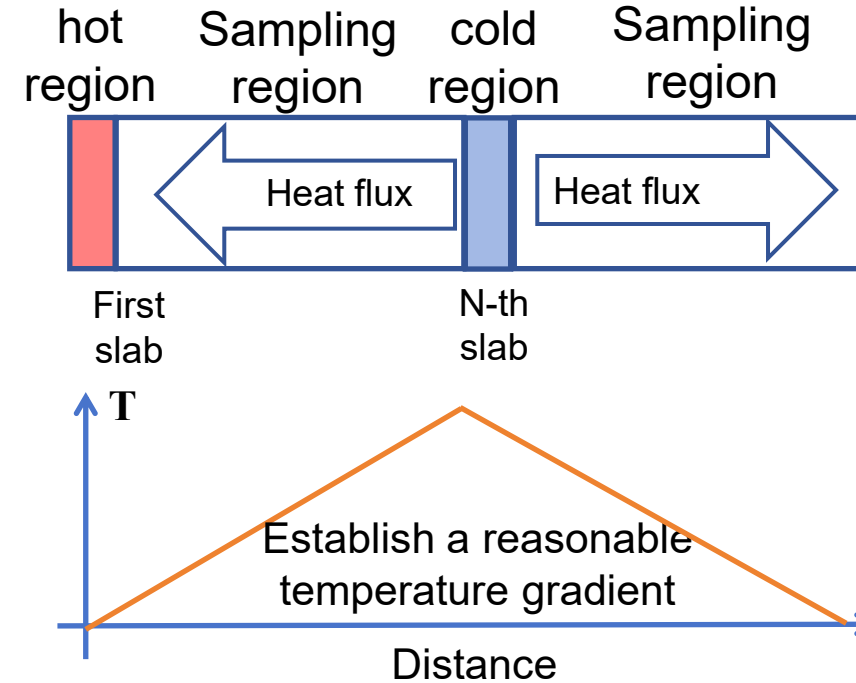


Convection term: $J_{\text{conv}} = \sum_i \mathbf{v}_i \left(\frac{1}{2} m_i \mathbf{v}_i^2 + U_i \right)$

Conduction term:

$$J_{\text{cond}} = \sum_i \mathbf{r}_i \frac{d}{dt} \left(\frac{1}{2} m_i \mathbf{v}_i^2 + U_i \right) = \sum_i \mathbf{r}_i (\mathbf{v}_i \cdot \mathbf{F}_i) + \sum_i \mathbf{r}_i \frac{dU_i}{dt}$$

NEMD method



Fourier's Law:

$$\kappa = \frac{J}{-\nabla T}$$

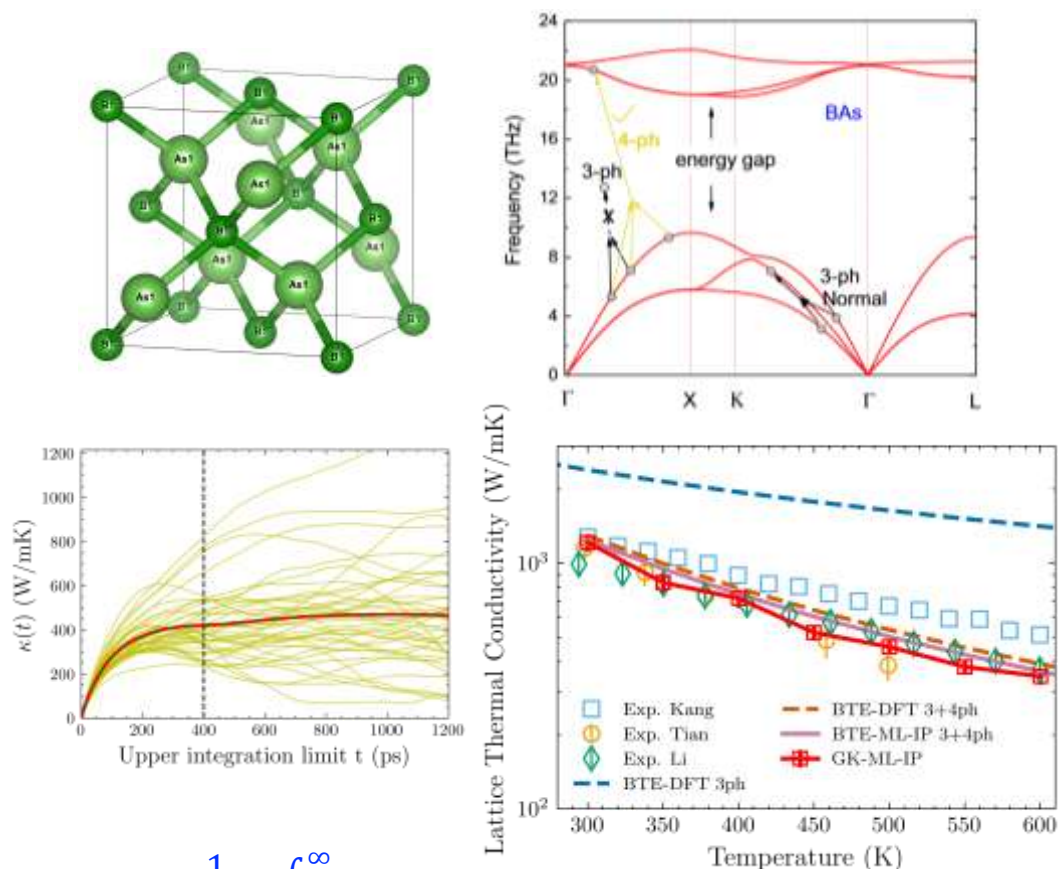
Size Extrapolation:

$$\frac{1}{\kappa} = \frac{1}{\kappa_\infty} + \frac{\beta}{L_{ss}}$$

J. Chem. Phys., 22, 398-413 (1954)
J. Phys. Soc. Jpn., 12, 570-586 (1957)
J. Chem. Phys., 106, 6082-6085 (1997)

3.3 Something Beyond

BAs with 4phScattering

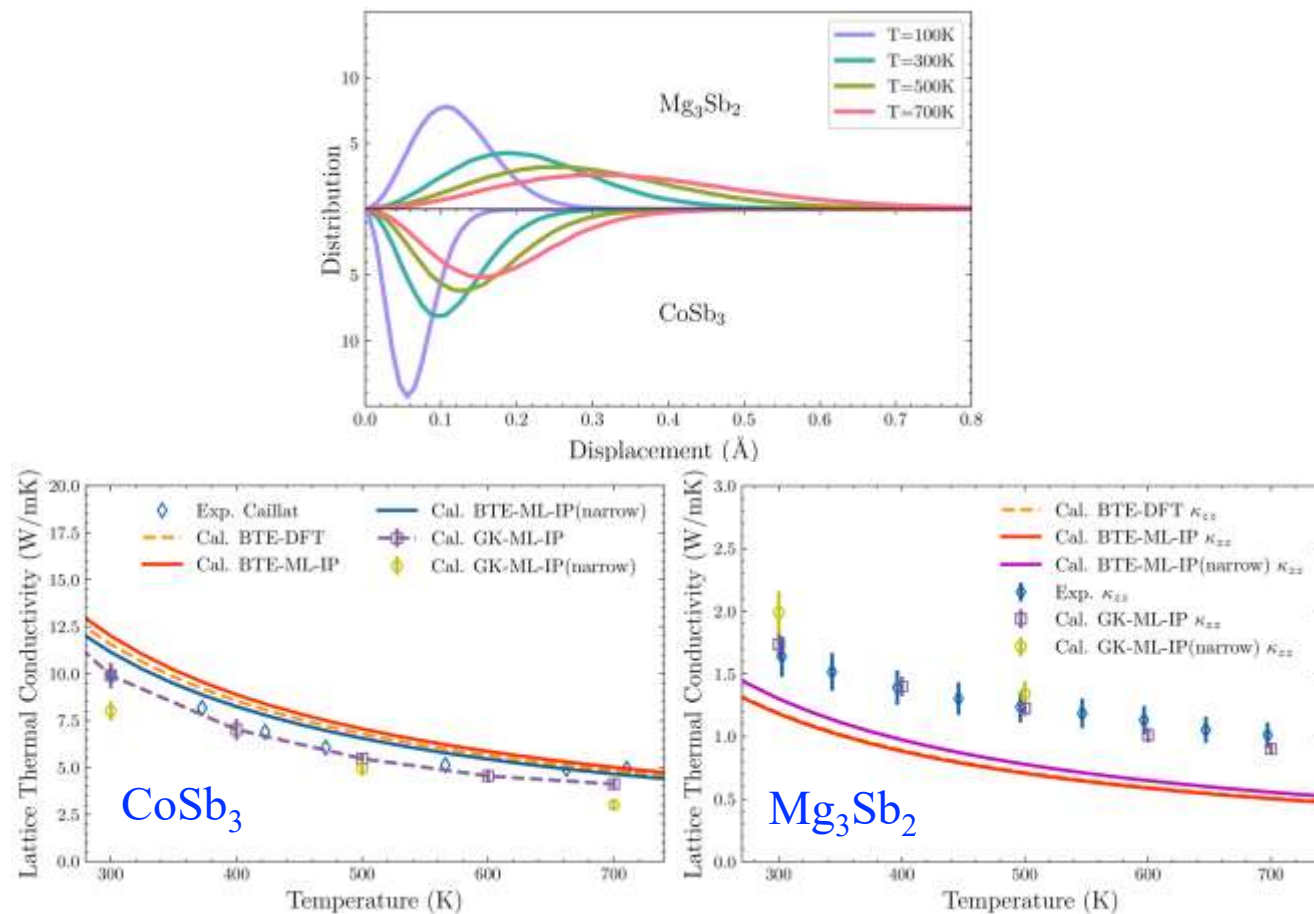


$$\kappa_{\alpha\beta} = \frac{1}{k_B T^2 V} \int_0^\infty \langle J_\alpha(0) J_\beta(t) \rangle dt$$

- Green-Kubo accurately predicts κ_L of BAs with four-phonon scattering.

Green-Kubo method

Machine-Learning Potential MD

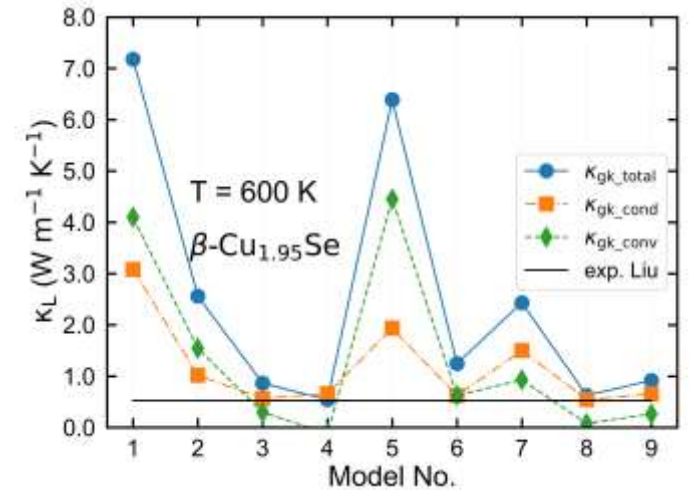
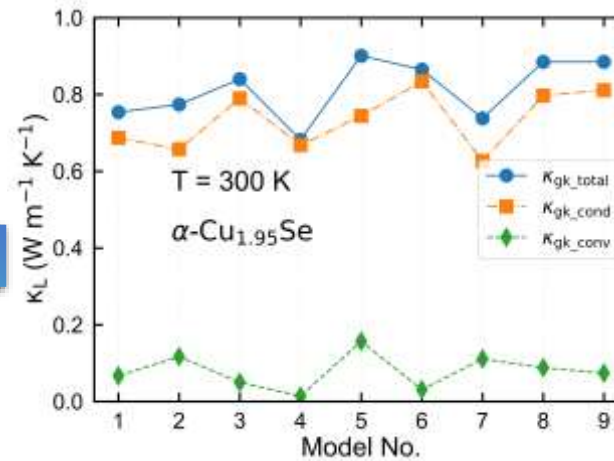
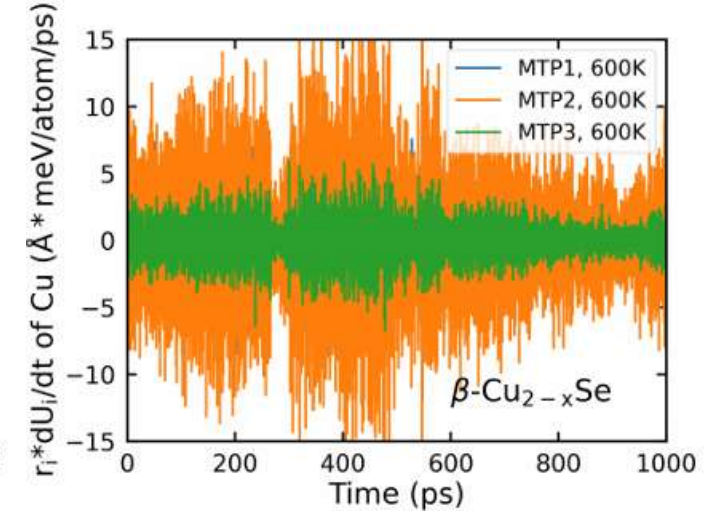
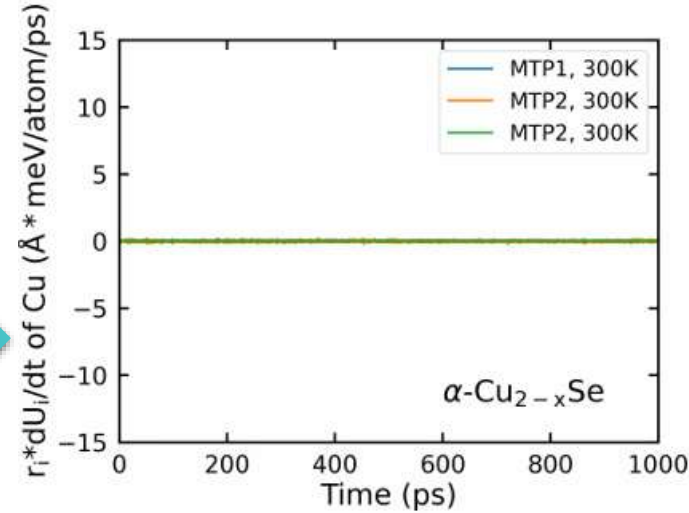


- GK naturally captures high-order interactions and temperature-dependent IFCs, yielding κ_L in good agreement with exp.

$$\begin{cases} J_{\text{conv.}} = \sum_i v_i \left(\frac{1}{2} m_i v_i^2 + U_i \right) \\ J_{\text{cond.}} = \sum_i r_i [(F_i \cdot v_i) + \frac{dU_i}{dt}] \end{cases}$$

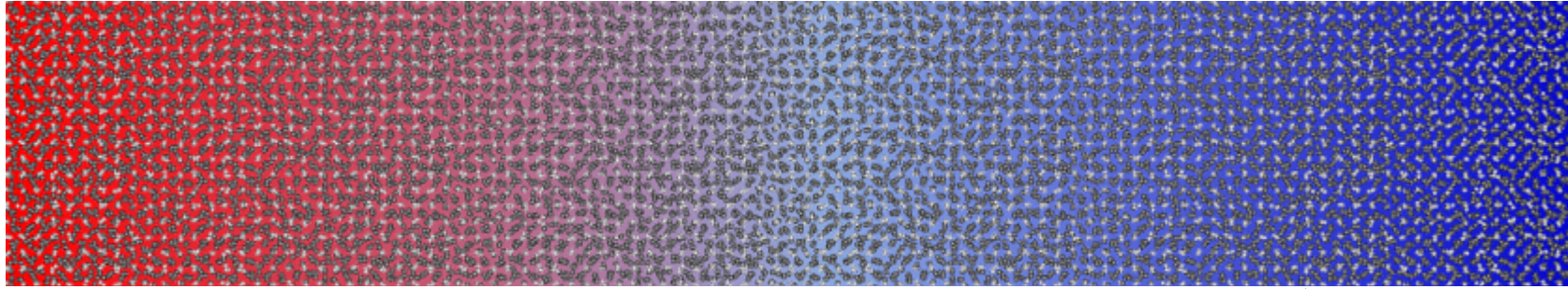
- GK-MLIP method failed in materials with atomic diffusion due to the strong influence from the uncertainty of atomic potential energy U_i in GK.

Ambiguous Projection



3.3 Something Beyond

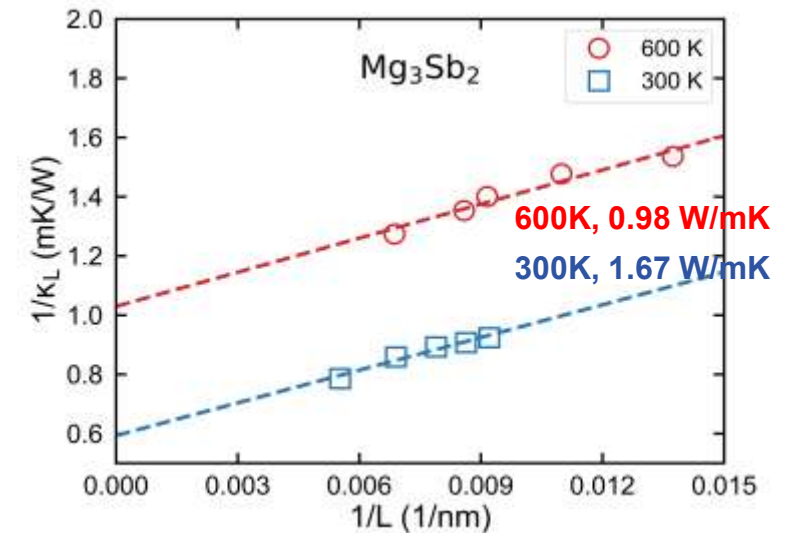
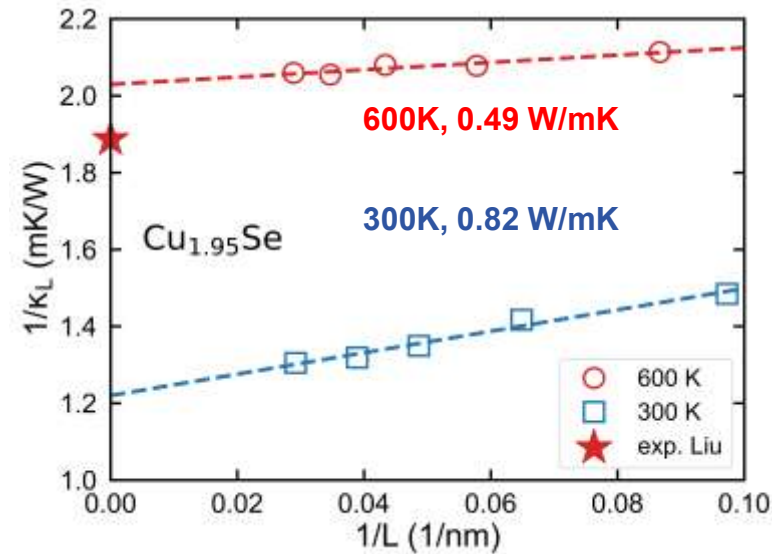
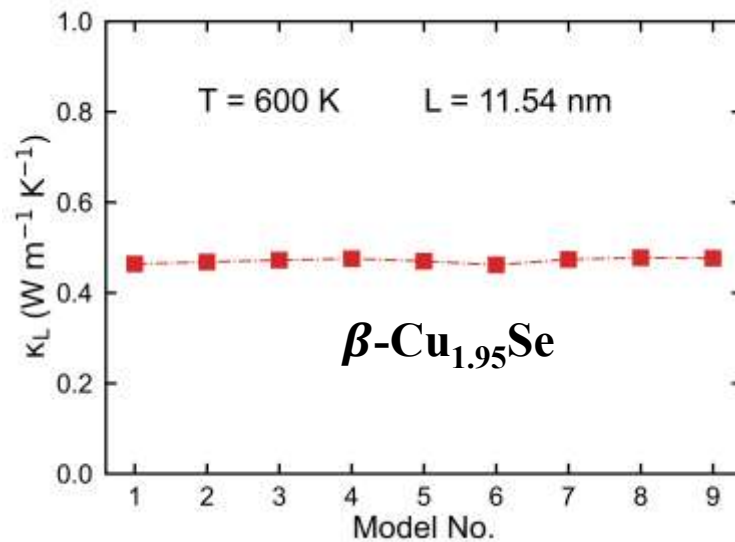
NEMD method



hot region

Heat flux

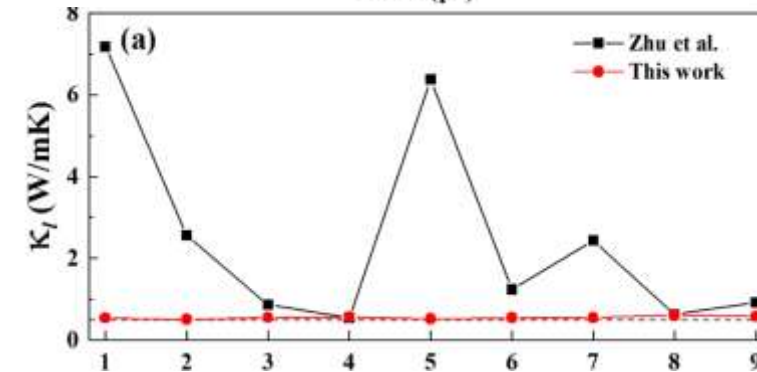
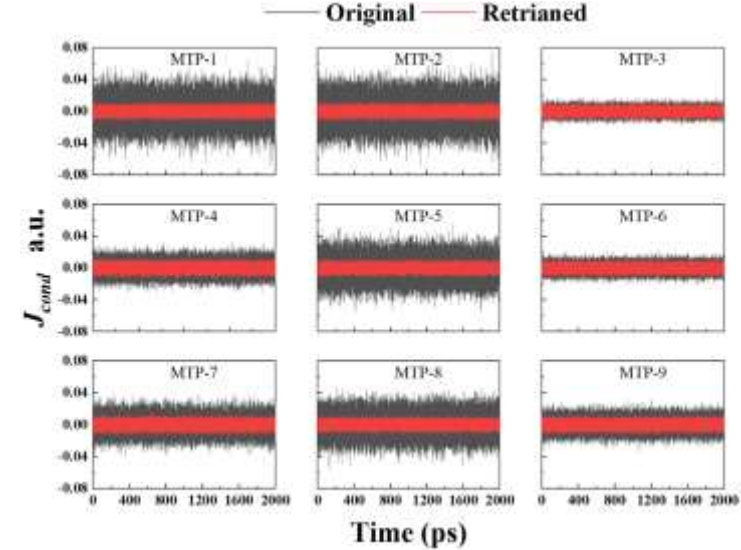
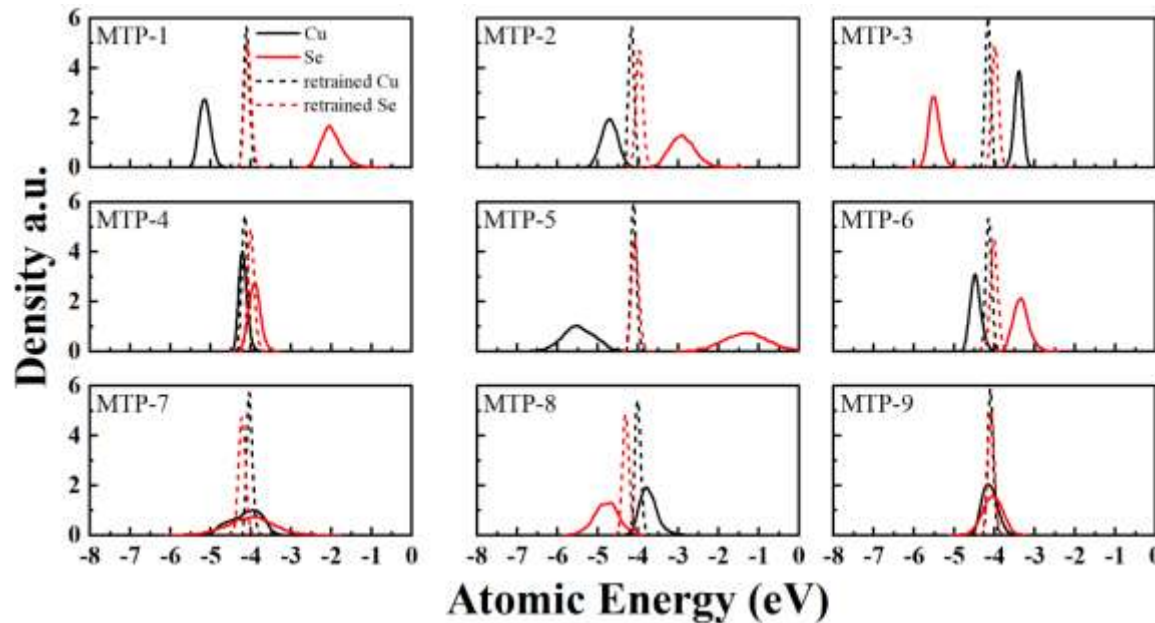
cold region



- Direct NEMD accurately predicts κ_L of $\beta\text{-Cu}_{1.95}\text{Se}$ and other crystalline materials.
- No noticeable fluctuations are observed among different ML models.

$$Loss = Loss_{label} + Loss_{dist.}$$

$$\begin{cases} Loss_{label} = \sum (y^{DFT} - y^{ML})^2 \\ Loss_{dist.} = \sum_t \sum_{i \in t} \frac{(U_i^{ML} - \bar{U}_t^{ML})^2}{2\sigma_i^2} \end{cases}$$



- Introduce the constraint on the distribution and absolute energy position of the atomic energy in the loss function.
- κ_L s for Cu_{2-x}Se predicted by each model exhibit high consistency in GK calculations, and agree well with experiments.

Summary on ph-trans

□ BTE level:

- ✓ The calculation of three-phonon interaction is less demanding than el-ph interaction, which make it more available in practice.
- ✓ The thermal transports based on three-phonon interaction for defective systems reshape the understanding on the influence of point defect.

□ Higher level:

- ✓ Renormalization on force constants and coherence κ_L , are the hot topics for materials with strong anharmonicity.
- ✓ EMD and NEMD methods can solve the problems beyond the phonon picture.

Summary

- ❑ The theories, softwares, and case studies for electrical and thermal transport based on BTE methods are summarized.
- ❑ The knowledges of basic transport are essential for advancing the overall comprehension in the thermoelectric transport, and uncovering new anomalies.



Yasong Wu



Yuyan Yang



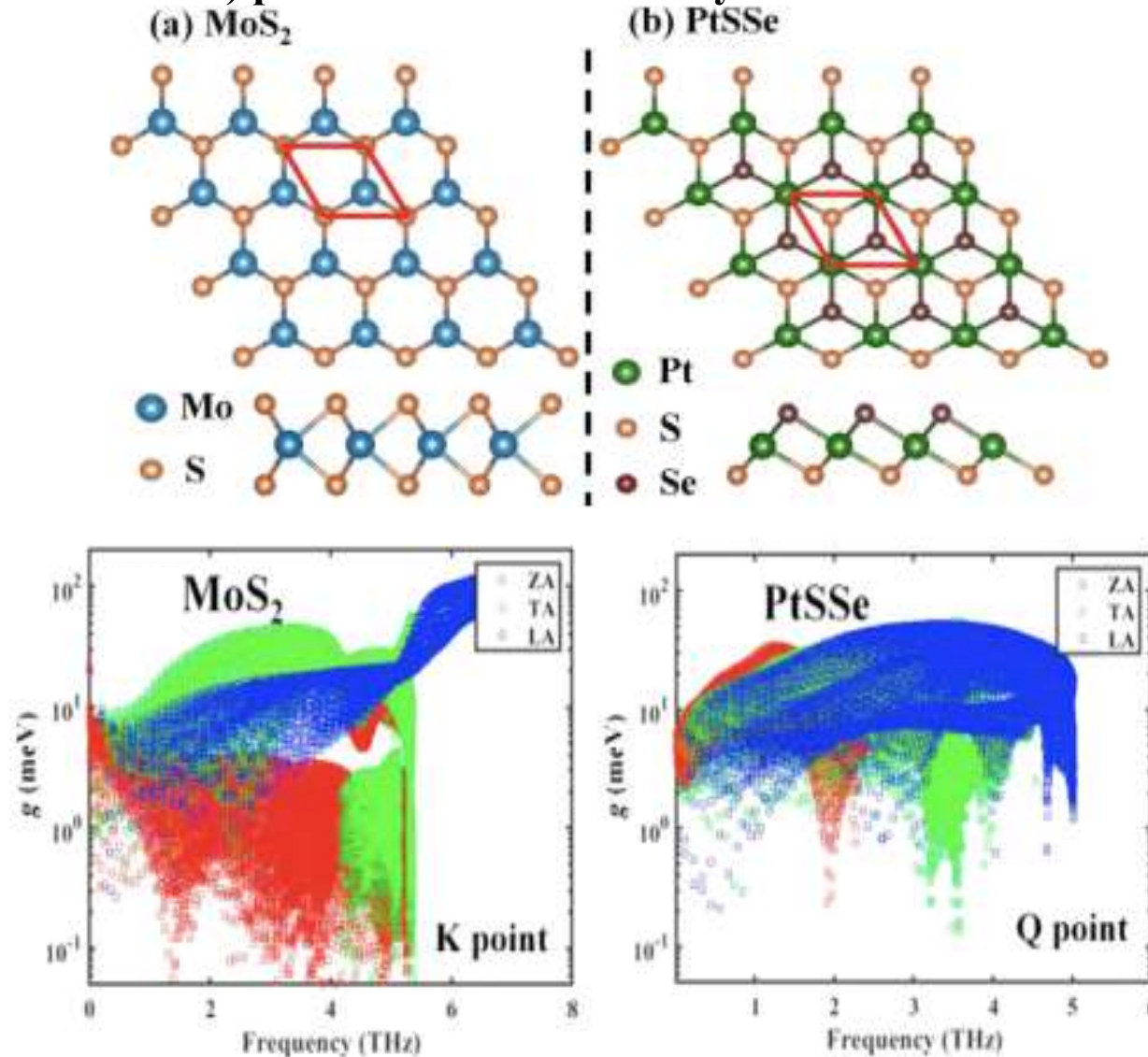
Dr. Shengnan Dai



Prof. Jinyang Xi

Thank you for your attention!

□ ZA (out-of-plane acoustic) phonon in TMD monolayers



Lack of horizontal mirror symmetry in PtSSe enables a strong el-ZA ph coupling

Mater. Today Phys., 15, 100277 (2020)

3.1 BTE in Lattice Thermal Transport

□ Under a temperature gradient ∇T , the heat flux J is defined as: $J = \sum_p \int f_{\lambda} \hbar \omega_{\lambda} \mathbf{v}_{\lambda} \frac{d\mathbf{q}}{(2\pi)^3}$

□ Phonon distribution deviation arises from the temperature-gradient-induced **diffusion** and **scattering**:

$$\frac{df_{\lambda}}{dt} = \left. \frac{\partial f_{\lambda}}{\partial t} \right|_{\text{diffusion}} + \left. \frac{\partial f_{\lambda}}{\partial t} \right|_{\text{scattering}} = 0$$

□ Linearized Boltzmann Transport Equation (BTE): $\mathbf{F}_{\lambda} = \tau_{\lambda}^0 (\mathbf{v}_{\lambda} + \Delta_{\lambda})$

$$\frac{1}{\tau_{\lambda}^0} = \frac{1}{N} \left(\sum_{\lambda' \lambda''}^{+} \Gamma_{\lambda \lambda' \lambda''}^{+} + \sum_{\lambda' \lambda''}^{-} \frac{1}{2} \Gamma_{\lambda \lambda' \lambda''}^{-} + \sum_{\lambda'} \Gamma_{\lambda \lambda'} \right)$$

$$\Delta_{\lambda} = \frac{1}{N} \sum_{\lambda' \lambda''}^{+} \Gamma_{\lambda \lambda' \lambda''}^{+} (\xi_{\lambda \lambda''} \mathbf{F}_{\lambda''} - \xi_{\lambda \lambda'} \mathbf{F}_{\lambda'}) + \frac{1}{N} \sum_{\lambda' \lambda''}^{-} \frac{1}{2} \Gamma_{\lambda \lambda' \lambda''}^{-} (\xi_{\lambda \lambda''} \mathbf{F}_{\lambda''} + \xi_{\lambda \lambda'} \mathbf{F}_{\lambda'}) + \frac{1}{N} \sum_{\lambda'} \Gamma_{\lambda \lambda'} \xi_{\lambda \lambda'} \mathbf{F}_{\lambda'}$$

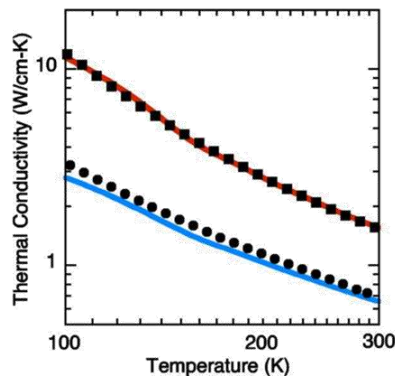


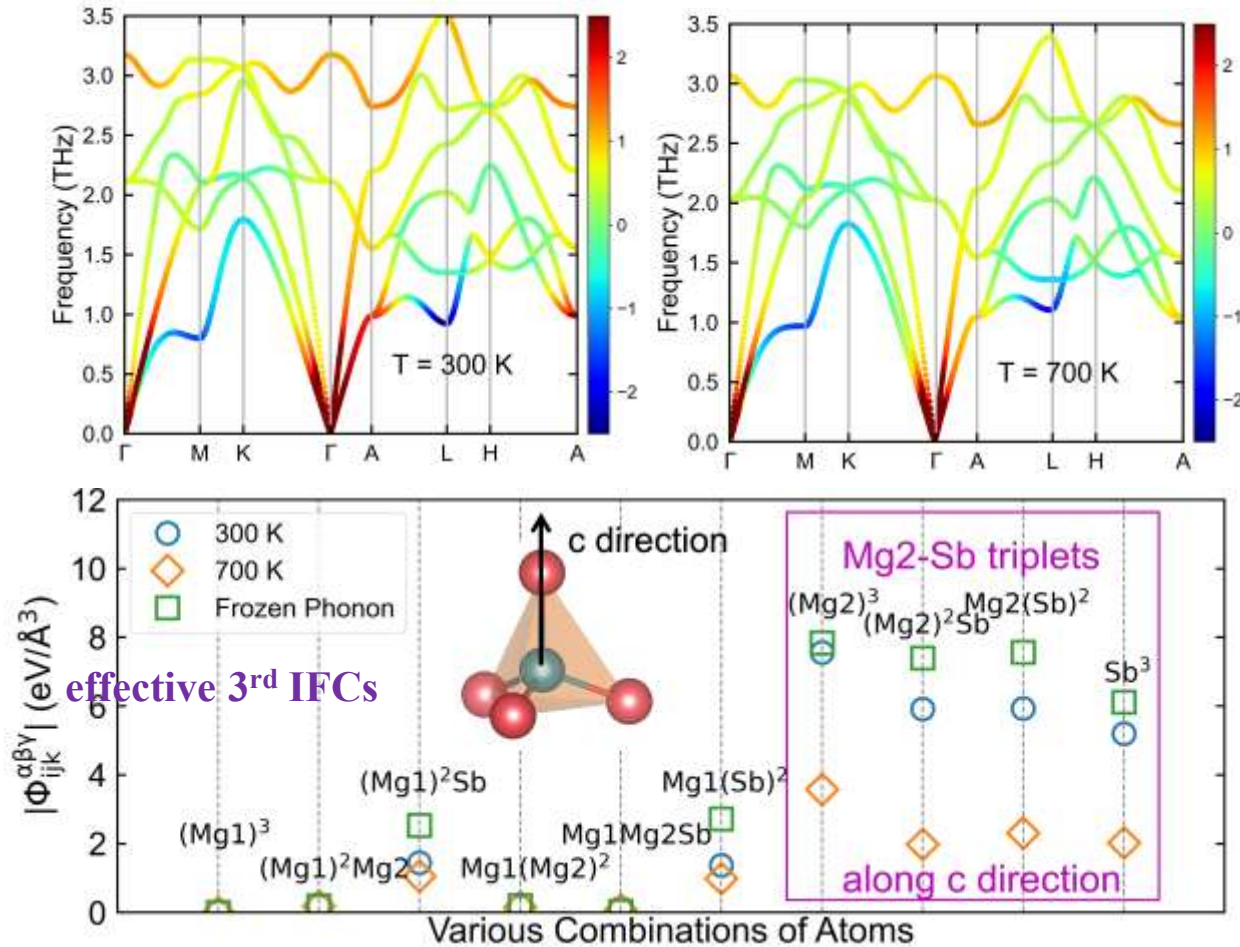
FIG. 1. (Color online) Lattice thermal conductivity $\kappa_L^{(i)}$ as a function of temperature. The red line and solid squares are the calculated and measured thermal conductivities of silicon, respectively, while the blue line and the solid circles are the corresponding quantities for germanium.

- Since **2007**, three-phonon calculations combined with **BTE** have become a standard approach for κ_L prediction, achieving high accuracy in conventional crystals.

Appl. Phys. Lett., 91, 231922 (2007)
Phys. Rev. B, 87, 165201 (2013)
Phys. Rev. B, 185, 1747 (2014)

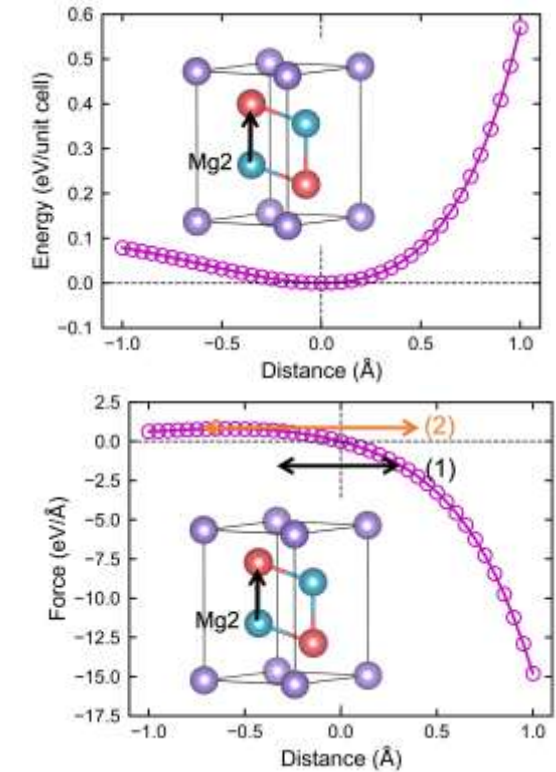
3.3 Something Beyond Temperature-dependent force constants

Grüneisen parameter–projected phonon dispersion



- The reduction in the absolute Grüneisen parameter with T confirms that anharmonicity weakens in Mg_3Sb_2 .
- Temperature-induced reduction of Mg–Mg and Sb–Sb 3rd IFCs leads to the weak κ_L –T dependence in Mg_3Sb_2 .

Asymmetric energy/force–displacement curve



- The curve of the Mg2 atoms is asymmetric, and this asymmetry increases with temperature.